DATA HANDBOOK

Wideband Hybrid IC Modules

Philips Semiconductors



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QUALITY ASSURED

Our quality system focuses on the continuing high quality of our components and the best possible service for our customers. We have a three-sided quality strategy: we apply a system of total quality control and assurance; we operate customer-oriented dynamic improvement programmes; and we promote a partnering relationship with our customers and suppliers.

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All used or obsolete components should be disposed of according to the regulations applying at the disposal location. Depending on the location, electronic components are considered to be 'chemical', 'special' or sometimes 'industrial' waste. Disposal as domestic waste is usually not permitted.

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DATA HANDBOOK SYSTEM

SELECTION GUIDE

Selection guide

Wideband Hybrid IC Modules

CATV AMPLIFIER MODULES

TYPE NUMBER	FREQUENCY RANGE (MHz)	POWER GAIN at f = 50 MHz (G _p) (dB)	SLOPE CABLE EQUIVALENT (SL) (dB)	APPLICATION	PAGE
BGD102	40 to 450	18 to 19	0.5 to 2.5	power doubler	31
BGD104	40 to 450	19.5 to 20.5	0.5 to 2.5	power doubler	31
BGD106	40 to 450	21.5 to 22.5	0 to 2	power doubler	33
BGD108	40 to 450	35 to 37	0.2 to 2.2	power doubler	35
BGD502 (note 1)	40 to 550	18 to 19	0.2 to 2.2	power doubler	37
BGD504 (note 1)	40 to 550	19.5 to 20.5	0.2 to 2.2	power doubler	37
BGD506	40 to 550	21.5 to 22.5	0 to 2	power doubler	41
BGD508	40 to 550	35 to 37	0.2 to 2.2	power doubler	43
BGD601 (note 2)	40 to 600	12 to 13	0.2 to 2.2	power doubler	45
BGD602 (note 2)	40 to 600	18 to 19	0.2 to 2.2	power doubler	49
BGD702	40 to 750	18 to 19	0 to 1.5	power doubler	53
BGD885	40 to 860	16.5 to 17.5	0.2 to 1.6	power doubler	55
BGE85A	40 to 450	17.4 to 19.4	0.3 to 1.5	output amplifier	59
BGE88	40 to 450	33 to 36	0.5 to 2.5	amplifier	61
BGE88/01	40 to 450	33 to 36	0.5 to 2.5	amplifier	61
BGE885	40 to 860	16.5 to 17.5	0.2 to 1.2	amplifier	63
BGE887	470 to 860	22.5 to 25 (note 3)	-0.2 to +1	amplifier	65
BGX881	40 to 860	12 to 13	0.2 to 1.4	amplifier	67
BGX885N	40 to 860	16.5 to 17.5	0.2 to 1.4	amplifier	71
BGY60	40 to 300	32.5 to 34.5	0.5 to 1.5	push-pull amplifier	73
BGY61	5 to 200	12.5 to 13.5 (note 4)	-0.2 to +0.5	reverse amplifier	75
BGY65	5 to 200	18 to 19 (note 4)	-0.2 to +0.5	reverse amplifier	77
BGY67	5 to 200	21.5 to 22.5 (note 4)	-0.2 to +0.5	reverse amplifier	79
BGY67A	5 to 200	23.5 to 24.5 (note 4)	-0.2 to +0.5	reverse amplifier	81
BGY80	40 to 450	12 to 13	0.2 to 1.5	pre-amplifier	83
BGY81	40 to 450	12 to 13	0.2 to 1.5	final amplifier	83
BGY82	40 to 450	13.5 to 14.5	0.2 to 1.5	amplifier	87
BGY83	40 to 450	13.5 to 14.5	0.2 to 1.5	amplifier	87
BGY84	40 to 450	16.5 to 17.5	0.5 to 1.5	pre-amplifier	91
BGY84A	40 to 450	18 to 18.8	0.3 to 1.5	pre-amplifier	95
BGY85	40 to 450	16.5 to 17.5	0.5 to 1.5	final amplifier	91
BGY85A	40 to 450	18 to 18.8	0.3 to 1.5	final amplifier	95
BGY85H/01	40 to 450	14.8 to 16.4	_	trunk amplifier	99
BGY86	40 to 450	21.5 to 22.5	0 to 1.5	pre-amplifier	103
BGY87	40 to 450	21.5 to 22.5	0 to 1.5	final amplifier	103
BGY87B	40 to 450	26.2 to 27.8	0.5 to 2.5	amplifier	107

CATV AMPLIFIER MODULES

	FREQUENCY	POWER GAIN at	SLOPE CABLE		
TYPE NUMBER	RANGE (MHz)	f = 50 MHz (G _p) (dB)	EQUIVALENT (SL) (dB)	APPLICATION	PAGE
BGY88	40 to 450	33.5 to 35.5	0.5 to 2.5	line extender	109
BGY89	40 to 450	37 to 39	0 to 2.5	line extender	111
BGY580	40 to 550	12 to 13	0.5 to 2	pre-amplifier	113
BGY581	40 to 550	12 to 13	0.5 to 2	final amplifier	113
BGY582	40 to 550	13.5 to 14.5	0.2 to 1.5	amplifier	117
BGY583	40 to 550	13.5 to 14.5	0.2 to 1.5	amplifier	117
BGY584 (note 1)	40 to 550	16.5 to 17.5	0.5 to 2	pre-amplifier	121
BGY584A (note 1)	40 to 550	17.7 to 18.7	0.5 to 2	pre-amplifier	127
BGY585 (note 1)	40 to 550	16.5 to 17.5	0.5 to 2	final amplifier	121
BGY585A (note 1)	40 to 550	17.7 to 18.7	0.5 to 2	final amplifier	127
BGY586	40 to 550	21.5 to 22.5	0.2 to 1.5	pre-amplifier	133
BGY587	40 to 550	21.5 to 22.5	0.2 to 1.5	final amplifier	133
BGY587B	40 to 550	26.2 to 27.8	0.5 to 2.5	amplifier	137
BGY588	40 to 550	33.5 to 35.5	0 to 2.5	line extender	139
BGY681	40 to 600	12 to 13	0.7 to 2.2	amplifier	143
BGY683	40 to 600	13.5 to 14.5	0.2 to 1.7	amplifier	145
BGY685	40 to 600	16.5 to 17.5	0.5 to 2.2	amplifier	147
BGY685A	40 to 600	17.7 to 18.7	0.5 to 2.2	amplifier	149
BGY685AL	40 to 600	18 to 19	0.5 to 2	amplifier	151
BGY687	40 to 600	21 to 22	0.8 to 2.2	amplifier	155
BGY687B	40 to 600	26.2 to 27.8	0.8 to 2.8	amplifier	157
BGY785A	40 to 750	18 to 19	0 to 1.5	amplifier	159
BGY787	40 to 750	21 to 22	0 to 1.5	amplifier	161
BGY885A	40 to 860	18 to 19	_	amplifier	163

Notes

- 1. Specifications also supplied for 450 MHz bandwidth operation.
- 2. Specifications also supplied for 450 MHz and 550 MHz bandwidth operation.
- 3. Power gain measured at f = 470 MHz.
- 4. Power gain measured at 10 MHz.

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GENERAL PURPOSE HYBRID AMPLIFIER MODULES

12 V supply voltage; 'low noise' CECC

TYPE	SUPPLY CURRENT	STAGES	GAIN (dB)	NOISE FIGURE	V _{O(RMS)} TYP. VALUES (dB/μV)	MAX. VSWR TYP. VALUES (note 2)		PAGE	
	(mA)	,		(dB)	(note 1)	INPUT	OUTPUT		
OM2045	11.5	1	12	3.6	99	2.0	1.4	205	
OM2050	18	2	18	5.2	100	1.5	1.9	217	
OM2052	42	2	28	4.5	107	2.2	2.1	223	
OM2060	56	3	23	5.4	107	1.4	1.6	229	
OM2063	52	3	29	3.6	105	2.3	1.4	235	
OM2064	51	3	28	4.4	107	1.3	1.5	243	
OM2070	100	3	28	4.8	112	2.3	1.9	251	

12 V supply voltage; 'high output' CECC

TYPE	SUPPLY CURRENT (mA)	STAGES	GAIN (dB)	NOISE FIGURE (dB)	TYP. V	RMS) ALUES /µV) te 1)	MAX. VSWR TYP. VALUES (note 2)		PAGE	
	, ,				VHF	UHF	INPUT	OUTPUT		
OM2046	82	1	10	10	116	114	1.5	1.4	211	
OM2070B	100	3	30	4.8	113	112	2.7	1.9	257	

12 V supply voltage; CECC

TYPE	SUPPLY CURRENT	STAGES	GAIN (dB)	NOISE FIGURE	V _{O(RMS)} TYP. VALUES (dB/μV)	MAX. VSWR TYP. VALUES (note 2)		PAGE
	(mA)			(dB)	(note 1)	INPUT	OUTPUT	
OM345	11.5	1	12	5.5	99	2.0	1.4	167
OM350	18	2	18	6.0	100	1.5	1.9	173
OM360	56	3	23	7.0	107	1.3	1.5	179
OM361	51	3	28	6.0	107	1.5	1.7	185
OM370	100	3	28	7.0	112	2.3	1.9	191

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Selection guide

12 V supply voltage; 'satellite band'

TYPE	SUPPLY CURRENT (mA)	RRENT STAGES	GAIN NOISE FIGURE (dB)	V _{O(RMS)} TYP. VALUES (dB/μV)	MAX. VSWR TYP. VALUES (note 2)		PAGE	
	(mA)	(111A)		(45)	(note 1)	INPUT	OUTPUT	
OM926	28	2	16	6.5	103	1.8	1.7	197

Notes

- 1. Measured at -60 dB intermodulation distortion to DIN 45004, para. 6.3: 3-tone.
- 2. The typical maximum VSWR occurring in the frequency range 40 860 MHz, for a sample connected to a 75 Ω line.

GENERAL

Pro electron type numbering system
Rating systems
Letter symbols
CATV parameters
Mounting and Soldering recommendations

General

PRO ELECTRON TYPE NUMBERING SYSTEM

Basic type number

This type designation code applies to discrete semiconductor devices (not integrated circuits), multiples of such devices, semiconductor chips and darlington transistors.

FIRST LETTER

The first letter gives information about the material for the active part of the device.

- A germanium or other material with a band gap of 0.6 to 1 eV
- B silicon or other material with a band gap of 1 to 1.3 eV
- C gallium arsenide (GaAs) or other material with a band gap of 1.3 eV or more
- R compound materials, e.g. cadmium sulphide.

SECOND LETTER

The second letter indicates the function for which the device is primarily designed. The same letter can be used for multi-chip devices with similar elements. In the following list low power types are defined by $R_{th \ imb} > 15 \ \text{K/W}$ and power types by $R_{th \ imb} \leq 15 \ \text{K/W}$.

- A diode; signal, low power
- B diode: variable capacitance
- C transistor; low power, audio frequency
- D transistor; power, audio frequency
- E diode; tunnel
- F transistor; low power, high frequency
- G multiple of dissimilar devices/miscellaneous devices; e.g. oscillators. Also with special third letter, see under 'Serial number'
- H diode; magnetic sensitive
- L transistor; power, high frequency
- N photocoupler
- P radiation detector; e.g. high sensitivity photo-transistor; with special third letter

- Q radiation generator; e.g. LED, laser; with special third letter
- R control and switching device; e.g. thyristor, low power; with special third letter
- S transistor; low power, switching
- T control and switching device; e.g. thyristor, power; with special third letter
- U transistor; power, switching
- W surface acoustic wave device
- X diode; multiplier, e.g. varactor, step recovery
- Y diode; rectifying, booster
- Z diode; voltage reference or regulator, transient suppressor diode; with special third letter.

SERIAL NUMBER/SPECIAL THIRD LETTER

The number comprises three figures running from 100 to 999 for devices primarily intended for consumer equipment, or one letter (Z, Y, X, etc.) and two figures running from 10 to 99 for devices primarily intended for industrial or professional equipment.⁽¹⁾ The letter has no fixed meaning, except in the following cases:

- A for triacs, after second letter 'R' or 'T'
- F for emitters and receivers in fibre-optic communication, after second letter 'G', 'P' or 'Q'. When the second letter is 'G', the first letter should be defined in accordance with the material of the main optical device.
- L for lasers in non-fibre-optic applications, after second letter 'G' or 'Q'. When the second letter is 'G', the first letter should be defined in accordance with the material of the main optical device.
- O for opto-triacs, after second letter 'R'
- T for 3-state bicolour LEDs, after second letter 'Q'
- W for transient voltage suppressor diodes, after second letter 'Z'.

⁽¹⁾ When the supply of these serial numbers is exhausted, the serial number may be expanded to three figures for industrial types and four figures for consumer types.

General

EXAMPLES OF BASIC TYPE NUMBERS

AA112: germanium, low-power signal diode

(consumer type)

ACY32: germanium, low-power AF transistor (industrial

type)

BD232: silicon, power AF transistor (consumer type) CQY17: GaAs, light-emitting diode (industrial type) RPY84: CdS, photo-conductive cell (industrial type).

Version letter(s)

One or two letters may be added to the basic type number to indicate minor electrical or mechanical variants of the basic type. The letters never have a fixed meaning, except that the letter 'R' indicates reverse polarity and the letter 'W' indicates a surface mounted device (SMD).

Suffix

Sub-classification can be used for devices supplied in a wide range of variants, called associated types. The following sub-coding suffixes are in use:

VOLTAGE REFERENCE AND VOLTAGE REGULATOR DIODES

One letter and one number, preceded by a hyphen (-). The letter, if required, indicates the nominal tolerance of the Zener voltage.

A 1% (in accordance with IEC 63, series E96)

B 2% (in accordance with IEC 63, series E48)

C 5% (in accordance with IEC 63, series E24)

D 10% (in accordance with IEC 63, series E12)

E 20% (in accordance with IEC 63, series E6).

In the case of a 3% tolerance, the letter 'F' is used.

The number denotes the typical operating (Zener) voltage, related to the nominal current rating for the entire range. The letter 'V' is used in place of the decimal point.

Example: BZY74-C6V3 or -C10.

TRANSIENT VOLTAGE SUPPRESSOR DIODES

One number, preceded by a hyphen (-). The number indicates the maximum recommended continuous reversed (stand-off) voltage, $V_{\rm R}$. The letter 'V' is used in place of the decimal point.

Example: BZW70-9V1 or -39.

The letter 'B' may be used immediately after the last number, to indicate a bidirectional suppressor diode.

Example: BZW10-15B.

CONVENTIONAL AND CONTROLLED AVALANCHE RECTIFIER DIODES AND THYRISTORS

One number, preceded by a hyphen (-). The number indicates the rated maximum repetitive peak reverse voltage, V_{RRM} , or the rated repetitive peak off-state voltage, V_{DRM} , whichever is the lower. Reversed polarity with respect to the case is indicated by the letter 'R' immediately after the number.

Example: BYT-100 or -100R.

RADIATION DETECTORS

One number, preceded by a hyphen (-). The number indicates the depletion layer in micrometres (μ m). The resolution is indicated by a version letter.

Example: BPX10-2A.

ARRAY OF RADIATION DETECTORS AND GENERATORS

One number, preceded by a hyphen (-). The number indicates the number of basic devices assembled into the array.

Examples: BPW50-6, BPW50-9, BPW50-12.

HIGH FREQUENCY POWER TRANSISTORS

One number, preceded by a hyphen (-). The number indicates the supply voltage.

Example: BLU80-24.

RATING SYSTEMS

The rating systems described are those recommended by the International Electrotechnical Commission (IEC) in its publication number 134.

Definitions of terms used

ELECTRONIC DEVICE

An electronic tube or valve, transistor or other semiconductor device. This definition excludes inductors, capacitors, resistors and similar components.

CHARACTERISTIC

A characteristic is an inherent and measurable property of a device. Such a property may be electrical, mechanical, thermal, hydraulic, electro-magnetic or nuclear, and can be expressed as a value for stated or recognized conditions. A characteristic may also be a set of related values, usually shown in graphical form.

BOGEY ELECTRONIC DEVICE

An electronic device whose characteristics have the published nominal values for the type. A bogey electronic device for any particular application can be obtained by considering only those characteristics that are directly related to the application.

RATING

A value that establishes either a limiting capability or a limiting condition for an electronic device. It is determined for specified values of environment and operation, and may be stated in any suitable terms. Limiting conditions may be either maxima or minima.

RATING SYSTEM

The set of principles upon which ratings are established and which determine their interpretation. The rating system indicates the division of responsibility between the device manufacturer and the circuit designer, with the object of ensuring that the working conditions do not exceed the ratings.

Absolute maximum rating system

Absolute maximum ratings are limiting values of operating and environmental conditions applicable to any electronic device of a specified type, as defined by its published data, which should not be exceeded under the worst probable conditions.

These values are chosen by the device manufacturer to provide acceptable serviceability of the device, taking no responsibility for equipment variations, environmental variations, and the effects of changes in operating conditions due to variations in the characteristics of the device under consideration and of all other electronic devices in the equipment.

The equipment manufacturer should design so that, initially and throughout the life of the device, no absolute maximum value for the intended service is exceeded with any device, under the worst probable operating conditions with respect to supply voltage variation,

equipment component variation, equipment control adjustment, load variations, signal variation, environmental conditions, and variations in characteristics of the device under consideration and of all other electronic devices in the equipment.

Design maximum rating system

Design maximum ratings are limiting values of operating and environmental conditions applicable to a bogey electronic device of a specified type as defined by its published data, and should not be exceeded under the worst probable conditions.

These values are chosen by the device manufacturer to provide acceptable serviceability of the device, taking responsibility for the effects of changes in operating conditions due to variations in the characteristics of the electronic device under consideration.

The equipment manufacturer should design so that, initially and throughout the life of the device, no design maximum value for the intended service is exceeded with a bogey electronic device, under the worst probable operating conditions with respect to supply voltage variation, equipment component variation, variation in characteristics of all other devices in the equipment, equipment control adjustment, load variation, signal variation and environmental conditions.

Design centre rating system

Design centre ratings are limiting values of operating and environmental conditions applicable to a bogey electronic device of a specified type as defined by its published data, and should not be exceeded under normal conditions.

These values are chosen by the device manufacturer to provide acceptable serviceability of the device in average applications, taking responsibility for normal changes in operating conditions due to rated supply voltage variation, equipment component variation, equipment control adjustment, load variation, signal variation, environmental conditions, and variations in the characteristics of all electronic devices.

The equipment manufacturer should design so that, initially, no design centre value for the intended service is exceeded with a bogey electronic device in equipment operating at the stated normal supply voltage.

General

LETTER SYMBOLS

The letter symbols for transistors and signal diodes detailed in this section are based on IEC publication number 148.

Letter symbols for currents, voltages and powers

BASIC LETTERS

I, i current V, v voltage P, p power.

Upper-case letter symbols are used to represent all values except instantaneous values that vary with time, these are represented by lower-case letters.

SUBSCRIPTS

A, a	anode terminal
(AV), (av)	average value
B, b	base terminal (for MOS devices: substrate)
C, c	collector terminal
D, d	drain terminal
E, e	emitter terminal
F, f	forward
G, g	gate terminal
K, k	cathode terminal
M, m	peak value
О, о	as third subscript: the terminal not mentioned is open-circuit
R, r	as first subscript: reverse. As second subscript: repetitive. As third subscript: with a specified resistance between the terminal not mentioned and the reference terminal
(RMS), (rms)	root-mean-square value
S, s	as first or second subscript: source terminal (FETs only). As second subscript: non-repetitive (not FETs). As third subscript: short circuit between the terminal not mentioned and the reference terminal
X, x	specified circuit
Z, z	replaces R to indicate the actual working voltage, current or power of voltage

No additional subscript is used for DC values.

Upper-case subscripts are used for the indication of:

reference and voltage regulator diodes.

- continuous (DC) values (without signal), e.g. I_B
- instantaneous total values, e.g. i_B
- average total values, e.g. I_{B(AV)}
- peak total values, e.g. I_{RM}
- root-mean-square total values, e.g. I_{R(BMS)}.

Lower-case subscripts are used for the indication of values applying to the varying component alone:

- instantaneous values, e.g. in
- root-mean-square values, e.g. I_{b(rms)}
- peak values, e.g. I_{bm}
- average values, e.g. l_{b(av)}.

If more than one subscript is used, the subscript for which both styles exist are either all upper-case or all lower-case.

ADDITIONAL RULES FOR SUBSCRIPTS

Transistor currents

If it is necessary to indicate the terminal carrying the current, this should be done by the first subscript (conventional current flow from the external circuit into the terminal is positive).

Examples: I_B, i_B, i_b, I_{bm}.

Diode currents

To indicate a forward current (conventional current flow into the anode terminal), the subscript F or f should be used. For a reverse current (conventional current flow out of the anode terminal), the subscript R or r should be used.

Examples: I_F, I_R, i_F, I_{f(rms)}.

Transistor voltages

If it is necessary to indicate the points between which a voltage is measured, this should be done by the first two subscripts. The first subscript indicates the terminal at which the voltage is measured and the second the reference terminal or the circuit node. Where there is no possibility of confusion, the second subscript may be omitted.

Examples: V_{BE} , v_{BE} , v_{be} , V_{bem} .

Diode voltages

To indicate a forward voltage (anode positive with respect to cathode), the subscript F or f should be used. For a reverse voltage (anode negative with respect to cathode), the subscript R or r should be used.

Examples: V_F, V_R, v_F, V_{rm}.

Supply voltages or currents

Supply voltages or supply currents are indicated by repeating the appropriate terminal subscript.

Examples: V_{CC}, I_{EE}.

If it is necessary to indicate a reference terminal, this should be done by a third subscript.

Example: V_{CCE}.

Subscripts for devices with more than one terminal of the same kind

If a device has more than one terminal of the same kind, the subscript is formed by the appropriate letter for the terminal, followed by a number. In the case of multiple subscripts, hyphens may be necessary to avoid confusion.

Examples:

I_{B2} continuous (DC) current flowing into the second base terminal

V_{B2-E} continuous (DC) voltage between the terminals of second base and emitter.

Subscripts for multiple devices

For multiple unit devices, the subscripts are modified by a number preceding the letter subscript. In the case of multiple subscripts, hyphens may necessary to avoid confusion.

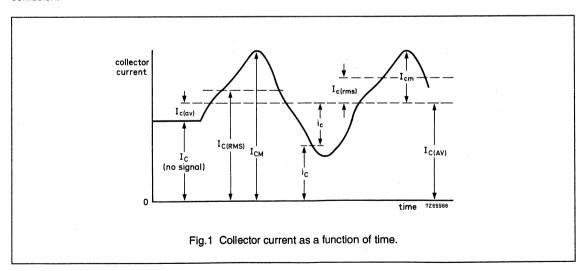
Examples:

I_{2C} continuous (DC) current flowing into the collector terminal of the second unit

V_{1C-2C} continuous (DC) voltage between the collector terminals of the first and second units.

Application of the rules

Figure 1 represents a transistor collector current as a function of time. It comprises a continuous (DC) current and a varying component.



General

Letter symbols for electrical parameters

DEFINITION

For the purpose of this publication, the term 'electrical parameter' applies to four-pole matrix parameters, elements of electrical equivalent circuits, electrical impedances and admittances, inductances and capacitances.

BASIC LETTERS

The following list comprises the most important basic letters used for electrical parameters of semiconductor devices.

B, b	susceptance (imaginary part of an admittance)
С	capacitance
G, g	conductance (real part of an admittance)
H, h	hybrid parameter
L	inductance
R, r	resistance (real part of an impedance)
X, x	reactance (imaginary part of an impedance)
Y, y	admittance
Z, z	impedance.

Upper-case letters are used for the representation of:

- electrical parameters of external circuits and of circuits in which the device forms only a part
- · all inductances and capacitances.

Lower-case letters are used for the representation of electrical parameters inherent in the device, with the exception of inductances and capacitances.

SUBSCRIPTS

General subscripts

The following list comprises the most important general subscripts used for electrical parameters of semiconductor devices.

F, 1		forward	(forward	transfer)	

I, i (or 1) input
L, I load
O, o (or 2) output

R, r reverse (reverse transfer)

S, s source. Examples: Z_S , h_f , h_F .

The upper-case variant of a subscript is used for the

designation of static (DC) values.

Examples:

h_{FE} static value of forward current transfer ratio in common-emitter configuration (DC current gain)

R_E DC value of the external emitter resistance.

The static value is the slope of the line from the origin to the operating point on the appropriate characteristic curve, i.e. the quotient of the appropriate electrical quantities at the operating point.

The lower-case variant of a subscript is used for the designation of small-signal values.

Examples:

h_{fe} small-signal value of the short-circuit forward current transfer ratio in common-emitter configuration

 $Z_e = R_e + jX_e$ small-signal value of the external impedance.

If more than one subscript is used, subscripts for which both styles exist are either all upper-case or all lower-case.

Example: h_{FE}, y_{RE}, h_{fe}.

Subscripts for four-pole matrix parameters

The first letter subscript (or double numeric subscript) indicates input, output, forward transfer or reverse transfer.

Examples: h_i (or h_{11}), h_0 (or h_{22}), h_i (or h_{21}), h_r (or h_{12}).

A further subscript is used for the identification of the circuit configuration. When no confusion is possible, this further subscript may be omitted.

Examples: h_{fe} (or h_{21e}), h_{FE} (or h_{21E}).

DISTINCTION BETWEEN REAL AND IMAGINARY PARTS

If it is necessary to distinguish between real and imaginary parts of electrical parameters, no additional subscripts should be used. If basic symbols for the real and imaginary parts exist, these may be used.

Examples: $Z_i = R_i + jX_i$, $y_{fe} = g_{fe} + jb_{fe}$.

If such symbols do not exist, or if they are not suitable, the following notation is used:

Examples:

Re (h_{ib}) etc. for the real part of h_{ib} Im (h_{ic}) etc. for the imaginary part of h_{ib}.

CATV PARAMETERS

Gain (G_p)

DEFINITION

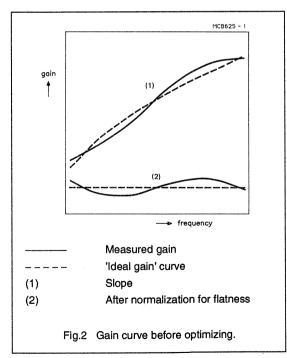
The power gain, expressed in dB, is the ratio of output and input power of a module, operating in a 75 Ω (Z_o) system.

MEASUREMENT

The power gain is measured at several frequencies throughout the band, although the gain performances are mostly given only at the start and stop frequencies. The gain is measured by applying a single tone signal to the module and measuring the output power. The input power is measured before connecting the module using a thru-line and feeding the system with exactly the same signals.

EQUIPMENT

Input and output power levels are measured with a power meter.



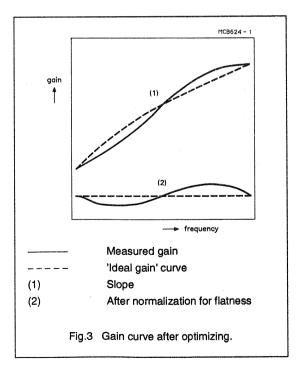
Flatness of frequency response (FL)

DEFINITION

The flatness of gain of a CATV amplifier module is defined as the maximum deviation from an absolute flat gain over a given frequency range, after the slope of the amplifier over this frequency range has been optimized and equalized by means of a certain cable length to give the best result for flatness (see Figs 2 and 3). This means that an 'ideal gain curve' for the module is calculated and the flatness is the maximum deviation of this 'ideal gain' curve.

CALCULATION

To determine the flatness, the measured gain values are compared with an 'ideal gain' curve derived from a mathematical model. The formula used is as follows:



General

$$Gain = G + C \sqrt{\frac{f_x}{f_1}}$$

where

G = constant gain (frequency independent)

C = cable constant

f_x = desired frequency

f₁ = start frequency

The cable constant (C) must be optimized during the flatness determination so that the gain curve best fits the measured gain figures. The start value for C is calculated using the formula:

$$C_{start} = \frac{G_n - G_1}{\sqrt{\frac{f_n}{f_r}} - 1}$$

where

G_n = the measured gain at stop frequency

G₁ = the measured gain at start frequency

f_n = stop frequency

The value of G is chosen so that the maximum positive deviation of the measured gain from the 'ideal gain' curve is the same as the maximum negative deviation. The value of C is adapted by \pm 0.001 until the 'ideal gain' curve best fits the measured curve.

The flatness of the module gain is the maximum deviation in measured gain from the optimized gain formula.

Slope (SL)

DEFINITION

The slope of a module is the difference between the 'ideal gain' at the start frequency and the 'ideal gain' at the stop frequency (see 'Flatness').

Flatness (S-curve method)

DEFINITION

For some high-slope modules the flatness is calculated according to the 'S-curve' method. The ideal S-curve is defined as:

$$G_t = G_t + \delta G \cdot a \cdot (f - f_1) + \delta G \cdot b \cdot (f - f_1)^2 + \delta G \cdot c \cdot (f - f_1)^3$$

where

$$\delta G = G_f - G_f$$

f₁ = start frequency

f_n = stop frequency

 $a = 3.1224 \times 10^{-3}$

 $b = 1.9932 \times 10^{-6}$

 $c = -8.934 \times 10^{-9}$

The flatness is the maximum deviation between the measured gain and the 'ideal gain' curve.

Delta gain

DEFINITION

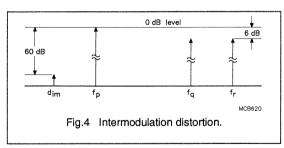
Delta gain is the difference in gain between two given frequencies (mostly the start and stop frequencies).

Intermodulation distortion (d_{im})

In accordance with DIN 45004B 6.3, 3-tone

DEFINITION

The intermodulation distortion product is the difference in dB between the peak of the RF signal in the measuring channel and the peak of the distortion signal caused by the influence of a signal in a neighbouring channel (see Fig.4).



To measure 3-tone d_{im} , three CW signals are applied to the module:

$$\begin{split} f_p &= f & \text{level} = & 0 \text{ dB} \\ f_q &= f + 7 \text{ MHz} & \text{level} = -6 \text{ dB} \\ f_r &= f + 9 \text{ MHz} & \text{level} = -6 \text{ dB} \end{split}$$

The distortion product is measured at f-2 MHz. This distortion product consists of the $(f_p+f_q-f_r)$ beats and is expressed in dB referred to the 0 dB level (the f_p signal level).

This 0 dB level should be chosen so that the distortion product (d_{im}) is -60 dB. For practical reasons the given output level (V_o) for 3-tone distortion is defined as the

General

0 dB level and the modules are rejected if the distortion level is worse than -60 dB.

EQUIPMENT

Spectrum analyzer with settings:

internal attenuator 40 dB resolution bandwidth 3 kHz video bandwidth 100 Hz span 50 kHz.

The three signals are obtained from three different generators (see Appendix A).

Composite third order distortion: composite triple beat (CTB) in CW carriers

In accordance with National Cable Television Association recommendations.

DEFINITION

Composite third order modulation is the amplitude distortion of desired signals, caused by third order curvature of non-linear transfer characteristics in system equipment. It is the ratio, expressed in dB, of the peak level of the RF signal to the peak level of the cluster of distortion components centred around the carrier.

MEASUREMENT

To measure the CTB, a signal at the measuring frequency is set to the specified V_o level. This output level is defined as the 0 dB level. During the measurement⁽¹⁾ all channels in the band are set to the specified V_o level, see Appendix D. Now, at the measuring frequency, the distortion product is measured with a spectrum analyzer or distortion analyzer.

The CTB distortion is measured high in the band because here the distortion products have most

amplitude (although the greatest number of beats ($f_1 \pm f_2$) $\pm f_3$ and $2 \times f_1 \pm f_2$) are found in the centre of the band).

EQUIPMENT

Spectrum analyzer with settings:

resolution bandwidth 30 kHz video bandwidth 100 kHz span 500 kHz.

A bandpass filter is used to eliminate the distortion products caused by the spectrum analyzer itself. If desired, a distortion analyzer can be used instead of the spectrum analyzer.

The carrier signals are obtained from a multi-channel generator. The frequency deviation of each channel must be less than 5 kHz.

Composite third order distortion: cross modulation (X_{mod}) in modulated carriers

DEFINITION

Cross modulation distortion is a form of distortion where modulation of interfering stations appears as a modulation of the desired station, caused by third order curvature of non-linear transfer characteristics in system equipment. It is the ratio, expressed in dB, of the peak level of the modulated RF signal to the peak level of the distortion components centred around the carrier (see Figs 5, 6 and 7).

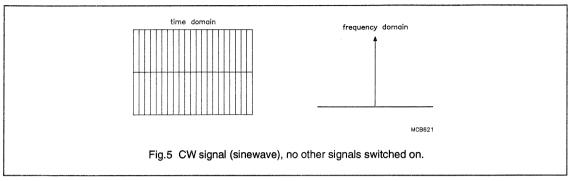
MEASUREMENT

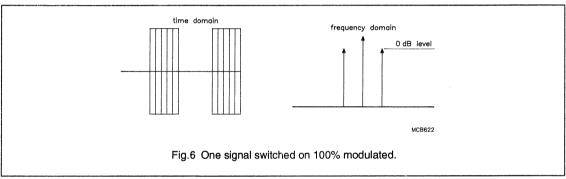
To measure X_{mod}, the carrier of the desired channel is set to the specified V_o level. This channel is then 100% modulated with a 15.75 kHz square wave.⁽²⁾ The peak level of this modulation signal (15.75 kHz on the carrier) is defined as the 0 dB level. The distortion product is now measured by setting each individual CW channel to the specified V_o level and switching them on in modulated

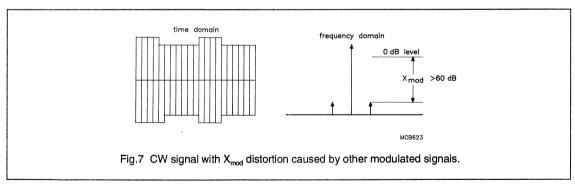
⁽¹⁾ In the USA, an equally spaced frequency raster is used with a space of 6 MHz between the channels. In the German frequency distribution the space between the channels is 7 MHz up to 300 MHz, and 8 MHz above 300 MHz. In general, the Philips measurements are made in accordance with the American frequency raster. For the German market, measurements can be made with a set-up which approximates as closely as possible to the German raster. A list of both rasters is given in Appendix C.

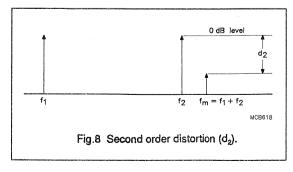
⁽²⁾ The 15.75 kHz square wave modulation signal, used with X_{mod} measurements, found its origin in the American broadcasting method. Using the NTSC system, the 15.75 kHz is defined by the 60 Hz mains frequency and the number of 525 TV lines, i.e. (NTSC) = 60 × 525 + 2 = 15.75 kHz.

The modulation frequency for PAL (one of the European methods) is 15.625 kHz. This is because in Europe the mains frequency is 50 Hz and the number of TV lines using PAL is 625.









General

Wideband Hybrid IC Modules

mode, see Appendix D. Only the carrier in the channel where the $\rm X_{mod}$ distortion is to be measured, is not modulated. The $\rm X_{mod}$ distortion peak now appears as 15.75 kHz on the carrier.

The X_{mod} distortion is most easily measured at the low end of the frequency band.

EQUIPMENT

Bandpass filter:

tuned to the channel in which the distortion product is to be measured.

Spectrum analyzer with settings (for most types):

resolution bandwidth

300 kHz

video bandwidth

30 Hz

span

5 kHz.

A multi-channel generator is required for the test signals.

A distortion analyzer will be required if the X_{mod} is to be measured at a high frequency in the band. This is because phase noise will make spectrum analyzer measurements inaccurate.

Second order distortion (d₂)

In accordance with DIN 45004-A1

DEFINITION

The second order distortion product is the difference in dB between the peak level of an RF signal at the measuring frequency, and the peak level of the signal at the measuring frequency caused by two CW signals with their second order modulation product $(f_1 \pm f_2)$ at the measuring frequency (see Fig.8).

MEASUREMENT

Second order modulation is measured at the frequency in the band where the distortion product is found to be worst. In general this will be at the high end of the band.

In most cases the measuring procedure will be as follows:

Signals f_1 and f_2 are chosen so that f_1 is the lowest channel in the band and f_2 is the highest, this means that $f_1 + f_2$ lays within the band.

The peak levels of $\rm f_1$ and $\rm f_2$ are equal and are defined as the 0 dB level. For frequency sets, see Appendix B.

EQUIPMENT

Spectrum analyzer with settings:

resolution bandwidth

3 kHz

video bandwidth

100 Hz

span

50 kHz.

A tunable bandpass filter is used to eliminate the distortion caused by the spectrum analyzer.

Composite second order (CSO) distortion

DEFINITION

Composite second order distortion is the ratio, expressed in dB, of the peak level, of the RF signal to the peak level of the cluster of distortion components centred around the desired signal. This distortion is caused by a compilation of components of second order intermodulation products of interfering signals with frequencies f_1 and f_2 , so that

 $f_m = f_1 \pm f_2$ or $f_m = 2 \times f_1$ or

 $f_m = 2 \times f_2$.

MEASUREMENT

Measurement is made by setting a signal with the desired frequency to the specified level for V_{\circ} . This V_{\circ} level is defined as the 0 dB level.

During the measurement, all channels in the band are levelled to the specified $V_{\rm o}$. Now at the measurement frequency, the distortion product is measured by use of a spectrum analyzer.

The CSO distortion is measured high in the band because it is here that this distortion product has most influence, see Appendix D.

EQUIPMENT

Spectrum analyzer with settings:

resolution bandwidth

30 kHz

video bandwidth

100 Hz

span

400 kHz.

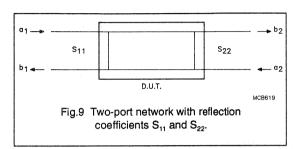
A bandpass filter is used at the input of the spectrum analyzer.

S-parameters S₁₁ and S₂₂ (return losses)

In accordance with IEC 747-7

DEFINITION

The return losses or reflection coefficients of a module can be defined as the S_{11} and the S_{22} of a two-port network (see Fig.9).



$$b_1 = S_{11} \cdot a_1 + S_{12} \cdot a_2 \tag{1}$$

$$b_2 = S_{21} \cdot a_1 + S_{22} \cdot a_2 \tag{2}$$

where

$$a_1 = \frac{1}{2 \cdot \sqrt{Z_o}} \cdot (V_1 + Z_o \cdot I_1) = \text{signal into port 1}$$
 (3)

$$a_2 = \frac{1}{2 \cdot \sqrt{Z}} \cdot (V_2 + Z_o \cdot i_2) = \text{signal into port 2}$$
 (4)

$$b_1 = \frac{1}{2 \cdot \sqrt{Z_o}} \cdot (V_1 + Z_o \cdot i_1) = \text{signal out of port 1}$$

$$b_2 = \frac{1}{2 \cdot \sqrt{Z_o}} \cdot (V_2 + Z_o \cdot i_2) = \text{signal out of port 2}$$

From (1) and (2) formulae for the return losses can be derived:

$$S_{11} = \frac{b_1}{a} \mid a_2 = 0 \tag{5}$$

$$S_{22} = \frac{b_2}{a_2} \mid a_1 = 0 \tag{6}$$

In (5), $a_2 = 0$ means output port terminated with Z_0 (derived from formula (4)).

In (6), $a_1 = 0$ means input port terminated with Z_o (derived from formula (3)).

MEASUREMENT

The return losses are measured with a network analyzer after calibration, where the influence of the test jig is

eliminated. The necessary termination of the other port with Z_0 is done automatically by the network analyzer.

The network analyzer must have a directivity of at least 40 dB to obtain an accuracy of 0.5 dB when measuring return loss figures of 20 dB. A full two-port correction method can be used to improve the accuracy.

Noise figure (F)

In accordance with IEC 747-7

DEFINITION

The noise figure is defined as the ratio of the total available noise power output from the module when connected to a noise source to that which is generated solely by the noise source.

MEASUREMENT

Noise figure is measured with a noise figure meter at the output of the module, while a noise source is connected to the input of the module. Measurements should be done in an electrically-shielded room to prevent pick-up of unwanted signals.

MOUNTING and SOLDERING RECOMMENDATIONS

Mounting

The heatsink surface must be flat, free of burrs, oxidation and parallel to the mounting surface.

The heatsink, mounting base and ground leads should be properly RF grounded.

Heatsink compound should be applied sparingly and evenly on the mounting base. Suitable heatsink compounds are Dow Corning 340, Eccotherm TC-5 (E&C) and Wakefield 120.

When mounting CATV hybrid components, the UNC screws must first be turned finger-tight. The screws should then be tightened to within the tolerance 0.5 Nm minimum and 0.7 Nm maximum.

Soldering

Devices may be soldered directly into a circuit using a soldering iron with a maximum temperature of 260 °C for not more than 3 s when the soldered joints are a minimum of 3 mm from the module.

General

APPENDIX A - COMMON FREQUENCY SETS for dim MEASUREMENTS

f _m (MHz)	f _p (MHz)	f _q (MHz)	f, (MHz)
33.25	35.25	42.25	44.25
163.25	165.25	172.25	174.25
185.25	187.25	194.25	196.25
285.25	287.25	294.25	296.25
335.25	337.25	344.25	346.25
339.25	341.25	348.25	350.25
385.25	387.25	394.25	396.25
438.25	440.25	447.25	449.25
481.25	483.25	490.25	492.25
538.25	540.25	547.25	549.25
849.25	851.25	858.25	860.25

APPENDIX B - COMMON FREQUENCY SETS for d₂ MEASUREMENTS

f _p (MHz)	f _q (MHz)		f _m (MHz)	
83.25	109.25	1 1	192.50	
66.00	144.00		210.00	
55.25	211.25		266.50	
55.25	343.35	14/2	398.50	
55.25	391.25		446.50	
55.25	493.25	Villa de	548.50	
300.00	450.00	The p	750.00	

APPENDIX C - LIST of FREQUENCY RASTERS for USA and GERMANY

Us	SA .
CHANNEL	FREQUENCY (MHz)
2	55.25
3	61.25
4	67.25
5	77.25
6	83.25
A2	109.25
A1	115.25
Α .	121.25
В	127.25
С	133.25
D	139.25
E3	145.25
F	151.25
G	157.25
Н	163.25
1	169.25
7	175.25
8	181.25
9	187.25
10	193.25
11	199.25
12	205.25
13	211.25
J	217.25
K	223.25
L	229.25
M	235.25
N	241.25
0	247.25
P	253.25
Q	259.25
R	265.25
s	271.25
Т	277.25
U	283.25
V	289.25

USA			
CHANNEL	FREQUENCY (MHz)		
W	295.25		
X	301.25		
Y	307.25		
4 / Z	313.25		
·H1	319.25		
H2	325.25		
H3	331.25		
⊬ H4	337.25		
H5	343.25		
H6	349.25		
H7	355.25		
H8	361.25		
. H9	367.25		
H10	373.25		
H11	379.25		
H12	385.25		
H13	391.25		
H14	397.25		
H15	403.25		
H16	409.25		
H17	415.25		
H18	421.25		
H19	427.25		
H20	433.25		
H21	439.25		
H22	445.25		
H23	451.25		
H24	457.25		
H25	463.25		

General

APPENDIX C (continued)

USA		
CHANNEL	FREQUENCY (MHz)	
14	469.25	
15	475.25	
16	481.25	
17	487.25	
18	493.25	
19	499.25	
20	505.25	
21	511.25	
22	517.25	
23	523.25	
24	529.25	
25	535.25	
26	541.25	
27	547.25	
28	553.25	
29	559.25	
30	565.25	
31	571.25	
32	577.25	
33	583.25	
34	589.25	
35	595.25	
36	601.25	
37	607.25	
38	461.25	
39	619.25	
40	625.25	
41	631.25	
42	637.25	
43	643.25	
44	649.25	
45	655.25	
46	661.25	
47	667.25	
48	673.25	
49	679.25	
50	685.25	

USA		
CHANNEL	FREQUENCY (MHz)	
51.2 %	691.25	
52	697.25	
53 44	703.25	
* 54 ****	709.25	
55	715.25	
56	721.25	
57	727.25	
58	733.25	
59	739.25	
60	745.25	
61	751.25	
62	757.25	
63	763.25	
64 , 1944	769.25	
65	775.25	
66 🔑 👙	781.25	
67	787.25	
68	793.25	
69	799.25	
70, . *	805.25	
71	811.25	
72	817.25	
73	823.25	
74	829.25	
75	835.25	
76	841.25	
77	847.25	
78	853.25	
79	859.25	
80	865.25	
81	871.25	
82	877.25	
83	883.25	
84	889.25	
85	895.25	

APPENDIX C (continued)

GERM	IANY
CHANNEL	FREQUENCY (MHz)
K2	48.25
кз	55.25
K4	62.25
_	69.25
_	76.25
S2	112.25
S3	119.25
S4	126.25
S5	133.25
S6	140.25
S7	147.25
S8	154.25
S10	168.25
K5	175.25
K6	182.25
K7	189.25
K8	196.25
K9	203.25
K10	210.25
K11	217.25
K12	224.25
S11	231.25
S12	238.25
S13	245.25
S14	252.25
S15	259.25
S16	266.25
S17	273.25
S18	280.25
S19	287.25
S20	294.25
S21	303.25
S22	311.25
S23	319.25
S24	327.25
S25	335.25
S26	343.25

GERMANY		
CHANNEL	FREQUENCY (MHz)	
S27	351.25	
S28	259.25	
S29	367.25	
S30	375.25	
S31	383.25	
S32	391.25	
S33	399.25	
S34	407.25	
S35	415.25	
S36	423.25	
S37	431.25	
S38	439.25	
S39	445.25	

General

APPENDIX D - TEST CHANNELS

Channels used during CTB, X_{mod} and CSO measurements

RANGE NAMES FREQUENC		FREQUENCIES (MHz)	CHANNELS
40 - 300 MHz	2-4	55.25 - 67.25	3 channels
32 channels	5-6	77.25 - 83.25	2 channels
	A-2	109.25	1 channel
	A-F	121.25 - 151.25	6 channels
	H-S	163.25 - 271.25	19 channels
	W	295.25	1 channel
40 - 450 MHz	2-4	55.25 - 67.25	3 channels
52 channels	5-6	77.25 - 83.25	2 channels
	A-2	109.25	1 channel
	A-F	121.25 - 151.25	6 channels
	H-H14	163.25 - 397.25	40 channels
5 - 200 MHz	T7-T13	7.00 - 43.00	7 channels
22 channels	2-4	55.25 - 67.25	3 channels
	5-6	77.25 - 83.25	2 channels
	A-7	121.25 - 175.25	10 channels
40 - 450 MHz	2-4	55.25 - 67.25	3 channels
60 channels	5-6	77.25 - 83.25	2 channels
	A-H22	121.25 - 445.25	55 channels
40 - 550 MHz	2-4	55.25 - 67.25	3 channels
82 channels	5-6	77.25 - 83.25	2 channels
	A-27	121.25 - 547.25	77 channels
40 - 600 MHz	2-4	55.25 - 67.25	3 channels
85 channels	5-6	77.25 - 83.25	2 channels
	A-35	121.25 - 595.25	80 channels
40 - 750 MHz	2-4	55.25 - 67.25	3 channels
110 channels	5-6	77.25 - 83.25	2 channels
	A-60	121.25 - 745.25	105 channels
40 - 860 MHz	2-4	55.25 - 67.25	3 channels
129 channels	5-6	77.25 - 83.25	2 channels
	A-79	121.25 - 859.25	124 channels
40 - 450 MHz	2-3	55.25 - 61.25	2 channels
36 channels	C-F	133.25 - 151.25	4 channels
German raster	Н	163.25	1 channel
	7	175.25	1 channel
	9	187.25	1 channel
	12	205.25	1 channel
	J	217.25	1 channel
	L-M	229.25 - 235.25	2 channels

DEVICE DATACATV amplifier modules

CATV power doubler amplifier modules

BGD102/104

FEATURES

- · Excellent linearity
- · High output level
- · Silicon nitride passivation
- · Rugged construction
- Optimal reliability ensured by TiPtAu metallized crystals.

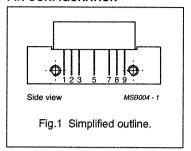
DESCRIPTION

Power doubler amplifier modules for CATV systems operating over a frequency range of 40 to 450 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz			
	BGD102		18	19	dB
	BGD104		19.5	20.5	dB
		f = 450 MHz			
	BGD102		19.2	21.2	dB
	BGD104		20.5	22.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	435	mA

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	65	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

CATV power doubler amplifier modules

BGD102/104

CHARACTERISTICS

Bandwidth 40 to 450 MHz; T_{mb} = 35 °C; Z_{S} = Z_{L} = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz			
Ρ	BGD102		18	19	dB
	BGD104		19.5	20.5	dB
		f = 450 MHz			
	BGD102		19.2	21.2	dB
	BGD104		20.5	22.5	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.5	2.5	dB
FL	flatness of frequency response	f = 40 to 450 MHz	-	± 0.3	dB
S ₁₁	input return losses	f = 40 to 450 MHz	18	-	dB
S ₂₂	output return losses	f = 40 to 450 MHz	18	_	dB
СТВ	composite triple beat	60 chs flat; $V_o = 46 \text{ dBmV}$; measured at 445.25 MHz			
	BGD102		-	-65	dB
	BGD104			-64	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz			
	BGD102		-	-67	dB
	BGD104		-	-66	dB
d ₂	second order distortion	note 1	-	73	dB
V _o	output voltage	d _{im} = -60 dB note 2			
	BGD102		65	-	dBmV
	BGD104		64.5	_	dBmV
F	noise figure	f = 40 to 450 MHz		7	dB
tot	total current consumption	DC value; V _B = +24 V note 3	_	435	mA

Notes

1. $f_p = 55.25 \text{ MHz}$; $V_o = 46 \text{ dBmV}$; $f_q = 343.25 \text{ MHz}; V_q = 46 \text{ dBmV};$ measured at $f_p + f_q = 398.5$ MHz.

2. Measured according to DIN45004B;

$$\begin{split} &f_p = 440.25 \text{ MHz; } V_p = V_o; \\ &f_q = 447.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \end{split}$$

 $f_r = 449.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$ measured at $f_p + f_q - f_r = 438.25 \text{ MHz}.$

3. The modules normally operate at $V_B = +24 \text{ V}$, but are able to withstand supply transients up to 30 V.

CATV power doubler amplifier module

BGD106

FEATURES

- Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

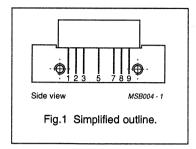
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 40 to 450 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	21.5	22.5	dB
		f = 450 MHz	22.1	-	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	-	435	mA

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

CATV power doubler amplifier module

BGD106

CHARACTERISTICS

Bandwidth 40 to 450 MHz; $\rm T_{case}$ = 35 °C; $\rm Z_{S}$ = $\rm Z_{L}$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	21.5	22.5	dB
P		f = 450 MHz	22.1	-	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0	2	dB
FL	flatness of frequency response	f = 40 to 450 MHz	_	± 0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	_	20	dB
		f = 80 to 160 MHz;	-	19	dB
		f = 160 to 450 MHz	-	18	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	-	20	dB
22	·	f = 80 to 160 MHz;	-	19	dB
		f = 160 to 450 MHz	-	18	dB
СТВ	composite triple beat	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz	_	-63	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz	_	-63	dB
CSO	composite second order distortion	60 chs flat; V _o = 46 dBmV; measured at 446.5 MHz	_	-59	dB
d ₂	second order distortion	V _o = 46 dBmV note 1	-	-68	dB
V _o	output voltage	d _{im} = -60 dB note 2	66.5	_	dBmV
F	noise figure	f = 450 MHz	_	6.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V; note 3	-	435	mA

Notes

- 1. f_p = 55.25 MHz; V_p = 46 dBmV; f_q = 391.25 MHz; V_q = 46 dBmV; measured at f_p + f_q = 446.5 MHz
- 2. Measured according to DIN45004B;

 $f_p = 440.25 \text{ MHz}; V_p = V_o = 66.5 \text{ dBmV};$ $f_q = 447.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$

 $f_r = 449.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$

3. The module normally operates at $V_B = +24 \text{ V}$, but is able to withstand supply transients up to +30 V.

BGD108

FEATURES

- · Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- Gold metallization ensures excellent reliability.

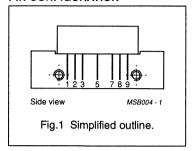
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 40 to 450 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	35	37	dB
		f = 450 MHz	36.5	_	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	625	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	55	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	–20	+100	°C

BGD108

CHARACTERISTICS

 $T_{case} = 35 \, ^{\circ}C; Z_{S} = Z_{L} = 75 \, \Omega;$ Bandwidth 40 to 450 MHz; $V_{B} = +24 \, V.$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	35	37	dB
۲		f = 450 MHz	36.5	_	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.2	2.2	dB
FL	flatness of frequency response	f = 40 to 450 MHz	T-	± 0.4	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	_	dB
.,	·	f = 80 to 160 MHz;	19	-	dB
		f = 160 to 450 MHz	18	_	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	_	dB
22	·	f = 80 to 160 MHz;	19	-	dB
		f = 160 to 450 MHz	18	_	dB
СТВ	composite triple beat	60 chs flat;	-	-64	dB
	' '	V _o = 46 dBmV; measured at 445.25 MHz			
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz	-	-65	dB
CSO	composite second order distortion	60 chs flat; V _o = 46 dBmV; measured at 446.5 MHz	_	-62	dB
d ₂	second order distortion	note 1	-	-73	dB
V _o	output voltage	d _{im} = -60 dB note 2	67	-	dBmV
F	noise figure	f = 450 MHz	-	7	dB
I _{tot}	total current consumption	DC value; V _B = +24 V		625	mA

- 1. $f_p = 55.25$ MHz; $V_p = 46$ dBmV; $f_q = 391.25$ MHz; $V_q = 46$ dBmV; measured at $f_p + f_q = 446.5$ MHz
- 2. $f_p = 440.25 \text{ MHz}; V_p = V_o;$ $f_q = 447.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$ $f_r = 449.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$ measured at $f_p + f_q - f_r = 438.25 \text{ MHz}.$

CATV power doubler amplifier modules

BGD502;BGD504

FEATURES

- Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- Rugged construction
- Optimal reliability ensured by TiPtAu metallized crystals.

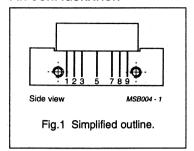
DESCRIPTION

Hybrid amplifier modules for CATV systems operating over a frequency range of 40 to 550 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz			
	BGD502		18	19	dB
	BGD504		19.5	20.5	dB
		f = 550 MHz			
	BGD502		18.8	20.8	dB
	BGD504		20.2	22.2	dB
I _{tot}	total current	DC value;	_	435	mA
	consumption	$V_B = +24 \text{ V}$			

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{case}	operating case temperature range	-20	+100	°C

CATV power doubler amplifier modules

BGD502;BGD504

CHARACTERISTICS

Bandwidth 40 to 550 MHz; $\rm T_{case}$ = 35 °C; $\rm Z_{S}$ = $\rm Z_{L}$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz				
P	BGD502		18	_	19	dB
	BGD504		19.5	-	20.5	dB
		f = 550 MHz				
	BGD502		18.8	_	20.8	dB
	BGD504		20.2	_	22.2	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0.2	-	2.2	dB
FL	flatness of frequency response	f = 40 to 550 MHz	. –	-	± 0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	_	 -	dB
••		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 550 MHz	18	-	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	 -	_	dB
22	•	f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 550 MHz	18	-	-	dB
СТВ	composite triple beat	77 chs flat; V _o = 44 dBmV; measured at 547.25 MHz				
	BGD502		_	_	-65	dB
	BGD504		-	-	-64	dB
X _{mod}	cross modulation	77 chs flat; V _o = 44 dBmV; measured at 55.25 MHz				
	BGD502		-	-	-68	dB
	BGD504		_	-	67	dB
d ₂	second order distortion	note 1				
	BGD502		-	-	-72	dB
	BGD504			<u> </u>	-70	dB
V _o	output voltage	d _{im} = -60 dB note 2				
	BGD502		64	-	-	dBmV
	BGD504		63.5	-		dBmV
F	noise figure	f = 550 MHz	-	_	8	dB
I _{tot}	total current consumption	DC value; V _B = +24 V; note 3	_	415	435	mA

CATV power doubler amplifier modules

BGD502;BGD504

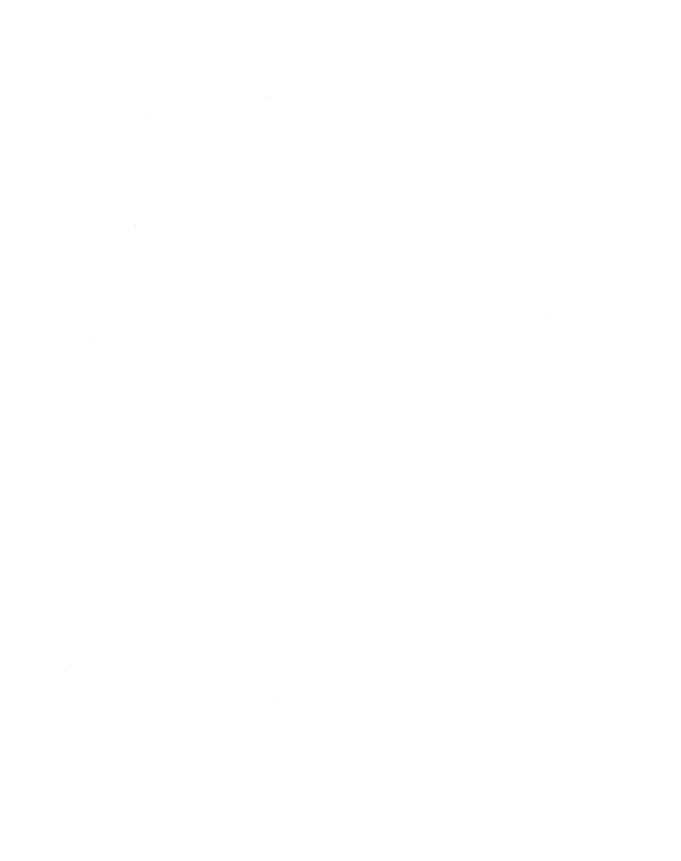
Notes

 $f_{q}^{I} = 493.25 \text{ MHz}; V_{q} = 44 \text{ dBmV};$ measured at $f_{p} + f_{q} = 548.5 \text{ MHz}$ 2. Measured according to DIN45004B; $f_{p} = 540.25 \text{ MHz}; V_{p} = V_{o};$ $f_{q} = 547.25 \text{ MHz}; V_{q} = V_{o} - 6 \text{ dB};$ $f_{r} = 549.25 \text{ MHz}; V_{r} = V_{o} - 6 \text{ dB};$

measured at $f_p + f_q - f_r = 538.25 \text{ MHz}$

1. $f_p = 55.25 \text{ MHz}$; $V_p = 44 \text{ dBmV}$;

3. The modules normally operate at $V_B = +24 \text{ V}$, but are able to withstand supply transients up to 30 V.



BGD506

FEATURES

- Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

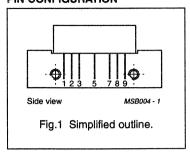
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 40 to 550 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	21.5	22.5	dB
		f = 550 MHz	22.1	-	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	-	435	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
Vi	RF input voltage	-	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	ů
V _B	DC supply voltage	_	+28	٧

BGD506

CHARACTERISTICS

Bandwidth 40 to 550 MHz; T_{case} = 35 °C; Z_{S} = Z_{L} = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	21.5	22.5	dB
		f = 550 MHz	22.1	-	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0	2	dB
FL	flatness of frequency response	f = 40 to 550 MHz	-	± 0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	_	20	dB
		f = 80 to 160 MHz;	-	19	dB
		f = 160 to 550 MHz	-	18	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	_	20	dB
		f = 80 to 160 MHz;	_	19	dB
		f = 160 to 550 MHz	_	18	dB
СТВ	composite triple beat	77 chs flat; V _o = 44 dBmV; measured at 547.25 MHz	-	-62	dB
X _{mod}	cross modulation	77 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	-	-63	dB
CSO	composite second order distortion	77 chs flat; V _o = 44 dBmV; measured at 548.5 MHz	-	-55	dB
d ₂	second order distortion	V _o = 44 dBmV; note 1	-	-66	dB
V _o	output voltage	d _{im} = -60 dB note 2	62.5	-	dBmV
F	noise figure	f = 550 MHz	-	6.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V; note 3	-	435	mA

Notes

- 1. f_p = 55.25 MHz; V_p = 44 dBmV; f_q = 493.25 MHz; V_q = 44 dBmV; measured at f_p + f_q = 548.5 MHz
- 2. Measured according to DIN45004B;

 $f_p = 540.25 \text{ MHz}; V_o = V_p;$ $f_q = 547.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$ $f_r = 549.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$ measured at $f_p + f_q - f_r = 538.25 \text{ MHz}$ $V_o = 62.5 \text{ dBmV}.$

3. The module normally operates at $V_B = +24 \text{ V}$, but is able to withstand supply transients up to +30 V.

BGD508

FEATURES

- Excellent linearity
- Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- Gold metallization ensures excellent reliability.

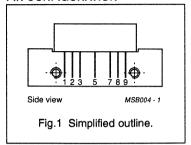
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 40 to 550 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C.

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
. 8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	35	37	dB
		f = 550 MHz	36.5		dB
I _{tot}	total current consumption	DC value; V _B = +24 V	-	625	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	_	55	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	ç

BGD508

CHARACTERISTICS

 $T_{case} = 35$ °C; $Z_{S} = Z_{L} = 75 \Omega$; Bandwidth 40 to 550 MHz; $V_{B} = +24 V$.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	35	37	dB
		f = 550 MHz	36.5	-	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0.2	2.2	dB
FL	flatness of frequency response	f = 40 to 550 MHz	-	± 0.4	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 550 MHz	18	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 550 MHz	18	_	dB
СТВ	composite triple beat	77 chs flat; V _o = 44 dBmV; measured at 547.25 MHz	-	-62	dB
X _{mod}	cross modulation	77 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	-	-65	dB
CSO	composite second order distortion	V _o = 44 dBmV; measured at 548.5 MHz	-	-58	dB
d ₂	second order distortion	note 1	_	-70	dB
V _o	output voltage	d _{im} = -60 dB note 2	63	-	dBmV
F	noise figure	f = 550 MHz	-	7.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	625	mA

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Notes

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1. f_p = 55.25 \text{ MHz}; V_p = 46 \text{ dBmV};

f_q = 393.25 \text{ MHz}; V_q = 46 \text{ dBmV};

measured at f_p + f_q = 548.5 \text{ MHz}
```

2. $f_p = 440.25$ MHz; $V_p = V_o$; $f_q = 447.25$ MHz; $V_q = V_o -6$ dB; $f_r = 449.25$ MHz; $V_r = V_o -6$ dB; measured at $f_p + f_q - f_r = 438.25$ MHz.

BGD601

FEATURES

- · Excellent linearity
- · Extremely low noise
- Silicon nitride passivation
- · Rugged construction
- Gold metallization ensures excellent reliability.

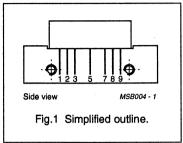
DESCRIPTION

Hybrid high dynamic range amplifier module for CATV systems operating over a frequency range of 40 to 600 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	12	13	dB
		f = 600 MHz	12.7	_	dB
I _{tot}	total current consumption	DC value; V _R = +24 V	-	435	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
Vi	RF input voltage	-	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGD601

CHARACTERISTICS

Bandwidth 40 to 600 MHz; $T_{case} = 35$ °C; $Z_{S} = Z_{L} = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	12	13	dB
		f = 600 MHz	12.7	_	dB
SL	slope cable equivalent	f = 40 to 600 MHz	0.2	2.2	dB
FL	flatness of frequency response	f = 40 to 600 MHz	_	± 0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	_	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 600 MHz	18	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	19	_	dB
		f = 160 to 600 MHz	18	-	dB
СТВ	composite triple beat	85 chs flat; V _o = 44 dBmV; measured at 595.25 MHz	_	-62	dB
X _{mod}	cross modulation	85 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	_	-66	dB
CSO	composite second order distortion	85 chs flat; V _o = 44 dBmV; measured at 596.5 MHz	-	-60	dB
d ₂	second order distortion	note 1	_	-70	dB
V _o	output voltage	d _{im} = -60 dB note 2	63	_	dBmV
F	noise figure	f = 600 MHz	-	9.5	dB
l _{tot}	total current consumption	DC value; V _B = +24 V		435	mA

- 1. $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 541.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 596.5$ MHz
- $\begin{array}{lll} \text{2.} & f_{p} = 590.25 \text{ MHz; } V_{p} = V_{o}; \\ f_{q} = 597.25 \text{ MHz; } V_{q} = V_{o} 6 \text{ dB;} \\ f_{r} = 599.25 \text{ MHz; } V_{r} = V_{o} 6 \text{ dB;} \\ \text{measured at } f_{p} + f_{q} f_{r} = 588.25 \text{ MHz.} \\ \end{array}$

BGD601

CHARACTERISTICS

Bandwidth 40 to 550 MHz; $T_{case} = 35$ °C; $Z_{S} = Z_{L} = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	12	13	dB
		f = 550 MHz	12.5	14.5	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0.2	2	dB
FL	flatness of frequency response	f = 40 to 550 MHz	-	± 0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	_	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 550 MHz	18	_	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	_	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 550 MHz	18	_	dB
СТВ	composite triple beat	77 chs flat; V _o = 44 dBmV; measured at 547.25 MHz	_	65	dB
X _{mod}	cross modulation	77 chs flat; V _o = 44 dBmV; measured at 55.25 MHz		-68	dB
CSO	composite second order distortion	85 chs flat; V _o = 44 dBmV; measured at 548.5 MHz	_	-64	dB
d ₂	second order distortion	note 1	-	-72	dB
V _o	output voltage	d _{im} = -60 dB note 2	64	_	dBmV
F	noise figure	f = 550 MHz	-	9	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	435	mA

- 1. $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 493.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 548.5$ MHz
- $\begin{array}{lll} \text{2.} & f_p = 540.25 \text{ MHz; } V_p = V_o; \\ & f_q = 547.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \\ & f_r = 549.25 \text{ MHz; } V_r = V_o -6 \text{ dB;} \\ & \text{measured at } f_p + f_q f_r = 538.25 \text{ MHz.} \end{array}$

BGD601

CHARACTERISTICS

Bandwidth 40 to 450 MHz; $T_{case} = 35$ °C; $Z_{S} = Z_{L} = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	12	13	dB
·		f = 450 MHz	12.5	-	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.2	1.5	dB
FL	flatness of frequency response	f = 40 to 450 MHz	-	± 0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	_	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 450 MHz	18	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	_	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 450 MHz	18	-	dB
СТВ	composite triple beat	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz	-	–67	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz	-	- 67	dB
CSO	composite second order distortion	60 chs flat; V _o = 46 dBmV; measured at 446.5 MHz	-	-65	dB
d ₂	second order distortion	note 1	-	-75	dB
V _o	output voltage	d _{im} = -60 dB note 2	67	-	dBmV
F	noise figure	f = 450 MHz	-	8	dB
l _{tot}	total current consumption	DC value; V _B = +24 V	-	435	mA

- 1. $f_p = 55.25$ MHz; $V_p = 46$ dBmV; $f_q = 391.25$ MHz; $V_q = 46$ dBmV; measured at $f_p + f_q = 446.5$ MHz
- $\begin{array}{lll} \text{2.} & f_p = 440.25 \text{ MHz; } V_p = V_o; \\ f_q = 447.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \\ f_r = 449.25 \text{ MHz; } V_r = V_o -6 \text{ dB;} \\ \text{measured at } f_p + f_q f_r = 438.25 \text{ MHz.} \\ \end{array}$

BGD602

FEATURES

- Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- Gold metallization ensures excellent reliability.

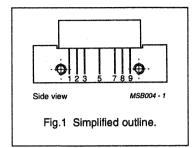
DESCRIPTION

Hybrid high dynamic range amplifier module designed for applications in CATV systems with a bandwidth of 40 MHz to 600 MHz operating with a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	18	19	dB
		f = 600 MHz	19	_	dB
l _{tot}	total current consumption	DC value; V _B = +24 V	_	435	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGD602

CHARACTERISTICS

Bandwidth 40 to 600 MHz; T_{case} = 35 °C; Z_S = Z_L = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	18	19	dB
		f = 600 MHz	19	-	dB
SL	slope cable equivalent	f = 40 to 600 MHz	0.2	2.2	dB
FL	flatness of frequency response	f = 40 to 600 MHz	_	± 0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 600 MHz	18	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 600 MHz	18	-	dB
СТВ	composite triple beat	85 chs flat; V _o = 44 dBmV; measured at 595.25 MHz	_	-62	dB
X _{mod}	cross modulation	85 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	_	-66	dB
CSO	composite second order distortion	85 chs flat; $V_o = 44 \text{ dBmV}$; measured at 596.5 MHz	_	-60	dB
d ₂	second order distortion	note 1	-	-70	dB
V _o	output voltage	d _{im} = -60 dB note 2	63	_	dBmV
F	noise figure	f = 600 MHz	_	8	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	435	mA

Notes

1. $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 541.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 596.5$ MHz

2. $f_p = 590.25 \text{ MHz}$; $V_p = V_o$; $f_q = 597.25 \text{ MHz}$; $V_q = V_o -6 \text{ dB}$; $f_r = 599.25 \text{ MHz}$; $V_r = V_o -6 \text{ dB}$; measured at $f_p + f_q - f_r = 588.25 \text{ MHz}$.

BGD602

CHARACTERISTICS

Bandwidth 40 to 550 MHz; $T_{case} = 35$ °C; $Z_{S} = Z_{L} = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	18	19	dB
		f = 550 MHz	18.8	-	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0.2	2.2	dB
FL	flatness of frequency response	f = 40 to 550 MHz	-	± 0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	_	dB
	·	f = 80 to 160 MHz;	19	-	dB
		f = 160 to 550 MHz	18	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 550 MHz	18	_	dB
СТВ	composite triple beat	77 chs flat; V _o = 44 dBmV; measured at 547.25 MHz	-	-66	dB
X _{mod}	cross modulation	77 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	-	68	dB
CSO	composite second order distortion	77 chs flat; V _o = 44 dBmV; measured at 548.5 MHz	-	-62	dB
d ₂	second order distortion	note 1	-	-72	dB
V _o	output voltage	d _{im} = -60 dB note 2	64	-	dBmV
F	noise figure	f = 550 MHz	-	7.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	435	mA

- 1. $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 493.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 548.5$ MHz
- $\begin{array}{lll} \text{2.} & f_p = 540.25 \text{ MHz; } V_p = V_o; \\ & f_q = 547.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \\ & f_r = 549.25 \text{ MHz; } V_r = V_o -6 \text{ dB;} \\ & \text{measured at } f_p + f_q f_r = 538.25 \text{ MHz.} \\ \end{array}$

BGD602

CHARACTERISTICS

Bandwidth 40 to 450 MHz; $T_{case} = 35$ °C; $Z_S = Z_L = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	18	19	dB
		f = 450 MHz	18.6	_	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.2	1.8	dB
FL	flatness of frequency response	f = 40 to 450 MHz	_	± 0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 450 MHz	18	_	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	19	- ,	dB
		f = 160 to 450 MHz	18	_	dB
СТВ	composite triple beat	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz		-67	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz	_	66	dB
d ₂	second order distortion	note 1	-	-75	dB
V _o	output voltage	d _{im} = -60 dB note 2	67	-	dBmV
F	noise figure	f = 450 MHz	_	7	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	435	mA

- 1. $f_p = 55.25$ MHz; $V_p = 46$ dBmV; $f_q = 391.25$ MHz; $V_q = 46$ dBmV; measured at $f_p + f_q = 446.5$ MHz
- 2. $f_p = 440.25 \text{ MHz}; V_p = V_o;$ $f_q = 447.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$ $f_r = 449.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$ measured at $f_p + f_q - f_r = 438.25 \text{ MHz}.$

BGD702

FEATURES

- Excellent linearity
- Extremely low noise
- · Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

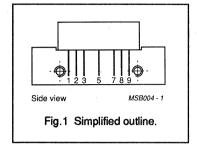
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 40 to 750 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1 .	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	18	19	dB
		f = 750 MHz	18.5	-	dB
l _{tot}	total current consumption	DC value; V _B = +24 V	-	435	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGD702

CHARACTERISTICS

 $T_{case} \,=\, 35~^{\circ}C;\, Z_{S} \,=\, Z_{L} \,=\, 75~\Omega;$ Bandwidth 40 to 750 MHz.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	18	19	dB
r		f = 750 MHz	18.5	-	dB
SL	slope cable equivalent	f = 40 to 750 MHz	0	1.5	dB
FL	flatness of frequency response	f = 40 to 750 MHz	-	± 0.5	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	-	dB
	NAME OF THE PROPERTY OF THE PR	f = 80 to 160 MHz;	18.5	-	dB
	Acceptance of the second secon	f = 160 to 320 MHz	17	.	dB
		f = 320 to 640 MHz;	15.5	-	dB
		f = 640 to 750 MHz	14	_	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	18.5		dB
		f = 160 to 320 MHz	17	-	dB
		f = 320 to 640 MHz;	15.5	_	dB
		f = 640 to 750 MHz	14	-	dB
СТВ	composite triple beat	110 chs flat; V _o = 44 dBmV; measured at 745.25 MHz		-58	dB
X _{mod}	cross modulation	110 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	-	-62	dB
CSO	composite second order distortion	110 chs flat; V _o = 44 dBmV; measured at 746.5 MHz	-	-58	dB
d ₂	second order distortion	note 1	-	-68	dB
V _o	output voltage	d _{im} = -60 dB note 2	61	_	dBmV
F	noise figure	f = 750 MHz	-	9	dB
l _{tot}	total current consumption	DC value; V _B = +24 V	-	435	mA

Notes

1. $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 691.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 746.5$ MHz

2. $f_p = 740.25 \text{ MHz}$; $V_p = V_o$; $f_q = 747.25 \text{ MHz}$; $V_q = V_o -6 \text{ dB}$; $f_r = 749.25 \text{ MHz}$; $V_r = V_o -6 \text{ dB}$; measured at $f_p + f_q - f_r = 738.25 \text{ MHz}$.

BGD885

FEATURES

- Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- Gold metallization ensures excellent reliability.

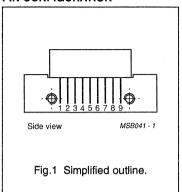
DESCRIPTION

Hybrid amplifier module for CATV/MATV systems operating over a frequency range of 40 MHz to 860 MHz at a voltage supply of +24 V (DC).

PINNING -SOT115D

PIN	DESCRIPTION
1	input
2	common
3	common
4	10 V - 200 mA supply terminal
5	common
6	common
7	common
8	+V _B
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	at 50 MHz	16.5	17.5	dB
I _{tot}	total current consumption		-	450	mA
		$V_B = +24 \text{ V}$			

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	_	60	dBmV
T _{stg}	storage temperature range	-40	100	°C
T _{mb}	mounting base operating temperature range	-20	100	°C
V _B	DC supply voltage	_	26	٧

BGD885

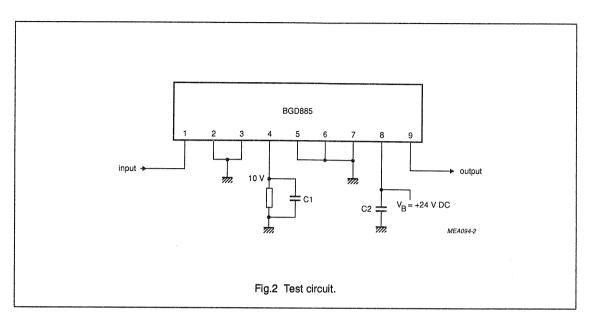
CHARACTERISTICS

 $T_{mb} = 30 \, ^{\circ}\text{C}; \, Z_{S} = Z_{L} = 75 \, \Omega.$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	at 50 MHz	16.5	17.5	dB
SL	slope cable equivalent	f = 40 to 860 MHz	0.2	1.6	dB
FL	flatness of frequency response	f = 40 to 860 MHz	-	±0.5	dB
S ₁₁	input return losses	f = 40 MHz (note 1) f = 800 to 860 MHz	20 10	-	dB dB
S ₂₂	output return losses	f = 40 MHz (note 1) f = 800 to 860 MHz	20 10	_	dB dB
d ₂	second order distortion	note 2	-	-53	dB
V _o	output voltage	d _{im} = -60 dB note 3	64	_	dBmV
		d _{im} = -60 dB note 4	63	_	dBmV
F	noise figure	f = 860 MHz	_	8	dB
l _{tot}	total current consumption	DC value; V _B = 24 V	_	450	mA

- 1. Decrease per octave of 1.5 dB.
- $\begin{array}{ll} \text{2.} & \text{V}_p = 59 \text{ dBmV at } f_p = 349.25 \text{ MHz}; \\ \text{V}_q = 59 \text{ dBmV at } f_q = 403.25 \text{ MHz}; \\ \text{measured at } f_p + f_q = 752.5 \text{ MHz}. \end{array}$
- $\begin{array}{lll} 3. & f_p = 341.25 \text{ MHz; } V_p = V_o \\ & f_q = 348.25 \text{ MHz; } V_q = V_o -6 \text{ dB} \\ & f_r = 350.25 \text{ MHz; } V_r = V_o -6 \text{ dB} \\ & \text{measured at } f_p + f_q f_r = 339.25 \text{ MHz.} \end{array}$
- $\begin{array}{ll} \text{4.} & f_p = 851.25 \text{ MHz; } V_p = V_o \\ & f_q = 858.25 \text{ MHz; } V_q = V_o -6 \text{ dB} \\ & f_r = 860.25 \text{ MHz; } V_r = V_o -6 \text{ dB} \\ & \text{measured at } f_p + f_q f_r = 849.25 \text{ MHz.} \end{array}$

BGD885



List of components (see test circuit)

COMPONENT	DESCRIPTION	
C1,C2	ceramic multilayer capacitor	1 nF
R	2 Watt resistor	56 Ω

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BGE85A

FEATURES

- Excellent linearity
- Extremely low noise
- · Silicon nitride passivation
- Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

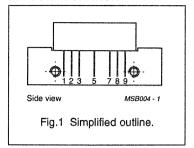
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 40 to 450 MHz at a voltage supply of +24 V (DC). Intended for use as an 18.5 dB output amplifier module.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz;	17.4	_	19.4	dB
l _{tot}	total current consumption	DC value; V _B = +24 V	_	200	230	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	_	65	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{case}	operating case temperature range	-20	+100	°C

BGE85A

CHARACTERISTICS

Bandwidth 40 to 450 MHz; $\rm T_{case}$ = 30 °C; $\rm Z_{S}$ = $\rm Z_{L}$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	17.4	-	19.4	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.3	-	1.5	dB
FL	flatness of frequency response	f = 40 to 450 MHz	-	-	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	_	-	dB
"	•	f = 80 to 450 MHz;	15.5	-	_	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	_	-	dB
22		f = 80 to 450 MHz;	15.5	-	_	dB
d ₂	second order distortion	V _o = 46 dBmV note 1	-	-	-72	dB
V _o	output voltage	d _{im} = -60 dB note 2	60.5		-	dBmV
F	noise figure	f = 40 to 450 MHz	_	-	7	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	-	200	230	mA

Notes

- 1. $f_p = 55.25 \text{ MHz}$; $V_o = 46 \text{ dBmV}$; $f_q = 343.25 \text{ MHz}; V_o = 46 \text{ dBmV};$ measured at $f_p + f_q = 398.5 \text{ MHz}$
- 2. Measured according to DIN45004B;

 $f_p = 440.25 \text{ MHz}; V_p = V_o;$

 $f_{q} = 447.25 \text{ MHz}; V_{q} = V_{o} -6 \text{ dB};$

 $f_r = 449.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$

Measured at $f_p + f_q - f_r = 438.25$ MHz.

BGE88;BGE88/01

FEATURES

- · Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- Rugged construction
- Optimal reliability ensured by TiPtAu metallized crystals.

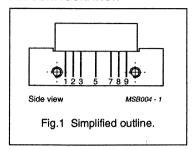
DESCRIPTION

Low cost hybrid amplifier modules for CATV systems operating over a frequency range of 40 to 450 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz	33	-	36	dB
I _{tot}	total current consumption	DC value; V _B = +24 V				
	BGE88		-	290	330	mA
	BGE88/01		-	250	260	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	_	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{case}	operating case temperature range	-20	+100	°C

BGE88;BGE88/01

CHARACTERISTICS

Bandwidth 40 to 450 MHz; T_{case} = 30 °C; Z_{S} = Z_{L} = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	33	_	36	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.5	_	2.5	dB
FL	flatness of frequency response	f = 40 to 450 MHz	-	-	0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	_	-	dB
.,		f = 80 to 160 MHz	18.5	-	-	dB
		f = 160 to 320 MHz	17	-	-	dB
		f = 320 to 450 MHz	15.5	- '	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	_	-	dB
- 22	'	f = 80 to 160 MHz	18.5	-	-	dB
		f = 160 to 320 MHz	17	_	_	dB
	·	f = 320 to 450 MHz	15.5	-	-	dB
d ₂	second order distortion	note 1	-	-	–70	dB
V _o	output voltage	d _{im} = -60 dB note 2				
	BGE88		60	-	-	dBmV
	BGE88/01		59	_		dBmV
F	noise figure	f = 450 MHz	-		6	dB
I _{tot}	total current consumption	DC value; V _B = +24 V; note 3				
	BGE88		-	290	330	mA
	BGE88/01		_	250	260	mA

- 1. $f_p = 55.25$ MHz; $V_p = 46$ dBmV; $f_q = 343.25$ MHz; $V_q = 46$ dBmV; measured at $f_p + f_q = 398.5$ MHz
- 2. $f_p = 440.25$ MHz; $V_p = V_o$; $f_q = 447.25$ MHz; $V_q = V_o 6$ dB; $f_r = 449.25$ MHz; $V_r = V_o 6$ dB; measured at $f_p + f_q f_r = 438.25$ MHz.
- 3. The modules normally operate at $V_B = +24 \text{ V}$, but are able to withstand supply transients up to 30 V.

BGE885

FEATURES

- Excellent linearity
- · Extremely low noise
- · Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

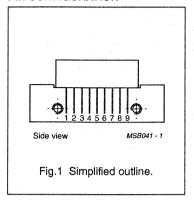
DESCRIPTION

Hybrid amplifier module intended for use in CATV systems operating over a frequency range of 40 to 860 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115D

PIN	DESCRIPTION
- 1	input (note 1)
2	common
3	common
4	12 V - 60 mA supply terminal
	terminai
5	common
6	common
7	common
8	+V _B
9	output (note 1)

PIN CONFIGURATION



Note

1. Pins 1 and 9 carry DC voltages.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	16.5	17.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	240	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	ç
V_B	DC supply voltage	_	+28	٧

BGE885

CHARACTERISTICS

 T_{mb} = 30 °C; Z_{S} = Z_{L} = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	16.5	17.5	dB
SL	slope cable equivalent	f = 40 to 860 MHz	0.2	1.2	dB
FL	flatness of frequency response	f = 40 to 860 MHz	-	± 0.5	dB
S ₁₁	input return losses	f = 40 to 450 MHz	-	14	dB
,,		f = 450 to 860 MHz	_	10	dB
S ₂₂	output return losses	f = 40 to 450 MHz	_	14	dB
22		f = 450 to 860 MHz	-	10	dB
d ₂	second order distortion	note 1	-	-53	dB
V _o	output voitage	d _{im} = -60 dB note 2	_	59	dBmV
F	noise figure	f = 350 MHz; f = 860 MHz	-	7.5 8	dB dB
I _{tot}	total current consumption	DC value; V _B = +24 V		240	mA

- 1. V_p = 59 dBmV at f_p = 350 MHz; V_p = 59 dBmV at f_p = 400 MHz; measured at f_p + f_q = 750 MHz.
- $\begin{array}{lll} \text{2.} & \text{Measured according to DIN45004B;} \\ f_p = 851.25 \text{ MHz; } V_p = V_o = 59.0 \text{ dBmV;} \\ f_q = 858.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \\ f_r = 860.25 \text{ MHz; } V_r = V_o -6 \text{ dB;} \\ \text{measured at } f_p + f_q f_r = 849.25 \text{ MHz.} \\ \end{array}$

BGE887

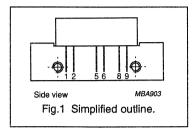
FEATURES

- Excellent linearity
- Extremely low noise
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

PINNING - SOT115H

PIN	DESCRIPTION
1	input
2	common
5	+V _B
6	common
8	common
9	output

PIN CONFIGURATION



DESCRIPTION

Hybrid amplifier module intended for use in the UHF part of VHF/UHF split-band CATV systems over a frequency range of 470 to 860 MHz with a voltage supply of +24 V (DC).

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 470 MHz;	22.5	25	dB
I _{tot}	total current consumption	DC value; $V_B = +24 \text{ V};$ note 1	_	280	mA

Note

1. The module normally operates at $V_B = +24 \, \text{V}$, but is able to withstand supply transients up to +30 V.

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
Vi	RF input voltage	_	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C
V _B	DC supply voltage	_	+28	٧

BGE887

CHARACTERISTICS

 $T_{case} = 30 \,^{\circ}C; Z_{S} = Z_{L} = 75 \,\Omega;$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 470 MHz;	22.5	25	dB
SL	slope cable equivalent	f = 470 to 860 MHz	-0.2	+1	dB
FL	flatness of frequency response	f = 470 to 860 MHz	-	±0.3	dB
S ₁₁	input return losses	f = 470 to 860 MHz;	12	_	dB
S ₂₂	output return losses	f = 470 to 860 MHz;	17	_	dB
V _o	output voltage	d _{im} = -60 dB note 1	60.5	-	dBmV
		d _{im} = -60 dB note 2	60.5	-	dBmV
F	noise figure	f = 470 MHz; f = 860 MHz		8 8.5	dB dB
l _{tot}	total current consumption	DC value; V _B = +24 V		280	mA

- $\begin{array}{llll} \text{1.} & f_p = 483.25 \text{ MHz; V}_p = \text{V}_o \\ & f_q = 490.25 \text{ MHz; V}_q = \text{V}_o 6 \text{ dB} \\ & f_r = 492.25 \text{ MHz; V}_r = \text{V}_o 6 \text{ dB} \\ & \text{measured at f}_p + f_q f_r = 481.25 \text{ MHz} \end{array}$
- $\begin{array}{lll} \text{2.} & f_p = 851.25 \text{ MHz}; \ V_p = \ V_o; \\ f_q = 858.25 \text{ MHz}; \ V_q = \ V_o \ -6 \text{ dB}; \\ f_r = 860.25 \text{ MHz}; \ V_r = \ V_o \ -6 \text{ dB}; \\ \text{measured at } f_p + \ f_q \ f_r = \ 849.25 \text{ MHz}. \end{array}$

BGX881

FEATURES

- Excellent linearity
- Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- Gold metallization ensures excellent reliability.

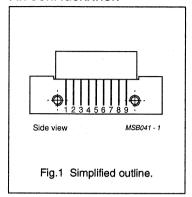
DESCRIPTION

Hybrid amplifier module for CATV/MATV systems operating over a frequency range of 40 to 860 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115D

PIN	DESCRIPTION
1	input (note 1)
2	common
3	common
4	12 V - 60 mA supply terminal
5	common
6	common
7	common
8	+V _B (24 V DC)
9	output (note 1)

PIN CONFIGURATION



Note

1. Pins 1 and 9 carry DC voltages.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	12	13	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	240	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	_	60	dBmV
T_{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C
V _B	DC supply voltage	-	+26	V

BGX881

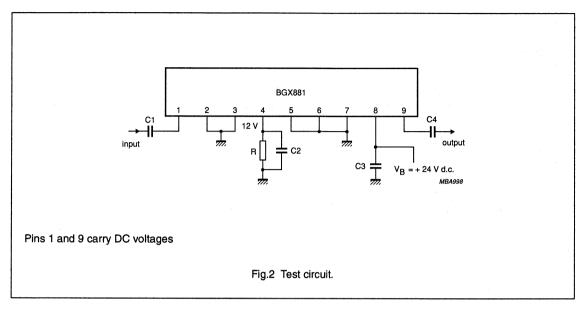
CHARACTERISTICS

 $T_{mb} = 30 \,^{\circ}\text{C}; Z_{S} = Z_{L} = 75 \,\Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	12	13	dB
SL	slope cable equivalent	f = 40 to 860 MHz	0.2	1.4	dB
FL	flatness of frequency response	f = 40 to 860 MHz	-	± 0.3	dB
S ₁₁	input return losses	f = 40 MHz (note 1)	20	-	dB
11		f = 800 to 860 MHz;	10	-	dB
S ₂₂	output return losses	f = 40 MHz (note 1)	20	-	dB
- 22		f = 640 to 860 MHz	15	-	dB
d_2	second order distortion	note 2	_	-53	dB
V _o	output voltage	d _{im} = -60 dB note 3	60.5	-	dBmV
		$d_{im} = -60 \text{ dB}$ note 4	59.5	_	dBmV
F	noise figure	f = 350 MHz;	-	8.5	dB
•		f = 860 MHz		9	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	240	mA

- 1. Decreases 1.5 dB per octave
- 2. $f_p = 349.25 \text{ MHz}; V_p = 59 \text{ dBmV}; \\ f_q = 403.25 \text{ MHz}; V_q = 59 \text{ dBmV}; \\ \text{measured at } f_p + f_q = 752.5 \text{ MHz}$
- $\begin{array}{lll} 3. & f_p = 341.25 \text{ MHz; } V_p = V_o; \\ & f_q = 348.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \\ & f_r = 350.25 \text{ MHz; } V_r = V_o -6 \text{ dB;} \\ & \text{measured at } f_p + f_q f_r = 339.25 \text{ MHz.} \end{array}$
- $\begin{array}{lll} \text{4.} & \text{f}_{\text{p}} = 851.25 \text{ MHz; } \text{V}_{\text{p}} = \text{V}_{\text{o}}; \\ \text{f}_{\text{q}} = 858.25 \text{ MHz; } \text{V}_{\text{q}} = \text{V}_{\text{o}} 6 \text{ dB;} \\ \text{f}_{\text{r}} = 860.25 \text{ MHz; } \text{V}_{\text{r}} = \text{V}_{\text{o}} 6 \text{ dB;} \\ \text{measured at f}_{\text{p}} + \text{f}_{\text{q}} \text{f}_{\text{r}} = 849.25 \text{ MHz.} \end{array}$

BGX881



List of components (see test circuit)

COMPONENT	DESCRIPTION	VALUE
C1,C2,C3,C4	ceramic multilayer capacitor	10 nF
R	1 Watt resistor	200 Ω

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BGX885N

FEATURES

- Excellent linearity
- Extremely low noise
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

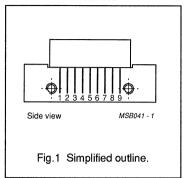
DESCRIPTION

Hybrid amplifier module for CATV/MATV systems operating over a frequency range of 40 to 860 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115D

PIN	DESCRIPTION
1	input
2	common
3	common
4	12 V - 60 mA output terminal
5	common
6	common
7	common
8	+V _B
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	16.5	17.5	dB
		f = 750 MHz	17.3	_	dB
I _{tot}	total current consumption	DC value;	_	240	mA
		$V_B = +24 \text{ V}$			

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_{i}	RF input voltage	_	60	dBmV
T_{stg}	storage temperature range	-40	100	°C
Т _{ть}	mounting base operating temperature range	-20	100	°C
V _B	DC supply voltage	_	26	٧

BGX885N

CHARACTERISTICS

 $T_{mb} = 30 \, ^{\circ}C; Z_{S} = Z_{L} = 75 \, \Omega.$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	16.5	17.5	dB
		f = 750 MHz	17.3	-	dB
SL	slope cable equivalent	f = 40 to 860 MHz	0.2	1.4	dB
FL	flatness of frequency response	f = 40 to 860 MHz	_	± 0.3	dB
S ₁₁	input return losses	f = 40 MHz (note 1)	20	_	dB
		f = 800 to 860 MHz	10	_	dB
S ₂₂	output return losses	f = 40 MHz (note 1)	20	_	dB
		f = 640 to 860 MHz	15	-	dB
d ₂	second order distortion	note 2	-	-53	dB
V _o	output voltage	$d_{im} = -60 \text{ dB}$			
-		note 3	61	-	dBmV
		note 4	60	_	dBmV
F	noise figure	f = 350 MHz;	_	7.5	dB
		f = 860 MHz	-	8	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	240	mA
		note 5			

Notes

- 1. Decreases by 1.5 dB per octave.
- $\begin{array}{lll} \text{2.} & f_p = 349.25 \text{ MHz; V}_p = \text{V}_o = 59 \text{ dBmV;} \\ f_q = 403.25 \text{ MHz; V}_q = \text{V}_o; \\ & \text{measured at f}_p + f_q = 752.5 \text{ MHz.} \\ \end{array}$
- $\begin{array}{lll} 3. & f_p = 341.25 \text{ MHz; } V_p = V_o; \\ f_q = 348.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \\ f_r = 350.25 \text{ MHz; } V_r = V_o -6 \text{ dB;} \\ \text{measured at } f_p + f_q f_r = 339.25 \text{ MHz.} \end{array}$
- 4. f_p = 851.25 MHz; V_p = V_o; f_q = 858.25 MHz; V_q = V_o - 6dB; f_r = 860.25 MHz; V_r = V_o - 6dB; measured at f_p + f_q - f_r = 849.25 MHz.
- 5. The module normally operates at $V_B = +24 \text{ V}$, but is able to withstand supply transients up to +30 V.

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Hybrid VHF push-pull amplifier module

BGY60

FEATURES

- Excellent linearity
- Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

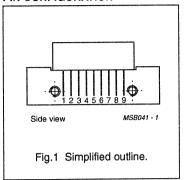
DESCRIPTION

Interstage hybrid amplifier module for CATV systems operating over a frequency range of 40 to 300 MHz at a voltage supply of +24 V (DC). The inputs and outputs of the stages have been terminated separately.

PINNING - SOT115D

PIN	DESCRIPTION
1	input pre-stage
2	common
3	common
4	output pre-stage
5	+V _B
6	input final stage
7	common
8	common
9	output final stage

PIN CONFIGURATION



QUICK REFERENCE DATA

For total amplifier.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	32.5	_	34.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	320	340	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
Vi	RF input voltage (total amplifier)	-	55	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+90	°C

Hybrid VHF push-pull amplifier module

BGY60

CHARACTERISTICS

For total amplifier unless otherwise specified; Bandwidth 40 to 300 MHz; T_{amb} = 25 °C; Z_S = Z_L = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Gp	power gain	f = 50 MHz;	32.5	-	34.5	dB
SL	slope cable equivalent	f = 40 to 300 MHz	0.5	_	1.5	dB
FL	flatness of frequency response	f = 40 to 300 MHz	-	_	± 0.3	dB
S ₁₁	input return losses	f = 40 to 300 MHz;				
		pre-stage;	20	-	-	dB
		final stage	18	-	-	dB
S ₂₂	output return losses	f = 40 to 300 MHz;				
	,	pre-stage;	18		-	dB
		final stage	20	-	-	dB
d ₂	second order distortion	note 1	_	-	-66	dB
V _o	output voltage	d _{im} = -60 dB note 2	64	-	_	dBmV
F	noise figure	f = 40 to 300 MHz	-	_	6	dB
I _{tot}	total current consumption	DC value; V _B = +24 V; note 3	-	320	340	mA

- $\begin{array}{ll} \text{1.} & \text{f}_p = 55.25 \text{ MHz}; \, \text{V}_p = \text{V}_o = 50 \text{ dBmV}; \\ \text{f}_q = 211.25 \text{ MHz}; \, \text{V}_q = \text{V}_o = 50 \text{ dBmV}; \\ \text{measured at f}_p + \text{f}_q = 266.5 \text{ MHz} \end{array}$
- 2. Measured according to DIN45004B;
 $$\begin{split} f_p &= 287.25 \text{ MHz; } V_p = V_o; \\ f_q &= 294.25 \text{ MHz; } V_q = V_o 6 \text{ dB;} \\ f_r &= 296.25 \text{ MHz; } V_r = V_o 6 \text{ dB;} \\ \text{measured at } f_p + f_q f_r = 285.25 \text{ MHz} \end{split}$$
- 3. The module normally operates at $V_B = +24 \text{ V}$, but is able to withstand supply transients up to +30 V.

BGY61

FEATURES

- · Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

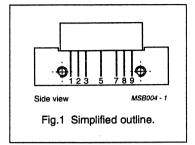
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 5 to 200 MHz at a voltage supply of +24 V (DC). The device is intended as a reverse amplifier for use in two way systems.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 10 MHz;	12.5	-	13.5	dB
I _{tot}	1	DC value; V _B = +24 V	-	215	230	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
Vi	RF input voltage	-	67	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+90	ပဲ

BGY61

CHARACTERISTICS

Bandwidth 5 to 200 MHz; $\rm T_{mb}$ = 30 °C; $\rm Z_{S}$ = $\rm Z_{L}$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 10 MHz;	12.5	_	13.5	dB
SL	slope cable equivalent	f = 5 to 200 MHz	-0.2	_	+0.5	dB
FL	flatness of frequency response	f = 5 to 200 MHz	-	-	± 0.2	dB
S ₁₁	input return losses	f = 5 to 200 MHz;	20	-	_	dB
S ₂₂	output return losses	f = 5 to 200 MHz;	20	-	_	dB
СТВ	composite triple beat	22 chs flat; V _o = 50 dBmV; measured at 175.25 MHz	-	-	-68	dB
X _{mod}	cross modulation	22 chs flat; V _o = 50 dBmV; measured at 55.25 MHz	-	-	-61	dB
d ₂	second order distortion	V _o = 50 dBmV; note 1	-	-	-72	dB
V _o	output voltage	d _{im} = -60 dB note 2	67	_	_	dBmV
		d _{im} = -60 dB note 3	64	-	_	dBmV
F	noise figure	f = 200 MHz	-	-	7	dB
l _{tot}	total current consumption	DC value; V _B = +24 V; note 4	_	215	230	mA

Notes

- 1. $f_p = 83.25 \text{ MHz}$; $V_p = 50 \text{ dBmV}$; $f_{q}^{r} = 109.25 \text{ MHz}; V_{q} = 50 \text{ dBmV};$ measured at $f_p + f_q = 192.5 \text{ MHz}$
- 2. Measured according to DIN45004B;

$$\begin{split} &f_p = 35.25 \text{ MHz; } V_o = V_p; \\ &f_q = 42.25 \text{ MHz; } V_q = V_o \text{ } -6 \text{ dB;} \end{split}$$

 $f_r = 44.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$

measured at $f_p + f_q - f_r = 33.25 \text{ MHz}$

3. Measured according to DIN45004B;

 $f_p = 187.25 \text{ MHz}; V_o = V_p;$

 $f_q = 194.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$ $f_r = 196.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$

measured at $f_p + f_q - f_r = 185.25 \text{ MHz}$

4. The module normally operates at $V_B = +24 \text{ V}$, but is able to withstand supply transients up to +30 V.

BGY65

FEATURES

- · Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

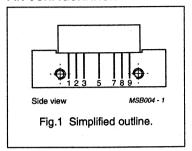
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 5 to 200 MHz at a voltage supply of +24 V (DC). The device is intended as a reverse amplifier for use in two way systems.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 10 MHz;	18	-	19	dB
l _{tot}	1	DC value; V _B = +24 V	-	215	230	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
Vi	RF input voltage	-	65	dBmV
T _{stg}	storage temperature range	-40	+100	C
T _{mb}	mounting base operating temperature range	-20	+90	°C

BGY65

CHARACTERISTICS

Bandwidth 5 to 200 MHz; $\rm T_{mb}$ = 30 °C; $\rm Z_{S}$ = $\rm Z_{L}$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 10 MHz;	18	_	19	dB
SL	slope cable equivalent	f = 5 to 200 MHz	-0.2	-	+0.5	dB
FL	flatness of frequency response	f = 5 to 200 MHz	_	_	± 0.2	dB
S ₁₁	input return losses	f = 5 to 200 MHz;	20	_	_	dB
S ₂₂	output return losses	f = 5 to 200 MHz;	20	 -	-	dB
СТВ	composite triple beat	22 chs flat; $V_o = 50 \text{ dBmV}$; measured at 175.25 MHz	_	_	-68	dB
X _{mod}	cross modulation	22 chs flat; V _o = 50 dBmV; measured at 55.25 MHz	-	_	-61	dB
d ₂	second order distortion	V _o = 50 dBmV; note 1	-	_	-72	dB
V _o	output voltage	d _{im} = -60 dB note 2	67	_	_	dBmV
		d _{im} = -60 dB note 3	64	_	-	dBmV
F	noise figure	f = 200 MHz	-	-	5.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V; note 4	-	215	230	mA

Notes

- 1. $f_p = 83.25 \text{ MHz}; V_p = 50 \text{ dBmV}; \\ f_q = 109.25 \text{ MHz}; V_q = 50 \text{ dBmV}; \\ \text{measured at } f_p + f_q = 192.5 \text{ MHz}$
- 2. Measured according to DIN45004B;

 $\begin{array}{l} {\rm f_p = 35.25~MHz;~V_o = V_p;} \\ {\rm f_q = 42.25~MHz;~V_q = V_o ~-6~dB;} \\ {\rm f_r = 44.25~MHz;~V_r = V_o ~-6~dB;} \\ {\rm measured~at~f_p + f_q - f_r = 33.25~MHz} \end{array}$

3. Measured according to DIN45004B;

 $f_p = 187.25 \text{ MHz}; V_o = V_p;$ $f_q = 194.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$ $f_r = 196.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$ measured at $f_p + f_q - f_r = 185.25 \text{ MHz}$

4. The module normally operates at $V_B = +24 \text{ V}$, but is able to withstand supply transients up to +30 V.

BGY67

FEATURES

- Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

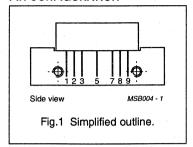
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 5 to 200 MHz at a voltage supply of +24 V (DC). The device is intended as a reverse amplifier for use in two way systems.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 10 MHz;	21.5	-	22.5	dB
I _{tot}	i	DC value; V _B = +24 V	-	215	230	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	65	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	20	+90	°C

BGY67

CHARACTERISTICS

Bandwidth 5 to 200 MHz; $T_{mb} = 30$ °C; $Z_S = Z_L = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 10 MHz;	21.5	_	22.5	dB
SL	slope cable equivalent	f = 5 to 200 MHz	-0.2	-	+0.5	dB
FL	flatness of frequency response	f = 5 to 200 MHz		-	± 0.2	dB
S ₁₁	input return losses	f = 5 to 200 MHz;	20	-	-	dB
S ₂₂	output return losses	f = 5 to 200 MHz;	20		-	dB
СТВ	composite triple beat	22 chs flat; V _o = 50 dBmV; measured at 175.25 MHz	-	-	-67	dB
X _{mod}	cross modulation	22 chs flat; V _o = 50 dBmV; measured at 55.25 MHz	_	_	-60	dB
d ₂	second order distortion	V _o = 50 dBmV; note 1	_	-	-67	dB
V _o	output voltage	d _{im} = -60 dB note 2	67	_	-	dBmV
		d _{im} = -60 dB note 3	64	_	_	dBmV
F	noise figure	f = 200 MHz	_	-	5.5	dB
l _{tot}	total current consumption	DC value; V _B = +24 V; note 4		215	230	mA

Notes

- 1. $f_p = 83.25 \text{ MHz}$; $V_p = 50 \text{ dBmV}$; $f_{q} = 109.25 \text{ MHz}; V_{q} = 50 \text{ dBmV};$ measured at $f_p + f_q = 192.5 \text{ MHz}$
- 2. Measured according to DIN45004B;

$$\begin{split} &f_p = 35.25 \text{ MHz; } V_o = V_p; \\ &f_q = 42.25 \text{ MHz; } V_q = V_o \text{ } -6 \text{ dB;} \end{split}$$

 $f_r = 44.25 \text{ MHz}; V_r = V_o - 6 \text{ dB};$ measured at $f_p + f_q - f_r = 33.25 \text{ MHz}$

3. Measured according to DIN45004B;

$$\begin{split} f_p &= 187.25 \text{ MHz; } V_o = V_p; \\ f_q &= 194.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \\ f_r &= 196.25 \text{ MHz; } V_r = V_o -6 \text{ dB;} \end{split}$$

measured at $f_p + f_q - f_r = 185.25 \text{ MHz}$

4. The module normally operates at $V_B = +24 \text{ V}$, but is able to withstand supply transients up to +30 V.

BGY67A

FEATURES

- Excellent linearity
- · Extremely low noise
- Silicon nitride passivation
- Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

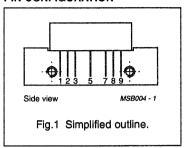
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 5 to 200 MHz at a voltage supply of +24 V (DC). The device is intended as a reverse amplifier for use in two way systems.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 10 MHz;	23.5	-	24.5	dB
I _{tot}	l .	DC value; V _B = +24 V	-	215	230	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	_	63	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+90	°C

BGY67A

CHARACTERISTICS

Bandwidth 5 to 200 MHz; $T_{mb} = 30$ °C; $Z_S = Z_L = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 10 MHz;	23.5	-	24.5	dB
SL	slope cable equivalent	f = 5 to 200 MHz	-0.2		+0.5	dB
FL	flatness of frequency response	f = 5 to 200 MHz	-	-	± 0.2	dB
S ₁₁	input return losses	f = 5 to 200 MHz;	20	_		dB
S ₂₂	output return losses	f = 5 to 200 MHz;	20	-	-	dB
СТВ	composite triple beat	22 chs flat; V _o = 50 dBmV; measured at 175.25 MHz	-	-	–67	dB
X _{mod}	cross modulation	22 chs flat; V _o = 50 dBmV; measured at 55.25 MHz	-	_	– 59	dB
d ₂	second order distortion	V _o = 50 dBmV; note 1	-		-67	dB
V _o	output voltage	d _{im} = -60 dB note 2	67		_	dBmV
		d _{im} = -60 dB note 3	64		-	dBmV
F	noise figure	f = 200 MHz	_	_	5.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V; note 4	-	215	230	mA

- 1.
 $$\begin{split} \text{f}_{\text{p}} = & \text{83.25 MHz; V}_{\text{p}} = \text{50 dBmV;} \\ \text{f}_{\text{q}} = & \text{109.25 MHz; V}_{\text{q}} = \text{50 dBmV;} \\ \text{measured at f}_{\text{p}} + \text{f}_{\text{q}} = \text{192.5 MHz} \end{split}$$
- 2. Measured according to DIN45004B; $\begin{aligned} f_p &= 35.25 \text{ MHz; } V_o = V_p; \\ f_q &= 42.25 \text{ MHz; } V_q = V_o &-6 \text{ dB;} \\ f_r &= 44.25 \text{ MHz; } V_r = V_o &-6 \text{ dB;} \\ \text{measured at } f_p + f_q f_r = 33.25 \text{ MHz} \end{aligned}$
- 3. Measured according to DIN45004B;
 - $\begin{array}{l} f_p = 187.25 \text{ MHz; } V_o = V_p; \\ f_q = 194.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \\ f_r = 196.25 \text{ MHz; } V_r = V_o -6 \text{ dB;} \\ \text{measured at } f_p + f_q f_r = 185.25 \text{ MHz} \end{array}$
- 4. The module normally operates at $V_B = +24 \text{ V}$, but is able to withstand supply transients up to +30 V.

BGY80/81

FEATURES

- · Excellent linearity
- Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- Optimal reliability ensured by TiPtAu metallized crystals.

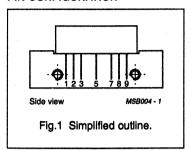
DESCRIPTION

Hybrid amplifier modules for CATV systems operating over a frequency range of 40 to 450 MHz at a voltage supply of +24 V (DC). BGY80 intended for use as a 12.5 dB pre-amplifier and BGY81 as a 12.5 dB final-amplifier.

PINNING - SOT115C

PIN	DESCRIPTION		
1	input		
2	common		
3	common		
5	+V _B		
7	common		
8	common		
9	output		

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz	12	13	dB
		f = 450 MHz	12.5	14	dB
I _{tot}	total current consumption	DC value; V _B = +24 V			
	BGY80		_	200	mA
	BGY81		_	240	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
Vi	RF input voltage	_	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{case}	operating case temperature range	-20	+100	°C

BGY80/81

CHARACTERISTICS

Bandwidth 40 to 450 MHz; $T_{case} = 35$ °C; $Z_{s} = Z_{L} = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	12	1-	13	dB
P		f = 450 MHz	12.5	-	14	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.2	-	1.5	dB
FL	flatness of frequency response	f = 40 to 450 MHz	-	_	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	_	-	dB
		f = 80 to 160 MHz	19	_	-	dB
		f = 160 to 450 MHz	18	-	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	_	-	dB
		f = 80 to 160 MHz	19	_	-	dB
		f = 160 to 450 MHz	18	-	_	dB
СТВ	composite triple beat	60 chs flat; $V_o = 46 \text{ dBmV}$; measured at 445.25 MHz				
	BGY80		_	-	-54	dB
	BGY81		-	-	-58	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz				
	BGY80		_	-	-59	dB
	BGY81		_	-	-62	dB
d ₂	second order distortion	note 1				
	BGY80		-	-	-72	dB
	BGY81		-		-74	dB
V _o	output voltage	d _{im} = -60 dB note 2				
	BGY80		61.5	-	-	dBmV
	BGY81		64	_		dBmV
F	noise figure	f = 450 MHz				
	BGY80		-	-	7.5	dB
	BGY81			_	8	dB
l _{tot}	total current consumption	DC value; V _B = +24 V; note 3				
	BGY80		_	180	200	mA
	BGY81		_	220	240	mA

BGY80/81

- 1. f_p = 55.25 MHz; V_p = 46 dBmV; f_q = 391.25 MHz; V_q = 46 dBmV; measured at f_p + f_q = 446.5 MHz
- 2. $f_p = 440.25 \text{ MHz}; V_p = V_o;$ $f_q = 447.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$ $f_r = 449.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$ measured at $f_p + f_q - f_r = 438.25 \text{ MHz}.$
- 3. The modules normally operate at $V_B = +24 \text{ V}$, but are able to withstand supply transients up to 30 V.



BGY82;BGY83

FEATURES

- Excellent linearity
- · Extremely low noise
- Silicon nitride passivation
- Rugged construction
- Optimal reliability ensured by TiPtAu metallized crystals.

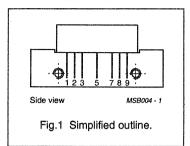
DESCRIPTION

Hybrid amplifier modules for CATV systems operating over a frequency range of 40 to 450 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	13.5	_	14.5	dB
		f = 450 MHz	14.5	_	_	dB
I _{tot}	total current consumption	DC value; V _B = +24 V				
	BGY82		_	180	200	mΑ
	BGY83		_	220	240	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	_	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{case}	operating case temperature range	-20	+100	ပွ

BGY82;BGY83

CHARACTERISTICS

Bandwidth 40 to 450 MHz; $T_{case} = 30$ °C; $Z_{S} = Z_{L} = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	13.5	_	14.5	dB
۲		f = 450 MHz	14.5	-	-	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.2	-	1.5	dB
FL	flatness of frequency response	f = 40 to 450 MHz	_	-	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	_	-	dB
		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 450 MHz	18	-	_	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	-	_	dB
Late		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 450 MHz	18	-	-	dB
CTB	composite triple beat	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz				
	BGY82		-	-	-55	dB
	BGY83		-	-	-59	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz				
	BGY82		_	-	-56	dB
	BGY83		-	-	-59	dB
CSO	composite second order distortion	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz				
	BGY82		_	_	-55	dB
	BGY83		_	_	-59	dB
d ₂	second order distortion	note 1				
	BGY82		_	-	-72	dB
	BGY83		-	-	74	dB
V _o	output voltage	d _{im} = -60 dB note 2				
	BGY82		61.5	-	-	dBmV
	BGY83		64	-	-	dBmV
F	noise figure	f = 450 MHz				
	BGY82		_	-	7	dB
	BGY83		-	-	8	dB

BGY82;BGY83

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
l _{tot}	total current consumption	DC value; V _B = +24 V; note 3				
	BGY82			180	200	mA
	BGY83		_	220	240	mA

Notes

- 1. f_p = 55.25 MHz; V_p = 46 dBmV; f_q = 391.25 MHz; V_q = 46 dBmV; measured at f_p + f_q = 446.5 MHz
- 2. Measured according to DIN45004B; $f_p = 440.25 \text{ MHz}; V_p = V_o;$ $f_q = 447.25 \text{ MHz}; V_q = V_o - 6 \text{ dB};$ $f_r = 449.25 \text{ MHz}; V_r = V_o - 6 \text{ dB};$

measured at $f_p + f_q - f_r = 438.25$ MHz.

3. The modules normally operate at $V_B = +24 \text{ V}$, but are able to withstand supply transients up to 30 V.

BGY84;BGY85

FEATURES

- Excellent linearity
- · Extremely low noise
- Silicon nitride passivation
- · Rugged construction
- Optimal reliability ensured by TiPtAu metallized crystals.

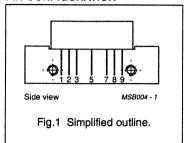
DESCRIPTION

Hybrid amplifier modules for CATV systems operating over a frequency range of 40 to 450 MHz at a voltage supply of +24 V (DC). BGY84 intended for use as an input amplifier module and BGY85 as an output amplifier module.

PINNING - SOT115C

PIN	DESCRIPTION
. 1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	16.5	-	17.5	dB
		f = 450 MHz	17.3	_	18.8	dB
I _{tot}	total current consumption	DC value; V _B = +24 V				
	BGY84		_	180	200	mA
	BGY85		-	220	240	mΑ

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	65	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGY84;BGY85

CHARACTERISTICS

Bandwidth 40 to 450 MHz; $T_{mb} = 30$ °C; $Z_S = Z_L = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	16.5	_	17.5	dB
- p		f = 450 MHz	17.3	_	18.8	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.5	-	1.5	dB
FL	flatness of frequency response	f = 40 to 450 MHz	-	-	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	_	-	dB
- 11	,	f = 80 to 160 MHz	19	_	-	dB
		f = 160 to 450 MHz	18	-	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	-	_	dB
22		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 450 MHz	18	-	-	dB
СТВ	composite triple beat	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz				
	BGY84	'	-	-	-55	dB
	BGY85		-		-58	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz				
	BGY84		_	_	-57	dB
	BGY85		_	_	-60	dB
d ₂	second order distortion	note 1	-	_	-70	dB
V _o	output voltage	d _{im} = -60 dB note 2				
	BGY84		60	-	-	dBmV
	BGY85		62.5	-		dBmV
F	noise figure	f = 40 to 450 MHz				
	BGY84		-	-	6.5	dB
	BGY85		_		7	dB
I _{tot}	total current consumption	DC value; V _B = +24 V; note 3				
	BGY84		-	180	200	mA
	BGY85		-	220	240	mA

BGY84;BGY85

- 1. $f_p = 55.25$ MHz; $V_p = 46$ dBmV; $f_q = 343.25$ MHz; $V_q = 46$ dBmV; measured at $f_p + f_q = 398.5$ MHz
- 2. Measured according to DIN45004B; $f_p = 440.25 \text{ MHz}; V_p = V_o;$ $f_q = 447.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$ $f_r = 449.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$ measured at $f_p + f_q f_r = 438.25 \text{ MHz}.$
- 3. The modules normally operate at $V_B = +24 \text{ V}$, but are able to withstand supply transients up to 30 V.

BGY84A;BGY85A

FEATURES

- Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- Rugged construction
- Optimal reliability ensured by TiPtAu metallized crystals.

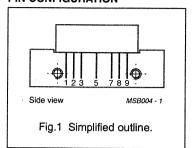
DESCRIPTION

Hybrid amplifier modules for CATV systems operating over a frequency range of 40 to 450 MHz at a voltage supply of +24 V (DC). The BGY84A is intended for use as an input amplifier module and BGY85A as an output amplifier module.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	18	-	18.8	dB
		f = 450 MHz	18.7	-	20.2	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	-			
	BGY84A		-	180	200	mA
	BGY85A		-	220	240	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	65	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	operating mounting base temperature range	-20	+100	°C

BGY84A;BGY85A

CHARACTERISTICS

Bandwidth 40 to 450 MHz; $T_{mb} = 30$ °C; $Z_S = Z_L = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Э _р	power gain	f = 50 MHz	18	-	18.8	dB
p		f = 450 MHz	18.7	-	20.2	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.3	_	1.5	dB
FL.	flatness of frequency response	f = 40 to 450 MHz	_	_	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	-	-	dB
.,		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 450 MHz	18	_		dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	-	-	dB
		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 450 MHz	18		-	dB
СТВ	composite triple beat	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz				
	BGY84A		-	-	-55	dB
	BGY85A		_		-59	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz				
	BGY84A		_	_	58	dB
	BGY85A		_	_	-61	dB
d ₂	second order distortion	note 1	-	-	-72	dB
V _o	output voltage	d _{im} = -60 dB note 2				
	BGY84A		60	-	-	dBmV
	BGY85A		62.5		_	dBmV
F	noise figure	f = 40 to 450 MHz				
	BGY84A	,	-	-	6.5	dB
	BGY85A		-		7	dB
I _{tot}	total current consumption	DC value; V _B = +24 V; note 3				
	BGY84A		_	180	200	mA
	BGY85A		_	220	240	mA

BGY84A;BGY85A

- $\begin{array}{ll} \text{1.} & \quad f_p = 55.25 \text{ MHz; V}_p = 46 \text{ dBmV;} \\ f_q = 343.25 \text{ MHz; V}_q = 46 \text{ dBmV;} \\ \text{measured at } f_p + f_q = 398.5 \text{ MHz} \end{array}$
- 2. Measured according to DIN45004B; $f_p = 440.25 \text{ MHz}; V_p = V_o;$ $f_q = 447.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$ $f_r = 449.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$ measured at $f_p + f_q f_r = 438.25 \text{ MHz}.$
- 3. The modules normally operate at $V_B = +24 \text{ V}$, but are able to withstand supply transients up to 30 V.



BGY85H/01

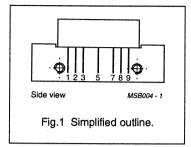
FEATURES

- Excellent linearity
- High slope of 5.1 dB so that total cable slope can be equalised by the slope of the module
- · Silicon nitride passivation
- Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



DESCRIPTION

High slope, pre-emphasis, hybrid amplifier module intended for use as a 20.7 dB trunk amplifier in CATV systems operating over a frequency range of 40 to 450 MHz at a voltage supply of +24 V (DC).

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	14.8	-	16.4	dB
		f = 450 MHz	20.2	-	21.2	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	-	215	230	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	65	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C
V _B	DC supply voltage	-	+28	٧

BGY85H/01

CHARACTERISTICS

Bandwidth 40 to 450 MHz; $\rm T_{case}$ = 30 °C; $\rm Z_{S}$ = $\rm Z_{L}$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	14.8	_	16.4	dB
P		f = 450 MHz	20.2	-	21.2	dB
ΔG	delta gain	f = 40 to 450 MHz	4.7	-	5.5	dB
FL	flatness of frequency response	f = 40 to 450 MHz; note 1	-	-	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	-	-	dB
		f = 80 to 160 MHz;	19	-	-	dB
		f = 160 to 450 MHz	18	-		dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	-	-	dB
22		f = 80 to 160 MHz;	19		_	dB
		f = 160 to 450 MHz	18	_		dB
СТВ	composite triple beat	36 chs flat; V _o = 46 dBmV; measured at 433.25 MHz	-	_	–65	dB
		60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz		–59	-	dB
X _{mod}	cross modulation	36 chs flat; V _o = 46 dBmV; measured at 55.25 MHz		-	-65	dB
		60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz	-	-61	-	dB
d ₂	second order distortion	note 2	_	_	-72	dB
V _o	output voltage	$d_{im} = -60 \text{ dB}$				
		note 3	65	-	-	dBmV
		note 4	64	-	-	dBmV
		note 5	62.5			dBmV
F	noise figure	f = 450 MHz	-	_	6.8	dB
l _{tot}	total current consumption	DC value; $V_B = +24 \text{ V}$; note 6	-	215	230	mA

Notes

1. Flatness calculation is based on the following formula which describes the 'ideal' gain versus frequency curve,

 $G_{\rm f}=G_{\rm 50}+\Delta G~[a~(f-50)+b~(f-50)^2+c~(f-50)^3],~in~which:\\ G_{\rm 50}=measured~gain~at~50~MHz;$

 ΔG = measured difference in gain between 450 and 50 MHz;

 $a = 3.132 \times 10^{-3}$

 $b = 1.993 \times 10^{-6}$

 $c = -8.934 \times 10^{-9}$

BGY85H/01

```
2. f_p = 55.25 MHz; V_p = 46 dBmV; f_q = 343.25 MHz; V_q = 46 dBmV; measured at f_p + f_q = 398.5 MHz
```

3. Measured according to DIN45004B;

```
f_p = 287.25 \text{ MHz}; V_p = V_o;

f_q = 294.25 \text{ MHz}; V_q = V_o -6 \text{ dB};

f_r = 296.25 \text{ MHz}; V_r = V_o -6 \text{ dB};

measured at f_p + f_q - f_r = 285.25 \text{ MHz}
```

4. Measured according to DIN45004B;

```
f_p = 387.25 \text{ MHz}; V_p = V_o;

f_q = 394.25 \text{ MHz}; V_q = V_o -6 \text{ dB};

f_r = 396.25 \text{ MHz}; V_r = V_o -6 \text{ dB};

measured at f_p + f_q - f_r = 385.25 \text{ MHz}
```

5. Measured according to DIN45004B;

```
\begin{array}{l} f_p = 440.25 \text{ MHz; } V_p = V_o; \\ f_q = 447.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \\ f_r = 449.25 \text{ MHz; } V_r = V_o -6 \text{ dB;} \\ \text{measured at } f_p + f_q - f_r = 438.25 \text{ MHz} \end{array}
```

6. The module normally operates at $V_B = +24 \text{ V}$, but is able to withstand supply transients up to +30 V.



BGY86;BGY87

FEATURES

- Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- Optimal reliability ensured by TiPtAu metallized crystals.

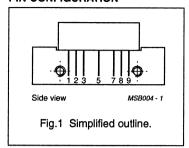
DESCRIPTION

Hybrid amplifier modules for CATV systems operating over a frequency range of 40 to 450 MHz at a voltage supply of +24 V (DC). The BGY86 is intended for use as a pre-amplifier and BGY87 as a final amplifier.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	21.5	_	22.5	dB
		f = 450 MHz	21.7	_	23.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V				
	BGY86		-	180	200	mA
	BGY87		-	220	240	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_{i}	RF input voltage	_	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{case}	operating case temperature range	-20	+100	°C

BGY86;BGY87

CHARACTERISTICS

Bandwidth 40 to 450 MHz; $T_{case} = 30$ °C; $Z_{S} = Z_{L} = 75~\Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	21.5	-	22.5	dB
		f = 450 MHz	21.7	_	23.5	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0	_	1.5	dB
FL	flatness of frequency response	f = 40 to 450 MHz	-	_	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	-	-	dB
		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 450 MHz	18	_		dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	-	-	dB
		f = 80 to 160 MHz	19	_	-	dB
		f = 160 to 450 MHz	18	-	-	dB
СТВ	composite triple beat	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz				
	BGY86		-	-	-54	dB
	BGY87		-		-58	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz				
	BGY86		_	-	-51	dB
	BGY87		-	-	-55	dB
d ₂	second order distortion	note 1				
	BGY86		-	-	-68	dB
	BGY87		_	_	-72	dB
V _o	output voltage	d _{im} = -60 dB note 2				
	BGY86		61.5	-	-	dBmV
	BGY87		64			dBmV
F	noise figure	f = 450 MHz			6	dB
	BGY86			_	6.5	dB
	BGY87	DO velve			0.5	100
l _{tot}	total current consumption	DC value; V _B = +24 V; note 3				
	BGY86		_	180	200	mA
	BGY87		-	220	240	mA

BGY86;BGY87

- 1. $f_p = 55.25 \text{ MHz}; V_p = 46 \text{ dBmV}; f_q = 391.25 \text{ MHz}; V_q = 46 \text{ dBmV}; measured at <math>f_p + f_q = 446.5 \text{ MHz}$
- 2. Measured according to DIN45004B; $f_p = 440.25 \text{ MHz}; V_p = V_o;$ $f_q = 447.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$ $f_r = 449.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$ measured at $f_p + f_q f_r = 438.25 \text{ MHz}.$
- 3. The modules normally operate at $V_B = +24 \text{ V}$, but are able to withstand supply transients up to 30 V.



BGY87B

FEATURES

- Excellent linearity
- Extremely low noise
- Silicon nitride passivation
- Rugged construction
- TiPtAu metallized crystals ensure optimum reliability.

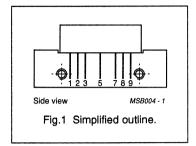
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 40 to 450 MHz at a voltage supply of +24 V.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
. 7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz	26.2	27.8	dB
I _{tot}	total current consumption	DC value; $V_B = +24 V$ (note 1)		340	mA

Note

1. The module normally operates at $V_{\rm B}=+24$ V, but is able to withstand supply transients up to +30 V.

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	55	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGY87B

CHARACTERISTICS

 $T_{case} = 35 \,^{\circ}C; Z_{S} = Z_{L} = 75 \,\Omega.$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	26.2	27.8	dB
P		f = 450 MHz	27.5	-	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.5	2.5	dB
FL	flatness of frequency response	f = 40 to 450 MHz	_	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	-	20	dB
**	·	f = 80 to 160 MHz;	_	19	dB
		f = 160 to 450 MHz	_	18	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	-	20	dB
22	·	f = 80 to 160 MHz;	_	19	dB
		f = 160 to 450 MHz	_	18	dB
СТВ	composite triple beat	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz	-	-58	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz	-	-58	dB
CSO	composite second order distortion	60 chs flat; V _o = 46 dBmV; measured at 446.5 MHz	-	-60	dB
d ₂	second order beat	V _o = 46 dBmV note 1	-	-70	dB
V _o	output voltage	$d_{im} = -60 \text{ dB}$ note 2	64	-	dBmV
F	noise figure	f = 450 MHz	_	6	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	-	340	mA

Notes

- $\begin{array}{lll} \text{1.} & \text{f}_{\text{p}} = 55.25 \; \text{MHz}; \; \text{V}_{\text{p}} = 46 \; \text{dBmV}; \\ & \text{f}_{\text{q}} = 391.25 \; \text{MHz}; \; \text{V}_{\text{q}} = 46 \; \text{dBmV}; \\ & \text{measured at f}_{\text{p}} + f_{\text{q}} = 446.5 \; \text{MHz}. \end{array}$
- $\begin{array}{lll} \text{2.} & \text{Measured according to DIN 45004B;} \\ & f_p = 440.25 \text{ MHz; } V_p = V_o; \\ & f_q = 447.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \\ & f_r = 449.25 \text{ MHz; } V_r = V_o -6 \text{ dB;} \\ & \text{measured at } f_p + f_q f_r = 438.25 \text{ MHz.} \\ \end{array}$

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BGY88

FEATURES

- · Excellent linearity
- Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

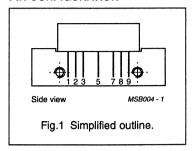
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 40 to 450 MHz at a voltage supply of +24 V (DC) and intended for use as a line-extender.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	33.5	-	35.5	dB
	-	f = 450 MHz	35	_	37	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	-	320	340	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	55	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGY88

CHARACTERISTICS

Bandwidth 40 to 450 MHz; T_{mb} = 35 °C; Z_{S} = Z_{L} = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	33.5	_	35.5	dB
. •		f = 450 MHz	35	-	37	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.5	-	2.5	dB
FL	flatness of frequency response	f = 40 to 450 MHz		-	± 0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	_	-	dB
		f = 80 to 160 MHz;	19	_	-	dB
		f = 160 to 450 MHz	18	-	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	-	_	dB
		f = 80 to 160 MHz;	19	-	-	dB
		f = 160 to 450 MHz	18	_	_	dB
СТВ	composite triple beat	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz		_	-58	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz	-	_	-59	dB
d_2	second order distortion	note 1	-	-	-70	dB
V _o	output voltage	d _{im} = -60 dB; note 2	62	-	_	dB
F	noise figure	f = 450 MHz	_	_	6	dB
I _{tot}	total current consumption	DC value; V _B = +24 V; note 3	-	320	340	mA

Notes

- 1. $f_p = 55.25$ MHz; $V_p = 46$ dBmV; $f_q = 343.25$ MHz; $V_q = 46$ dBmV; measured at $f_p + f_q = 398.5$ MHz
- $\begin{array}{lll} \text{2.} & \text{Measured according to DIN45004B;} \\ f_p = 440.25 \text{ MHz; } V_p = V_o = 62 \text{ dBmV;} \\ f_q = 447.25 \text{ MHz; } V_q = V_o & -6 \text{ dB;} \\ f_r = 449.25 \text{ MHz; } V_r = V_o & -6 \text{ dB;} \\ \text{measured at } f_p + f_q f_r = 438.25 \text{ MHz} \\ \end{array}$
- 3. The module normally operates at $V_B = +24 \text{ V}$, but is able to withstand supply transients up to +30 V.

BGY89

FEATURES

- · Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

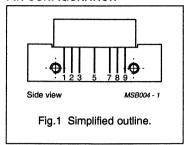
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 40 to 450 MHz at a voltage supply of +24 V (DC) and intended for use as a line-extender.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz;	37	-	39	dB
I _{tot}	1	DC value; V _B = +24 V	_	320	340	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	55	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{case}	operating case temperature range	-20	+100	ç

BGY89

CHARACTERISTICS

Bandwidth 40 to 450 MHz; T_{case} = 35 °C; Z_S = Z_L = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	37	1-	39	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0	_	2.5	dB
FL	flatness of frequency response	f = 40 to 450 MHz	-	_	±0.4	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	-	-	dB
		f = 80 to 160 MHz;	19	-	-	dB
		f = 160 to 450 MHz	18	-	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	-	-	dB
		f = 80 to 160 MHz;	19	-	-	dB
		f = 160 to 450 MHz	18	_	-	dB
СТВ	composite triple beat	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz		-	-58	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz	_	_	-58	dB
CSO	composite second order distortion	60 chs flat; V _o = 46 dBmV; measured at 446.5 MHz	-	-	-58	dB
d ₂	second order distortion	note 1	_	-	-70	dB
V _o	output voltage	d _{im} = -60 dB; note 2	63	_	_	dBmV
F	noise figure	f = 450 MHz	-		5.5	dB
l _{tot}	total current consumption	DC value; V _B = +24 V; note 3	-	320	340	mA

Notes

- 1. $f_p = 55.25$ MHz; $V_p = 46$ dBmV; $f_q = 343.25$ MHz; $V_q = 46$ dBmV; measured at $f_p + f_q = 398.5$ MHz
- 2. Measured according to DIN45004B;

$$\begin{split} &f_{p}=440.25 \text{ MHz; } V_{p}=V_{o}=63 \text{ dBmV;} \\ &f_{q}=447.25 \text{ MHz; } V_{q}=V_{o} -6 \text{ dB;} \\ &f_{r}=449.25 \text{ MHz; } V_{r}=V_{o} -6 \text{ dB;} \end{split}$$

measured at $f_p + f_q - f_r = 438.25 \text{ MHz}$

3. The module normally operates at $V_B = +24 \text{ V}$, but is able to withstand supply transients up to +30 V.

BGY580;BGY581

FEATURES

- Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- Rugged construction
- Optimal reliability ensured by TiPtAu metallized crystals.

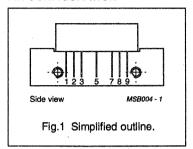
DESCRIPTION

Hybrid amplifier modules for CATV systems operating over a frequency range of 40 to 550 MHz at a voltage supply of +24 V (DC). The BGY580 is intended for use as a pre-amplifier and BGY581 as a final amplifier.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	12	_	13	dB
		f = 550 MHz	12.5	-	14.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V				
	BGY580		_	180	220	mA
	BGY581		- ,	220	240	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	_	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{case}	operating case temperature range	-20	+100	°C

BGY580;BGY581

CHARACTERISTICS

Bandwidth 40 to 550 MHz; $T_{case} = 30$ °C; $Z_S = Z_L = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	12	-	13	dB
P		f = 550 MHz	12.5	-	14.5	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0.5	_	2	dB
FL	flatness of frequency response	f = 40 to 550 MHz	-	-	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	-	 -	dB
		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 550 MHz	18	-	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	-	-	dB
	,	f = 80 to 160 MHz	19	_	-	dB
	-	f = 160 to 550 MHz	18	_	-	dB
СТВ	composite triple beat	77 chs flat; V _o = 44 dBmV; measured at 547.25 MHz				
	BGY580		-	-	-52	dB
	BGY581		-	-	-56	dB
X _{mod}	cross modulation	77 chs flat; $V_o = 44 \text{ dBmV}$; measured at 55.25 MHz				
	BGY580		-	-	<i>–</i> 59	dB
	BGY581		-	-	-62	dB
CSO	composite second order distortion	77 chs flat; V _o = 44 dBmV; measured at 548.5 MHz				
	BGY580		-	_	<i>-</i> 56	dB
	BGY581		_	_	-59	dB
d ₂	second order distortion	note 1				
	BGY580		-	-	-70	dB
	BGY581		-	-	-72	dB
V _o	output voltage	d _{im} = -60 dB note 2				
	BGY580		59	-	-	dBmV
	BGY581		61.5	-	-	dBmV
F	noise figure	f = 550 MHz				
	BGY580		-	-	8.5	dB
	BGY581		_	-	9	dB

BGY580;BGY581

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{tot}	total current consumption	DC value; V _B = +24 V; note 3				
	BGY580		-	180	220	mA
	BGY581		_	220	240	mA ·

Notes

- 1.
 $$\begin{split} \text{f}_{\text{p}} = 55.25 \text{ MHz; V}_{\text{p}} = 44 \text{ dBmV;} \\ \text{f}_{\text{q}} = 493.25 \text{ MHz; V}_{\text{q}} = 44 \text{ dBmV;} \\ \text{measured at f}_{\text{p}} + \text{f}_{\text{q}} = 548.5 \text{ MHz} \end{split}$$
- 2. Measured according to DIN45004B; $\begin{aligned} f_p &= 540.25 \text{ MHz; } V_p = V_o; \\ f_q &= 547.25 \text{ MHz; } V_q = V_p 6 \text{ dB;} \\ f_r &= 549.25 \text{ MHz; } V_r = V_p 6 \text{ dB;} \\ \text{measured at } f_p + f_q f_r = 538.25 \text{ MHz.} \end{aligned}$
- 3. The modules normally operate at $V_B = +24 \text{ V}$, but are able to withstand supply transients up to 30 V.

BGY582;BGY583

FEATURES

- Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- Optimal reliability ensured by TiPtAu metallized crystals.

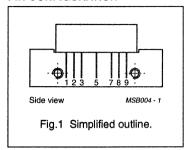
DESCRIPTION

Hybrid amplifier modules for CATV systems operating over a frequency range of 40 to 550 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	13.5	-	14.5	dB
		f = 550 MHz	14.5	-	-	dB
I _{tot}	total current consumption	DC value; V _B = +24 V				
	BGY582		_	180	200	mA
	BGY583		_	220	240	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage		60	dBmV
T _{stg}	storage temperature range	-4 0	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGY582;BGY583

CHARACTERISTICS

Bandwidth 40 to 550 MHz; T_{case} = 30 °C; Z_S = Z_L = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	13.5	_	14.5	dB
r		f = 550 MHz	14.5	-	-	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0.2	-	1.5	dB
FL	flatness of frequency response	f = 40 to 550 MHz	-	_	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	_	-	dB
		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 550 MHz	18	-	_	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	<u> </u>	_	dB
		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 550 MHz	18	- ,	-	dB
СТВ	composite triple beat	77 chs flat; V _o = 44 dBmV; measured at 547.25 MHz				
	BGY582		-	-	-55	dB
	BGY583		-	_	-59	dB
X _{mod}	cross modulation	77 chs flat; V _o = 44 dBmV; measured at 55.25 MHz				
	BGY582		_	-	-58	dB
	BGY583		-	-	61	dB
CSO	composite second order distortion	77 chs flat; V _o = 44 dBmV; measured at 547.25 MHz				
	BGY582		_	-	-55	dB
	BGY583		_	. -	-59	dB
d ₂	second order distortion	note 1				
	BGY582		_	_	-70	dB
	BGY583		_	-	-72	dB
V _o	output voltage	d _{im} = -60 dB note 2				
	BGY582		61.5	-	-	dBmV
	BGY583		64	-	-	dBmV
F	noise figure	f = 550 MHz				
	BGY582		_	-	7.5	dB
	BGY583		_	_	8.5	dB

BGY582;BGY583

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{tot}	total current consumption	DC value; V _B = +24 V; note 3				
	BGY582		_	180	200	mA
	BGY583		_	220	240	mA

Notes

- 1. $f_p = 55.25 \text{ MHz}; V_p = 44 \text{ dBmV};$ $f_q = 493.25 \text{ MHz}; V_q = 44 \text{ dBmV};$ measured at $f_p + f_q = 548.5 \text{ MHz}$

2. Measured according to DIN45004B;
$$f_p = 440.25 \text{ MHz; } V_p = V_o; \\ f_q = 447.25 \text{ MHz; } V_q = V_p -6 \text{ dB;} \\ f_r = 449.25 \text{ MHz; } V_r = V_p -6 \text{ dB;} \\ \text{measured at } f_p + f_q - f_r = 438.25 \text{ MHz.}$$

3. The modules normally operate at V_B = +24 V, but are able to withstand supply transients up to 30 V.



BGY584;BGY585

FEATURES

- Excellent linearity
- · Extremely low noise
- Silicon nitride passivation
- · Rugged construction
- Optimal reliability ensured by TiPtAu metallized crystals.

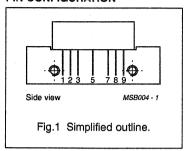
DESCRIPTION

Hybrid amplifier modules for CATV systems operating over a frequency range of 40 to 550 MHz at a voltage supply of +24 V (DC). The BGY584 is intended for use as a pre-amplifier and BGY585 as a final amplifier.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	16.5	-	17.5	dB
		f = 550 MHz	17.6	-	19	dB
I _{tot}	total current consumption	DC value; V _B = +24 V				-
	BGY584		_	180	200	mA
	BGY585		-	220	240	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	_	60	dBmV
T _{stg}	storage temperature range	-4 0	+100	°C
T _{case}	operating case temperature range	-20	+100	°C

BGY584;BGY585

CHARACTERISTICS

Bandwidth 40 to 550 MHz; $T_{case} = 30 \, ^{\circ}\text{C}$; $Z_{S} = Z_{L} = 75 \, \Omega$

gain rable ent s of frequency se eturn losses return losses site triple beat	f = 50 MHz f = 550 MHz f = 40 to 550 MHz 77 chs flat; V _o = 44 dBmV;	16.5 17.6 0.5 - 20 20		17.5 19 2 ± 0.2	dB dB dB
s of frequency se eturn losses return losses site triple beat	f = 40 to 550 MHz f = 40 to 550 MHz f = 40 to 550 MHz f = 40 to 550 MHz 77 chs flat;	0.5		2 ± 0.2	dB dB
s of frequency se eturn losses return losses site triple beat	f = 40 to 550 MHz f = 40 to 550 MHz f = 40 to 550 MHz 77 chs flat;	20	-	± 0.2	dB
se eturn losses return losses site triple beat	f = 40 to 550 MHz f = 40 to 550 MHz 77 chs flat;	20			
return losses site triple beat	f = 40 to 550 MHz 77 chs flat;			-	
site triple beat	77 chs flat;	20	_		dB
·					dB
34	measured at 547.25 MHz			-56	dB
		-	-		
35				-59	dB
nodulation	77 chs flat; V _o = 44 dBmV; measured at 55.25 MHz				
34		-	-	-59	dB
35		-	-	-62	dB
site second distortion	77 chs flat; V _o = 44 dBmV; measured at 548.25 MHz				
34		_	_	-56	dB
35		_	_	-59	dB
d order on	note 1				
34		_	_	68	dB
35			-	-70	dB
voltage	d _{im} = -60 dB note 2				
34		58.5	_	-	dBmV
85		61	_		dBmV
figure	f = 550 MHz				
84		_	-	7	dB
85		_	_	8	dB
urrent mption	DC value; V _B = +24 V; note 3				
		_	180	200	mA
84		_	ł	1	mA
6 8	gure :4 :5 :rrent :nption	gure $f = 550 \text{ MHz}$ 44 55 Trent DC value; nption $V_B = +24 \text{ V}$; note 3	gure	gure	gure

BGY584;BGY585

Notes

- 1. $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 493.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 548.5$ MHz
- 2. Measured according to DIN45004B; $f_p = 540.25 \text{ MHz; } V_p = V_o; \\ f_q = 547.25 \text{ MHz; } V_q = V_p 6 \text{ dB;} \\ f_r = 549.25 \text{ MHz; } V_r = V_p 6 \text{ dB;} \\ \text{measured at } f_p + f_q f_r = 538.25 \text{ MHz.}$
- 3. The modules normally operate at $V_B = +24 \text{ V}$, but are able to withstand supply transients up to 30 V.

BGY584;BGY585

CHARACTERISTICS

Bandwidth 40 to 450 MHz; $T_{case} = 30 \,^{\circ}\text{C}$; $Z_{s} = Z_{L} = 75 \,^{\circ}\Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	16.5	-	17.5	dB
P 1.		f = 450 MHz	17.4	-	18.8	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.5	_	1.8	dB
FL	flatness of frequency response	f = 40 to 450 MHz	-	_	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	-	-	dB
		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 450 MHz	18	-	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	 - 1	-	dB
22		f = 80 to 160 MHz	19	_]_	dB
		f = 160 to 450 MHz	18	_	-	dB
СТВ	composite triple beat	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz				
	BGY584		_	-	-58	dB
	BGY585		_	-	-61	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz				
	BGY584		_	-	-58	dB
	BGY585		-	-	-61	dB
CSO	composite second order distortion	60 chs flat; V _o = 46 dBmV; measured at 446.5 MHz				
	BGY584		_	-	-58	dB
	BGY585		_	-	-61	dB
d ₂	second order distortion	note 1				
	BGY584		_	-	-73	dB
	BGY585		_	_	-75	dB
V _o	output voltage	d _{im} = -60 dB note 1				
	BGY584		61.5	_	-	dBmV
	BGY585		64	-	-	dBmV
F	noise figure	f = 450 MHz				
	BGY584		_	-	6	dB
	BGY585		_	_	7	dB

BGY584;BGY585

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{tot}	total current consumption	DC value; V _B = +24 V; note 2				
	BGY584			180	200	mA
	BGY585		_	220	240	mA

Notes

- 1. f_p = 55.25 MHz; V_p = 46 dBmV; f_q = 391.25 MHz; V_q = 46 dBmV; measured at f_p + f_q = 446.5 MHz
- 2. Measured according to DIN45004B;
 $$\begin{split} f_p &= 440.25 \text{ MHz; } V_p = V_o; \\ f_q &= 447.25 \text{ MHz; } V_q = V_p 6 \text{ dB;} \\ f_r &= 449.25 \text{ MHz; } V_r = V_p 6 \text{ dB;} \\ \text{measured at } f_p + f_q f_r = 438.25 \text{ MHz.} \end{split}$$
- 3. The modules normally operate at $V_B = +24 \text{ V}$, but are able to withstand supply transients up to 30 V.

BGY584A;BGY585A

FEATURES

- · Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- Optimal reliability ensured by TiPtAu metallized crystals.

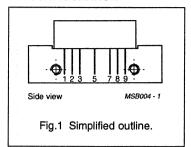
DESCRIPTION

Hybrid amplifier modules for CATV systems operating over a frequency range of 40 to 550 MHz at a voltage supply of +24 V (DC). The BGY584A is intended for use as a pre-amplifier and BGY585A as a final amplifier.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	17.7	-	18.7	dB
		f = 550 MHz	18.8	_	20	dB
I _{tot}	total current consumption	DC value; V _B = +24 V				
	BGY584A		-	180	200	mA
	BGY585A		-	220	240	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{case}	operating case temperature range	-20	+100	°C

BGY584A;BGY585A

CHARACTERISTICS

Bandwidth 40 to 550 MHz; $T_{case} = 30 \, ^{\circ}C; Z_{S} = Z_{L} = 75 \, \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	17.7	-	18.7	dB
۲		f = 550 MHz	18.8		20	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0.5	_	2	dB
FL	flatness of frequency response	f = 40 to 550 MHz	-	<u>-</u>	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	-	-	dB
		f = 80 to 160 MHz	19	_	_	dB
		f = 160 to 550 MHz	18	-	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	_		dB
22		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 550 MHz	18	-	-	dB
СТВ	composite triple beat	77 chs flat; V _o = 44 dBmV; measured at 547.25 MHz				
	BGY584A		-	-	-56	dB
	BGY585A		_	-	-59	dB
X _{mod}	cross modulation	77 chs flat; V _o = 44 dBmV; measured at 55.25 MHz				
	BGY584A		_	-	-59	dB
	BGY585A		-	_	-62	dB
CSO	composite second order distortion	60 chs flat; V _o = 44 dBmV; measured at 547.25 MHz				
	BGY584A		_	_	-55	dB
	BGY585A		-	_	-59	dB
d ₂	second order distortion	note 1				
	BGY584A		-	-	-70	dB
	BGY585A		-	-	-72	dB
V _o	output voltage	d _{im} = -60 dB note 2				
	BGY584A		59	-	-	dBmV
	BGY585A		61.5			dBmV
F	noise figure	f = 550 MHz				
	BGY584A		_	-	7	dB
	BGY585A		_	_	8	dB

BGY584A;BGY585A

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{tot}	total current consumption	DC value; V _B = +24 V; note 3				
	BGY584A		_	180	200	mA
	BGY585A		_	220	240	mA

Notes

- 1. $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 493.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 548.5$ MHz
- 2. Measured according to DIN45004B;

fl_p = 540.25 MHz; $V_p = V_o$; $f_q = 547.25$ MHz; $V_q = V_p - 6$ dB; $f_r = 549.25$ MHz; $V_r = V_p - 6$ dB; measured at $f_p + f_q - f_r = 538.25$ MHz.

3. The modules normally operate at $V_B = +24 \text{ V}$, but are able to withstand supply transients up to 30 V.

BGY584A;BGY585A

CHARACTERISTICS

Bandwidth 40 to 450 MHz; $T_{case} = 30$ °C; $Z_{S} = Z_{L} = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	17.7	-	18.7	dB
•		f = 450 MHz	18.6	-	19.8	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.5	-	1.8	dB
FL	flatness of frequency response	f = 40 to 450 MHz	-	-	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	_	-	dB
		f = 80 to 160 MHz	19	_	-	dB
		f = 160 to 450 MHz	18	-	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	_	 -	dB
		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 450 MHz	18	-	-	dB
СТВ	composite triple beat	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz				
	BGY584A		_	_	-57	dB
	BGY585A		_	-	-61	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz				
	BGY584A		_	_	-58	dB
	BGY585A		-	_	-61	dB
CSO	composite second order distortion	60 chs flat; V _o = 46 dBmV; measured at 446.5 MHz				
	BGY584A		_	-	-58	dB
	BGY585A		_	_	-61	dB
d ₂	second order distortion	note 1				
	BGY584A		_	-	-73	dB
	BGY585A		-	-	-75	dB
V _o	output voltage	d _{im} = -60 dB note 2				
	BGY584A		61.5	-	-	dBmV
	BGY585A		64	-		dBmV
F	noise figure	f = 450 MHz				
	BGY584A		-	-	6	dB
	BGY585A		_	_	7	dB

BGY584A;BGY585A

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{tot}	total current consumption	DC value; V _B = +24 V; note 3				
	BGY584A		_	180	200	mA
	BGY585A		_	220	240	mA

Notes

- 1. f_p = 55.25 MHz; V_p = 46 dBmV; f_q = 391.25 MHz; V_q = 46 dBmV; measured at f_p + f_q = 446.5 MHz
- 2. Measured according to DIN45004B; $\begin{array}{l} f_p = 440.25 \text{ MHz; } V_p = V_o; \\ f_q = 447.25 \text{ MHz; } V_q = V_p 6 \text{ dB;} \\ f_r = 449.25 \text{ MHz; } V_r = V_p 6 \text{ dB;} \\ \text{measured at } f_p + f_q f_r = 438.25 \text{ MHz.} \end{array}$
- 3. The modules normally operate at $V_B = +24 \text{ V}$, but are able to withstand supply transients up to 30 V.

BGY586;BGY587

FEATURES

- Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- Optimal reliability ensured by TiPtAu metallized crystals.

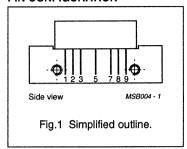
DESCRIPTION

Hybrid amplifier modules for CATV systems operating over a frequency range of 40 to 550 MHz at a voltage supply of +24 V (DC). The BGY586 is intended for use as a pre-amplifier and BGY587 as a final amplifier.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	21.5	-	22.5	dB
		f = 550 MHz	22	-	_	dB
I _{tot}	total current consumption	DC value; V _B = +24 V				
	BGY586		-	180	200	mA
	BGY587		_	220	240	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	_	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{case}	operating case temperature range	-20	+100	ç

BGY586;BGY587

CHARACTERISTICS

Bandwidth 40 to 550 MHz; $T_{case} = 30$ °C; $Z_{S} = Z_{L} = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz	21.5	_	22.5	dB
'		f = 550 MHz	22	_]-	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0.2	_	1.5	dB
FL	flatness of frequency response	f = 40 to 550 MHz	-	-	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	-]-	dB
		f = 80 to 160 MHz	19	_	-	dB
		f = 160 to 550 MHz	18	-	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	-	-	dB
		f = 80 to 160 MHz	19	_	-	dB
		f = 160 to 550 MHz	18	_	1-	dB
СТВ	composite triple beat	77 chs flat; V _o = 44 dBmV; measured at 547.25 MHz				
	BGY586		_	-	-53	dB
	BGY587		_	-	-57	dB
X _{mod}	cross modulation	77 chs flat; V _o = 44 dBmV; measured at 55.25 MHz				
	BGY586		-	-	-55	dB
	BGY587			-	-59	dB
d ₂	second order distortion	note 1				
	BGY586		_	-	-62	dB
	BGY587		-	-	-66	dB
V _o	output voltage	d _{im} = -60 dB note 2				
	BGY586		58.5	-	-	dBmV
	BGY587		61	_	_	dBmV
F	noise figure	f = 550 MHz				
	BGY586		_	-	6.5	dB
	BGY587		_	_	7	dB
I _{tot}	total current consumption	DC value; V _B = +24 V; note 3				
	BGY586		-	180	200	mA
	BGY587		-	220	240	mA

BGY586;BGY587

Notes

1. $f_p = 55.25 \text{ MHz}$; $V_p = 44 \text{ dBmV}$; $f_q = 493.25 \text{ MHz}$; $V_q = 44 \text{ dBmV}$; measured at $f_p + f_q = 548.5 \text{ MHz}$ 2. Measured according to DIN45004B; $f_p = 540.25 \text{ MHz}$; $V_p = V_o$; $f_q = 547.25 \text{ MHz}$; $V_q = V_p - 6 \text{ dB}$;

 $f_r = 549.25 \text{ MHz}; V_r = V_p - 6 \text{ dB};$ measured at $f_p + f_q - f_r = 538.25 \text{ MHz}.$

3. The modules normally operate at $V_B = +24 \text{ V}$, but are able to withstand supply transients up to 30 V.



BGY587B

FEATURES

- Excellent linearity
- Extremely low noise
- · Silicon nitride passivation
- Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

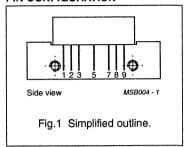
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 40 to 550 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	26.2	27.8	dB
		f = 550 MHz	27.5	_	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	340	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	55	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C
V _B	DC supply voltage	_	+28	V

BGY587B

CHARACTERISTICS

Bandwidth 40 to 550 MHz; $T_{case} = 35$ °C; $Z_{S} = Z_{L} = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	26.2	27.8	dB
'		f = 550 MHz	27.5	-	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0.5	2.5	dB
FL	flatness of frequency response	f = 40 to 550 MHz	-	± 0.4	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 550 MHz	18	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	_	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 550 MHz	18	-	dB
СТВ	composite triple beat	77 chs flat; V _o = 44 dBmV; measured at 547.25 MHz	-	-57	dB
X _{mod}	cross modulation	77 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	-	-60	dB
CSO	composite second order distortion	77 chs flat; V _o = 44 dBmV; measured at 548.5 MHz	-	-57	dB
d ₂	second order distortion	note 1	_	-68	dB
V _o	output voltage	d _{im} = -60 dB note 2	61	_	dBmV
F	noise figure	f = 550 MHz	_	6.5	dB
l _{tot}	total current consumption	DC value; $V_B = +24 \text{ V}$; note 3	-	340	mA

Notes

- 1. $f_p = 55.25 \text{ MHz}; V_p = 44 \text{ dBmV};$ $f_q = 493.25 \text{ MHz}; V_q = 44 \text{ dBmV};$ measured at $f_p + f_q = 548.5 \text{ MHz}$
- 2. Measured according to DIN45004B;

 $f_p = 540.25 \text{ MHz}; V_p = V_o = 66.5 \text{ dBmV};$

 $f_q^P = 547.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$

 $f_r = 549.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$

measured at $f_p + f_q - f_r = 538.25 \text{ MHz}$

3. The module normally operates at $V_B = +24 \text{ V}$, but is able to withstand supply transients up to +30 V.

BGY588

FEATURES

- Excellent linearity
- · Extremely low noise
- Silicon nitride passivation
- · Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

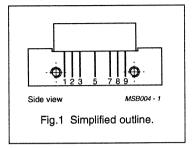
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 40 to 550 MHz at a voltage supply of +24 V (DC) and intended for use as a line-extender.

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	33.5	_	35.5	dB
		f = 550 MHz	35	-	37	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	320	340	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
Vi	RF input voltage	_	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGY588

CHARACTERISTICS

Bandwidth 40 to 550 MHz; T_{case} = 30 °C; Z_{S} = Z_{L} = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz;	33.5	-	35.5	dB
· ·		f = 550 MHz	35	_	37	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0	-	2.5	dB
FL	flatness of frequency response	f = 40 to 550 MHz	-	-	± 0.4	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	-	T-	dB
		f = 80 to 160 MHz;	19	-	-	dB
		f = 160 to 550 MHz	18	_	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	_	T-	dB
		f = 80 to 160 MHz;	19	-	-	dB
		f = 160 to 550 MHz	18	-	_	dB
СТВ	composite triple beat	77 chs flat; V _o = 44 dBmV; measured at 547.25 MHz	-	_	-57	dB
X _{mod}	cross modulation	77 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	-	_	-59	dB
CSO	composite second order distortion	77 chs flat; V _o = 44 dBmV; measured at 548.5 MHz	-	_	-57	dB
d ₂	second order distortion	note 1	-	-	-68	dB
V _o	output voltage	d _{im} = -60 dB note 2	61	-	_	dBmV
F	noise figure	f = 550 MHz	_	_	6.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V; note 3	_	320	340	mA

Notes

1. $f_p = 55.25 \text{ MHz}; V_p = 44 \text{ dBmV};$ $f_q = 493.25 \text{ MHz}; V_q = 44 \text{ dBmV};$ measured at $f_p + f_q = 548.5 \text{ MHz}$

2. Measured according to DIN45004B;

 $f_p = 540.25 \text{ MHz}; V_p = V_o = 66.5 \text{ dBmV};$

 $f_q = 547.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$

 $f_r = 549.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$

measured at $f_p + f_q - f_r = 538.25 \text{ MHz}$

3. The module normally operates at $V_B = +24 \text{ V}$, but is able to withstand supply transients up to +30 V.

BGY588

CHARACTERISTICS

Bandwidth 40 to 450 MHz; $T_{case} = 35$ °C; $Z_{s} = Z_{L} = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	33.5	1-	35.5	dB
•		f = 450 MHz	35	-	37	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.5	_	2.5	dB
FL	flatness of frequency response	f = 40 to 450 MHz	-	-	± 0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	_	-	dB
		f = 80 to 160 MHz;	19	_	-	dB
		f = 160 to 450 MHz	18	-	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	-	Ī-	dB
		f = 80 to 160 MHz;	19	_	-	dB
		f = 160 to 450 MHz	18		-	dB
CTB	composite triple beat	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz	-	_	-61	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz	-	_	-59	dB
CSO	composite second order distortion	60 chs flat; V _o = 46 dBmV; measured at 446.5 MHz		-	-59	dB
d ₂	second order distortion	note 1	_	-	-72	dB
V _o	output voltage	d _{im} = -60 dB note 2	64	-	_	dBmV
F	noise figure	f = 450 MHz	-	_	6	dB
I _{tot}	total current consumption	DC value; V _B = +24 V; note 3		320	340	mA ·

Notes

- 1. $f_p = 55.25 \text{ MHz}$; $V_p = 46 \text{ dBmV}$; $f_q = 391.25 \text{ MHz}$; $V_q = 46 \text{ dBmV}$; measured at $f_p + f_q = 446.5 \text{ MHz}$
- 2. Measured according to DIN45004B;

 $f_p = 440.25 \text{ MHz}; V_p = V_o = 66.5 \text{ dBmV};$

 $f_q = 447.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$

 $f_r = 449.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$

measured at $f_p + f_q - f_r = 438.25 \text{ MHz}$

3. The module normally operates at $V_B = +24 \text{ V}$, but is able to withstand supply transients up to +30 V.



BGY681

FEATURES

- · Excellent linearity
- · Extremely low noise
- Silicon nitride passivation
- · Rugged construction
- Gold metallization ensures excellent reliability.

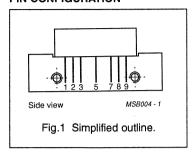
DESCRIPTION

Hybrid high dynamic range amplifier module designed for CATV systems operating over a frequency range of 40 to 600 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	12	13	dB
		f = 600 MHz	12.7	-	dB
I _{tot}	total current consumption	DC value;	_	240	mA
		$V_{B} = +24 \text{ V}$			

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	60	dBmV
T _{stg}	storage temperature range	-4 0	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGY681

CHARACTERISTICS

 $T_{case} = 30 \,^{\circ}C; Z_{S} = Z_{L} = 75 \,\Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _D	power gain	f = 50 MHz;	12	13	dB
•		f = 600 MHz	12.7	-	dB
SL	slope cable equivalent	f = 40 to 600 MHz	0.7	2.2	dB
FL	flatness of frequency response	f = 40 to 600 MHz		± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	_	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 600 MHz	18	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 600 MHz	18	-	dB
СТВ	composite triple beat	85 chs flat; V _o = 44 dBmV; measured at 595.25 MHz	_	-52	dB
X _{mod}	cross modulation	85 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	-	-58	dB
CSO	composite second order distortion	85 chs flat; V _o = 44 dBmV; measured at 596.5 MHz	_	-57	dB
d ₂	second order distortion	note 1	_	-70	dB
V _o	output voltage	d _{im} = -60 dB note 2	59.5	_	dBmV
F	noise figure	f = 600 MHz	-	9.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	240	mA

Notes

1. $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 541.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 596.5$ MHz

2. $f_p = 590.25 \text{ MHz}$; $V_p = V_o$; $f_q = 597.25 \text{ MHz}$; $V_q = V_o -6 \text{ dB}$; $f_r = 599.25 \text{ MHz}$; $V_r = V_o -6 \text{ dB}$; measured at $f_p + f_q - f_r = 588.25 \text{ MHz}$.

BGY683

FEATURES

- Excellent linearity
- Extremely low noise
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

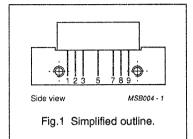
DESCRIPTION

Hybrid high dynamic range amplifier module for CATV systems operating over a frequency range of 40 to 600 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	13.5	14.5	dB
		f = 600 MHz	14.5	-	dB
I _{tot}	total current	DC value;	-	240	mA
	consumption	$V_B = +24 \text{ V}$			

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	MBOL PARAMETER		MAX.	UNIT
V _i	RF input voltage	-	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

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BGY683

CHARACTERISTICS

 T_{case} = 30 °C; Z_{S} = Z_{L} = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	13.5	14.5	dB
,		f = 600 MHz	14.5	-	dB
SL	slope cable equivalent	f = 40 to 600 MHz	0.2	1.7	dB
FL	flatness of frequency response	f = 40 to 600 MHz	-	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 600 MHz	18	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	19	-	dB
	• •	f = 160 to 600 MHz	18	-	dB
СТВ	composite triple beat	85 chs flat; V _o = 44 dBmV; measured at 595.25 MHz	_	-55	dB
X_{mod}	cross modulation	85 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	-	-59	dB
CSO	composite second order distortion	85 chs flat; V _o = 44 dBmV; measured at 596.5 MHz	_	-57	dB
d ₂	second order distortion	note 1	T-	-68	dB
V _o	output voltage	d _{im} = -60 dB (DIN45004B) note 2	58	_	dBmV
F	noise figure	f = 600 MHz	-	9	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	240	mA

Notes

```
1. f_p = 55.25 \text{ MHz}; V_p = 44 \text{ dBmV}; f_q = 541.25 \text{ MHz}; V_q = 44 \text{ dBmV}; measured at <math>f_p + f_q = 596.5 \text{ MHz}
```

2. $f_p = 590.25 \text{ MHz}$; $V_p = V_o$; $f_q = 597.25 \text{ MHz}$; $V_q = V_o -6 \text{ dB}$; $f_r = 599.25 \text{ MHz}$; $V_r = V_o -6 \text{ dB}$; measured at $f_p + f_q - f_r = 588.25 \text{ MHz}$.

BGY685

FEATURES

- Excellent linearity
- Extremely low noise
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

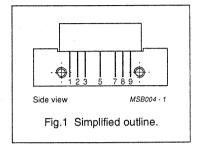
DESCRIPTION

Hybrid high dynamic range amplifier module designed for applications in CATV systems operating over a frequency range of 40 MHz to 600 MHz operating with a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	16.5	17.5	dB
	496	f = 600 MHz	17.8		dB
I _{tot}	total current consumption		-	240	mA
		$V_B = +24 V$			

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V,	RF input voltage	_	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C.
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGY685

CHARACTERISTICS

 $T_{case} = 30 \,^{\circ}C; Z_{S} = Z_{L} = 75 \,\Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	16.5	17.5	dB
•		f = 600 MHz	17.8	_	dB
SL	slope cable equivalent	f = 40 to 600 MHz	0.5	2.2	dB
FL	flatness of frequency response	f = 40 to 600 MHz	_	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 600 MHz	18	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 600 MHz	18	_	dB
СТВ	composite triple beat	85 chs flat; $V_o = 44 \text{ dBmV}$; measured at 595.25 MHz	_	-55	dB
X_{mod}	cross modulation	85 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	-	-60	dB
CSO	composite second order distortion	85 chs flat; V _o = 44 dBmV; measured at 596.5 MHz	-	-56	dB
d ₂	second order distortion	note 1	-	-68	dB
V _o	output voltage	d _{im} = -60 dB (DIN45004B) note 2	60	_	dBmV
F	noise figure	f = 600 MHz	_	8.5	dB
l _{tot}	total current consumption	DC value; V _B = +24 V	_	240	mA

Notes

```
1. f_p = 55.25 MHz; V_p = 44 dBmV; f_q = 541.25 MHz; V_q = 44 dBmV; measured at f_p + f_q = 596.5 MHz
```

2. $f_p = 590.25 \text{ MHz}; V_p = V_o;$ $f_q = 597.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$ $f_r = 599.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$ measured at $f_p + f_q - f_r = 588.25 \text{ MHz}.$

BGY685A

FEATURES

- Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- Gold metallization ensures excellent reliability.

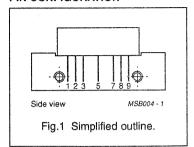
DESCRIPTION

Special Super High Dynamic range amplifier module designed for applications in CATV systems with a bandwidth of 40 to 600 MHz operating with a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	17.7	18.7	dB
		f = 600 MHz	19	-	dB
I _{tot}		DC value;	_	240	mA
		$V_B = +24 \text{ V}$			

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGY685A

CHARACTERISTICS

 $T_{case} = 30 \, ^{\circ}C; \, Z_{S} = Z_{L} = 75 \, \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	17.7	18.7	dB
		f = 600 MHz	19	-	dB
SL	slope cable equivalent	f = 40 to 600 MHz	0.5	2.2	dB
FL	flatness of frequency response	f = 40 to 600 MHz	-	± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz	20	_	dB
		f = 80 to 160 MHz	19	_	dB
		f = 160 to 600 MHz	18	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	_	dB
		f = 80 to 160 MHz	19	-	dB
		f = 160 to 600 MHz	18	-	dB
CTB	composite triple beat	85 chs flat; V _o = 44 dBmV; measured at 595.25 MHz	-	-55	dB
X_{mod}	cross modulation	85 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	_	-60	dB
CSO	composite second order distortion	85 chs flat; V _o = 44 dBmV; measured at 596.5 MHz	-	-56	dB
d ₂	second order distortion	note 1	-	-70	dB
V _o	output voltage	d _{im} = -60 dB (DIN45004B) note 2	60		dBmV
F	noise figure	f = 600 MHz	_	8.5	dB
l _{tot}	total current consumption	DC value; V _B = +24 V		240	mA

Notes

```
1. f_p = 55.25 \text{ MHz}; V_p = 44 \text{ dBmV}; \\ f_q = 541.25 \text{ MHz}; V_q = 44 \text{ dBmV}; \\ \text{measured at } f_p + f_q = 596.5 \text{ MHz}
```

2. $f_p = 590.25 \text{ MHz}$; $V_p = V_o$; $f_q = 597.25 \text{ MHz}$; $V_q = V_o -6 \text{ dB}$; $f_r = 599.25 \text{ MHz}$; $V_r = V_o -6 \text{ dB}$; measured at $f_p + f_q - f_r = 588.25 \text{ MHz}$.

BGY685AL

FEATURES

- · Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

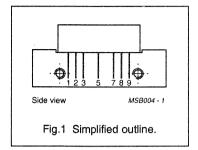
DESCRIPTION

Hybrid high dynamic range amplifier module designed for applications in CATV systems operating over a frequency range of 40 MHz to 600 MHz operating with a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	18	19	dB
		f = 600 MHz	18.5	-	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	250	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	_	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGY685AL

CHARACTERISTICS

Bandwidth 40 to 600 MHz; $T_{case} = 30$ °C; $Z_{S} = Z_{L} = 75~\Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	18	19	dB
-		f = 600 MHz	18.5	_	dB
SL	slope cable equivalent	f = 40 to 600 MHz	0.5	2.0	dB
FL	flatness of frequency response	f = 40 to 600 MHz	-	± 0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	_	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 600 MHz	18	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	_	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 600 MHz	18	-	dB
CTB	composite triple beat	85 chs flat; V _o = 44 dBmV; measured at 595.25 MHz		-57	dB
X _{mod}	cross modulation	85 chs flat; V _o = 44 dBmV; measured at 55.25 MHz		-55	dB
CSO	composite second order distortion	85 chs flat; V _o = 44 dBmV; measured at 596.5 MHz		-56	dB
d ₂	second order distortion	note 1	-	-70	dB
V _o	output voltage	d _{im} = -60 dB note 2	60	_	dBmV
F	noise figure	f = 600 MHz	num.	5.0	dB
l _{tot}	total current consumption	DC value; V _B = +24 V	-	250	mA

Notes

1. $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 541.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 596.5$ MHz

 $\begin{array}{lll} \text{2.} & f_p = 590.25 \text{ MHz; } V_p = V_o; \\ & f_q = 597.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \\ & f_r = 599.25 \text{ MHz; } V_r = V_o -6 \text{ dB;} \\ & \text{measured at } f_p + f_q - f_r = 588.25 \text{ MHz.} \\ \end{array}$

BGY685AL

CHARACTERISTICS

Bandwidth 40 to 550 MHz; $T_{case} = 30$ °C; $Z_{S} = Z_{L} = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	18	19	dB
		f = 550 MHz	18.5		dB
SL	slope cable equivalent	f = 40 to 550 MHz	0.5	2.0	dB
FL	flatness of frequency response	f = 40 to 550 MHz	-	± 0.3	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	_	dB
		f = 80 to 160 MHz;	19	_	dB
		f = 160 to 550 MHz	18		dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	_	dB
		f = 80 to 160 MHz;	19	- "	dB
		f = 160 to 550 MHz	18	_	dB
СТВ	composite triple beat	77 chs flat; V _o = 44 dBmV; measured at 547.25 MHz	_	-58	dB
X _{mod}	cross modulation	77 chs flat; V _o = 44 dBmV; measured at 55.25 MHz		-56	dB
CSO	composite second order distortion	77 chs flat; V _o = 44 dBmV; measured at 548.5 MHz		-58	dB
d ₂	second order distortion	note 1	-	-72	dB
V _o	output voltage	d _{im} = -60 dB note 2	61.5		dBmV
F	noise figure	f = 550 MHz	-	4.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	250	mA

Notes

- 1. $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 493.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 548.5$ MHz
- $\begin{array}{lll} \text{2.} & f_p = 540.25 \text{ MHz; } V_p = V_o; \\ f_q = 547.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \\ f_r = 549.25 \text{ MHz; } V_r = V_o -6 \text{ dB;} \\ \text{measured at } f_p + f_q f_r = 538.25 \text{ MHz.} \end{array}$

BGY685AL

CHARACTERISTICS

Bandwidth 40 to 450 MHz; $T_{case} = 30$ °C; $Z_{S} = Z_{L} = 75 \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	18	19	dB
P		f = 450 MHz	18.3	-	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.3	1.5	dB
FL	flatness of frequency response	f = 40 to 450 MHz		± 0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	19	-	dB
		f = 160 to 450 MHz	18	_	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	-	dB
22		f = 80 to 160 MHz;	19	_	dB
		f = 160 to 450 MHz	18	-	dB
СТВ	composite triple beat	60 chs flat; V _o = 46 dBmV; measured at 445.25 MHz	_	-58	dB
X _{mod}	cross modulation	60 chs flat; V _o = 46 dBmV; measured at 55.25 MHz		-54	dB
CSO	composite second order distortion	60 chs flat; V _o = 46 dBmV; measured at 446.5 MHz	_	-58	dB
d ₂	second order distortion	note 1	-	- 70	dB
V _o	output voltage	d _{im} = -60 dB note 2	62.5	_	dBmV
F	noise figure	f = 450 MHz	-	4.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V		250	mA

Notes

1. $f_p = 55.25$ MHz; $V_p = 46$ dBmV; $f_q = 391.25$ MHz; $V_q = 46$ dBmV; measured at $f_p + f_q = 446.5$ MHz

2. $f_p = 440.25 \text{ MHz}; V_p = V_o;$ $f_q = 447.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$ $f_r = 449.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$ measured at $f_p + f_q - f_r = 438.25 \text{ MHz}.$

BGY687

FEATURES

- Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

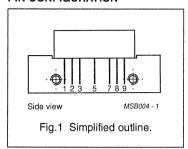
DESCRIPTION

Hybrid high dynamic range amplifier module designed for CATV systems operating over a frequency range of 40 to 600 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	21	22	dB
		f = 600 MHz	22	_	dB
I _{tot}	total current consumption		_	240	mA
		$V_B = +24 V$			

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_{i}	RF input voltage	_	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGY687

CHARACTERISTICS

 $T_{case} = 30 \,^{\circ}\text{C}; Z_{s} = Z_{i} = 75 \,\Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	21	22	dB
р		f = 600 MHz	22	-	dB
SL	slope cable equivalent	f = 40 to 600 MHz	0.8	2.2	dB
FL	flatness of frequency response	f = 40 to 600 MHz	-	0.2	dB
S ₁₁	input return losses	f = 40 to 80 MHz; f = 80 to 160 MHz; f = 160 to 600 MHz	20 19 18	- - -	dB dB dB
S ₂₂	output return losses	f = 40 to 80 MHz; f = 80 to 160 MHz; f = 160 to 550 MHz; f = 550 to 600 MHz	20 19 18 16	- - -	dB dB dB dB
СТВ	composite triple beat	85 chs flat; V _o = 44 dBmV; measured at 595.25 MHz	_	-54	dB
X _{mod}	cross modulation	85 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	_	-54	dB
CSO	composite second order distortion	85 chs flat; V _o = 44 dBmV; measured at 596.25 MHz	-	-52	dB
d ₂	second order distortion	note 1		-66	dB
V _o	output voltage	d _{im} = -60 dB note 2	58	_	dBmV
F	noise figure	f = 600 MHz	_	6.5	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	_	240	mA

Notes

1. $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 541.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 596.5$ MHz

 $\begin{array}{lll} \text{2.} & f_p = 590.25 \text{ MHz; } V_p = V_o; \\ & f_q = 597.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \\ & f_r = 599.25 \text{ MHz; } V_r = V_o -6 \text{ dB;} \\ & \text{measured at } f_p + f_q - f_r = 588.25 \text{ MHz.} \\ \end{array}$

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BGY687B

FEATURES

- Excellent linearity
- · Extremely low noise
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

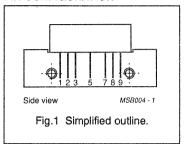
DESCRIPTION

Hybrid high dynamic range amplifier module designed for CATV systems operating over a frequency range of 40 to 600 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	26.2	27.8	dB
		f = 600 MHz	27.8	-	dB
I _{tot}	total current consumption	DC value;	_	340	mA
		$V_{\rm B} = +24 \text{ V}$			

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	60	dBmV
T _{stg}	storage temperature range		+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGY687B

CHARACTERISTICS

 $T_{case} = 30 \,^{\circ}C; Z_{S} = Z_{L} = 75 \,\Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
 G _р	power gain	f = 50 MHz;	26.2	27.8	dB
ν .		f = 600 MHz	27.8	-	dB
SL	slope cable equivalent	f = 40 to 600 MHz	0.8	2.8	dB
FL	flatness of frequency response	f = 40 to 600 MHz	_	± 0.4	dB
S ₁₁	input return losses	f = 40 to 80 MHz; f = 80 to 160 MHz; f = 160 to 600 MHz	20 19 18	- - -	dB dB dB
S ₂₂	output return losses	f = 40 to 80 MHz; f = 80 to 160 MHz; f = 160 to 600 MHz	20 19 18		dB dB dB
СТВ	composite triple beat	85 chs flat; V _o = 44 dBmV; measured at 595.25 MHz	_	-53	dB
X _{mod}	cross modulation	85 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	_	-58	dB
CSO	composite second order distortion	85 chs flat; V _o = 44 dBmV; measured at 596.25 MHz	_	-54	dB
d ₂	second order distortion	note 1	_	-66	dB
V _o	output voltage	$d_{im} = -60 \text{ dB (DIN45004B)}$ note 2	60	-	dBmV
F	noise figure	f = 600 MHz	-	7	dB
l _{tot}	total current consumption	DC value; V _B = +24 V	-	340	mA

Notes

1. $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 541.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 596.5$ MHz

 $\begin{array}{lll} \text{2.} & f_p = 590.25 \text{ MHz; } V_p = V_o; \\ f_q = 597.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \\ f_r = 599.25 \text{ MHz; } V_r = V_o -6 \text{ dB;} \\ \text{measured at } f_p + f_q - f_r = 588.25 \text{ MHz.} \\ \end{array}$

BGY785A

FEATURES

- Excellent linearity
- · Extremely low noise
- Silicon nitride passivation
- · Rugged construction
- Gold metallization ensures excellent reliability.

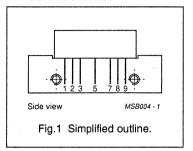
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 40 to 750 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	18	19	dB
		f = 750 MHz	18.5	_	dB
I _{tot}	total current consumption	DC value;	-	235	mA
		$V_B = +24 \text{ V}$			

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGY785A

CHARACTERISTICS

 T_{case} = 30 °C; Z_{S} = Z_{L} = 75 Ω ; Bandwidth 40 to 750 MHz;

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	18	19	dB
۲		f = 750 MHz	18.5	_	dB
SL	slope cable equivalent	f = 40 to 750 MHz	0	1.5	dB
FL	flatness of frequency response	f = 40 to 750 MHz	_	± 0.5	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	-	dB
		f = 80 to 160 MHz;	18.5	_	dB
		f = 160 to 320 MHz	17	-	dB
		f = 320 to 640 MHz;	15.5	-	dB
		f = 640 to 750 MHz	14	-	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20		dB
22		f = 80 to 160 MHz;	18.5	-	dB
		f = 160 to 320 MHz	17	_	dB
	a distance of the second of th	f = 320 to 640 MHz;	15.5	-	dB
		f = 640 to 750 MHz	14	-	dB
CTB	composite triple beat	110 chs flat; V _o = 44 dBmV; measured at 745.25 MHz	-	-53	dB
X _{mod}	cross modulation	110 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	-	-57	dB
CSO	composite second order distortion	110 chs flat; V _o = 44 dBmV; measured at 746.5 MHz	-	-53	dB
d ₂	second order distortion	note 1	_	-65	dB
V _o	output voltage	d _{im} = -60 dB note 2	59	_	dBmV
F	noise figure	f = 750 MHz	_	9	dB
I _{tot}	total current consumption	DC value; V _B = +24 V		235	mA

Notes

```
1. f_p = 55.25 MHz; V_p = 44 dBmV; f_q = 691.25 MHz; V_q = 44 dBmV; measured at f_p + f_q = 746.5 MHz
```

 $\begin{array}{lll} \text{2.} & f_p = 740.25 \text{ MHz; } V_p = V_o; \\ & f_q = 747.25 \text{ MHz; } V_q = V_o -6 \text{ dB;} \\ & f_r = 749.25 \text{ MHz; } V_r = V_o -6 \text{ dB;} \\ & \text{measured at } f_p + f_q - f_r = 738.25 \text{ MHz.} \end{array}$

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BGY787

FEATURES

- · Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- Gold metallization ensures excellent reliability.

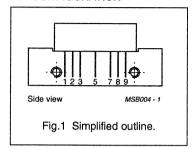
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 40 to 750 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	21	22	dB
		f = 750 MHz	22	-	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	-	235	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	-	60	dBmV
T _{sig}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

BGY787

CHARACTERISTICS

 $T_{case} = 30 \, ^{\circ}C; Z_{S} = Z_{L} = 75 \, \Omega;$ Bandwidth 40 to 750 MHz;

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	21	22	dB
		f = 750 MHz	22	_	dB
SL	slope cable equivalent	f = 40 to 750 MHz	0	1.5	dB
FL	flatness of frequency response	f = 40 to 750 MHz	_	± 0.5	dB
S ₁₁	input return losses	f = 40 to 80 MHz;	20	_	dB
		f = 80 to 160 MHz;	18.5	-	dB
		f = 160 to 320 MHz	17	-	dB
		f = 320 to 640 MHz;	15.5	-	dB
		f = 640 to 750 MHz	14	_	dB
S ₂₂	output return losses	f = 40 to 80 MHz;	20	_	dB
22		f = 80 to 160 MHz;	18.5	-	dB
		f = 160 to 320 MHz	17	-	dB
		f = 320 to 640 MHz;	15.5	-	dB
		f = 640 to 750 MHz	14	-	dB
СТВ	composite triple beat	110 chs flat; V _o = 44 dBmV; measured at 745.25 MHz	-	-51	dB
X _{mod}	cross modulation	110 chs flat; V _o = 44 dBmV; measured at 55.25 MHz	-	-55	dB
CSO	composite second order distortion	110 chs flat; V _o = 44 dBmV; measured at 746.5 MHz		-53	dB
d ₂	second order distortion	note 1	-	-63	dB
V _o	output voltage	d _{im} = -60 dB note 2	59	-	dBmV
F	noise figure	f = 750 MHz	-	8	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	-	235	mA

Notes

1. $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 691.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 746.5$ MHz

2. $f_p = 740.25$ MHz; $V_p = V_o$; $f_q = 747.25$ MHz; $V_q = V_o$ -6 dB; $f_r = 749.25$ MHz; $V_r = V_o$ -6 dB; measured at $f_p + f_q - f_r = 738.25$ MHz.

BGY885A

FEATURES

- · Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- · Rugged construction
- Gold metallization ensures excellent reliability.

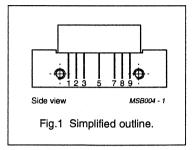
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 40 to 860 MHz at a voltage supply of +24 V (DC).

PINNING - SOT115C

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz;	18	19	dB
		f = 860 MHz	18.5	-	dB
I _{tot}	total current consumption	DC value; V _B = +24 V	-	235	mA

LIMITING VALUES

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	_	60	dBmV
T _{stg}	storage temperature range	-40	+100	°C
T _{mb}	mounting base operating temperature range	-20	+100	°C

DEVICE DATA

Hybrid ICs for wideband amplifiers

HYBRID INTEGRATED CIRCUIT VHF/UHF WIDE-BAND AMPLIFIER

One-stage wide-band amplifier in hybrid integrated circuit technique on a thin-film substrate, intended for aerial amplifiers in car radios, caravans or RATV and MATV applications.

QUICK REFERENCE DATA

D.C. supply voltage	V _B	=	12	V ± 10%
Frequency range	f		40 to 860	MHz
Source and load (characteristic) impedance	$R_s = R_{\ell} = Z_0$	=	75	Ω
Transducer gain	$G_{tr} = s_f ^2$	typ.	12	dB
Flatness of frequency response	$\pm \Delta s_f ^2$	typ.	1	dB
Output voltage at –60 dB intermodulation distortion (DIN 45004, 3-tone)		typ.	99	dΒμV
Noise figure	Vo(rms)	typ.	5.5	•
Operating ambient temperature	T _{amb}		-20 to + 70	

ENCAPSULATION 5-pin, in-line, resin-coated body, see MECHANICAL DATA (Fig. 2)

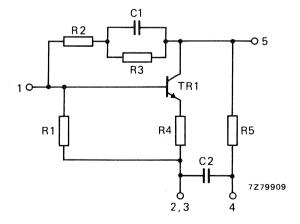


Fig. 1 Circuit diagram.

RATINGS

10.1111.00				
Limiting values in accordance with the Absolute Maxin	num System (IEC 134)		
Operating ambient temperature	T_{amb}	-20	-20 to +70	
Storage temperature	T_{stg}	40 to	-40 to +125	
D.C. supply voltage	V_B	max.	15	V
Peak incident powers on pins 1 and 5	P11M,P15M	max.	100	mW
CHARACTERISTICS				
Measuring conditions				
Ambient temperature	T _{amb}	=	25	οС
D.C. supply voltage	V _B	=	12	٧
Source impedance and load impedance	R _{s,} Rℓ	=	75	Ω
Characteristic impedance of h.f. connections	Z _o	==	75	Ω
Frequency range	f	= 40	to 860	MHz
Performance				
Supply current	1 _B	typ.	11,5	mΑ
Transducer gain	$G_{tr} = s_f ^2$	typ.	12	dB
Flatness of frequency response	$\pm \Delta s_f ^2$	typ.	1	dB
Individual maximum v.s.w.r.				
input	VSWR(i)	typ.	2,0	
output	VSWR _(o)	typ.	1,4	*
Back attenuation				
f = 100 MHz	$ s_r ^2$	typ.		dB
f = 860 MHz	$ s_r ^2$	typ.	19	dB
Output voltage				
at -60 dB intermodulation distortion (DIN 45004, par. 6.3: 3-tone)	V _{o(rms)}	typ.	99	dΒμV
(Diri 10001) puri olor o torio)	- 0(11113)			'

s-parameters:
$$s_f = s_{21}$$
 $s_i = s_{11}$ $s_r = s_{12}$ $s_o = s_{22}$

5,5 dB

typ.

Noise figure

^{*} Highest value, for a sample, occuring in the frequency range.

OPERATING CONDITIONS

Ambient temperature range	T_{amb}	-	–20 to + 70 °C
D.C. supply voltage	V_{B}	=	12 V ±10%
Frequency range	f		40 to 860 MHz
Source impedance and load impedance	$R_{s,R_{\ell}}$	=	75 Ω

MECHANICAL DATA

Dimensions in mm

The device is resin coated.

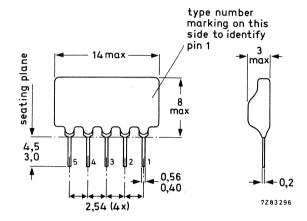


Fig. 2 Encapsulation.

Terminal connections

1	=	input
2,3	=	common
4	=	supply (+)
5	=	output

Soldering recommendations

Hand soldering

Maximum contact time for a soldering-iron temperature of 260 °C up to the seating plane is 5 s.

Dip or wave soldering

260 °C is the maximum permissible temperature of the solder; it must not be in contact with the joint for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds. The device may be mounted against the printed-circuit board, but the temperature of the device must not exceed 125 °C. If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature below the allowable limit.

Mounting recommendations

The module should preferably be mounted on double-sided printed-circuit board, see the example shown below.

Input and output should be connected to 75 Ω tracks.

The connections to the 'common' pins should be as close to the seating plane as possible.

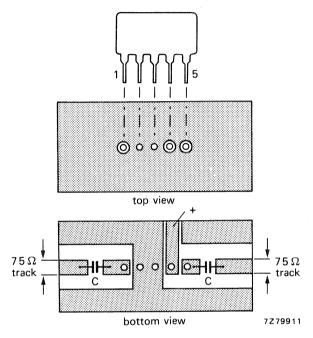


Fig. 3 Printed-circuit board holes and tracks. C > 220 pF ceramic capacitor.

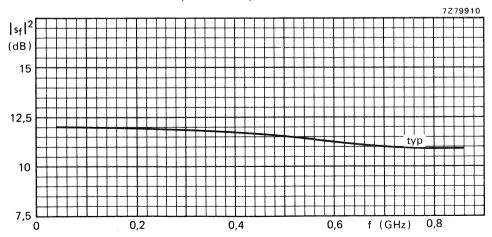


Fig. 4 Transducer gain as a function of frequency; $Z_0 = 75 \Omega$.

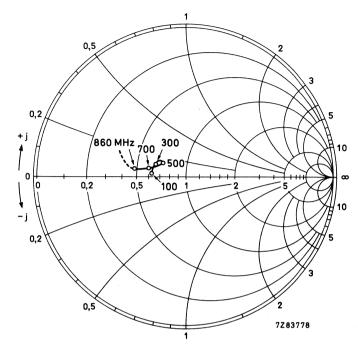


Fig. 5 Input impedance derived from input reflection coefficient s_i , co-ordinates in ohm x 75; typical values.

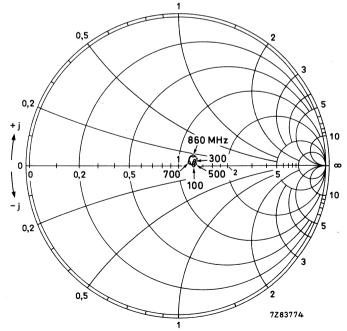


Fig. 6 Output impedance derived from output reflection coefficient s₀, co-ordinates in ohm x 75; typical values.

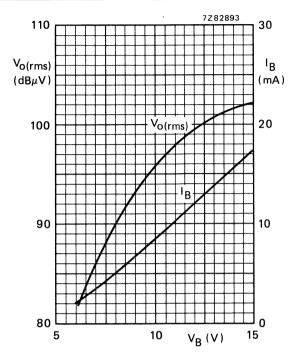


Fig. 7 Output voltage and supply current as a function of the supply voltage; typical values.

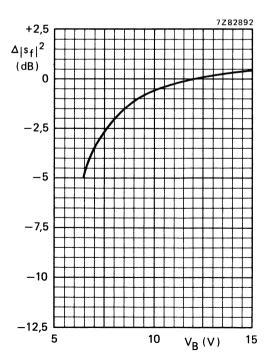


Fig. 8 Variation of transducer gain with supply voltage; reference 0 dB at 12 V; f = 100 to 860 MHz; typical values.

HYBRID INTEGRATED CIRCUIT VHF/UHF WIDE-BAND AMPLIFIER

Two-stage wide-band amplifier in hybrid integrated circuit technique on a thin-film substrate, intended for RATV and MATV applications.

QUICK REFERENCE DATA

D.C. supply voltage	VB	=	12	V ± 10%
Frequency range	f	40 t	o 860	MHz
Source and load (characteristic) impedance	$R_s = R_{\ell} = Z_0$	= ,	75	Ω
Transducer gain	$G_{tr} = s_f ^2$	typ.	18	dB
Flatness of frequency response	$\pm \Delta s_f ^2$	typ.	1	dB
Output voltage at -60 dB intermodulation	, .		100	ID V
distortion (DIN 45004, 3-tone)	$V_{o(rms)}$	typ.	100	dBμV
Noise figure	F	typ.	6	dB
Operating ambient temperature	T _{amb}	-20 to	+ 70	оС

ENCAPSULATION 5-pin, in-line, resin-coated body, see MECHANICAL DATA (Fig. 2)

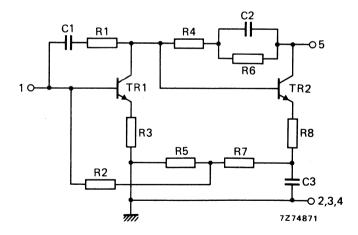


Fig. 1 Circuit diagram.

RATINGS

Limiting values in accordance with the	Absolute Maximum System (IEC 134)
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Limiting values in accordance with the Absolute Maximu	ım System (IEC 134	1)		
Operating ambient temperature	T_{amb}	-20 to	+ 70	oC
Storage temperature	T_{stg}	-40 to	+ 125	oC
D.C. supply voltage	V_{B}	max.	15	V
Peak incident powers on pins 1 and 5	P _{I1M} , P _{I5M}	max.	100	mW
CHARACTERISTICS				
Measuring conditions				
Ambient temperature	T_{amb}	=	25	oC
D.C. supply voltage	V_{B}	=	12	V
Source impedance and load impedance	R_s , R_ℓ	=	75	Ω
Characteristic impedance of h.f. connections	Z_0	=	75	Ω
Frequency range	f	= 40 to	860	MHz
Performance				
Supply current	I _B	typ.	18	mΑ
Transducer gain	$G_{tr} = s_f ^2$	typ.	18	dB
Flatness of frequency response	$\pm \Delta \mid$ Sf \mid 2	typ.	1	dB
Individual maximum v.s.w.r.				
input	V/CM/D	+	1,5	*
·	VSWR _(i)	typ.		
output	VSWR _(o)	typ.	1,9	
output Back attenuation	VSWR _(o)	typ.	1,9	*
output	VSWR $_{(0)}^{(0)}$		1,9 29	*
output Back attenuation f = 100 MHz f = 860 MHz Output voltage at -60 dB intermodulation distortion	VSWR ₍₀₎ s _r ² s _r ²	typ. typ. typ.	1,9 29 25	* dB dB
output Back attenuation f = 100 MHz f = 860 MHz Output voltage	VSWR $_{(0)}^{(0)}$	typ.	1,9 29 25 100	* dB

s-parameters:
$$s_f = s_{21}$$
 $s_i = s_{11}$ $s_r = s_{12}$ $s_o = s_{22}$

^{*} Highest value, for a sample, occuring in the frequency range.

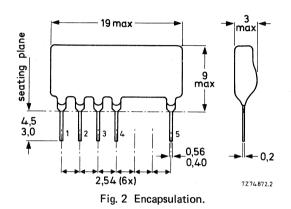
Dimensions in mm

OPERATING CONDITIONS

Ambient temperature range	T_{amb}	-20 to + 70 °C
D.C. supply voltage	V_{B}	= 12 V ± 10%
Frequency range	f	40 to 860 MHz
Source impedance and load impedance	R_s , R_ℓ	= 75 Ω

MECHANICAL DATA

The device is resin coated.



Terminal connections

1 = input 2,3,4 = common 5 = output/supply(+)

Soldering recommendations

Hand soldering

Maximum contact time for a soldering-iron temperature of 260 °C up to the seating plane is 5 s.

Dip or wave soldering

260 °C is the maximum permissible temperature of the solder; it must not be in contact with the joint for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds. The device may be mounted against the printed-circuit board, but the temperature of the device must not exceed 125 °C. If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature below the allowable limit.

Mounting recommendations

The module should preferably be mounted on double-sided printed-circuit board, see the example shown below.

Input and output should be connected to 75 Ω tracks.

The connections to the 'common' pins should be as close to the seating plane as possible.

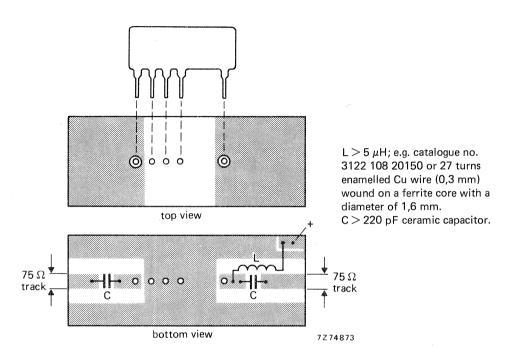


Fig. 3 Printed-circuit board holes and tracks.

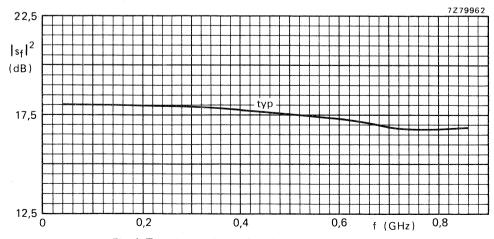


Fig. 4 Transducer gain as a function of frequency; $Z_0 = 75 \Omega$.

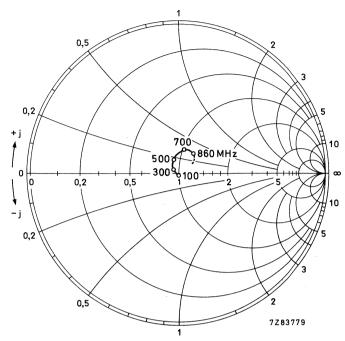


Fig. 5 Input impedance derived from input reflection coefficient s_i , co-ordinates in ohm x 75; typical values.

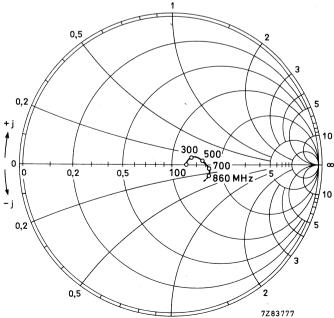


Fig. 6 Output impedance derived from output reflection coefficient s₀, co-ordinates in ohm x 75; typical values.

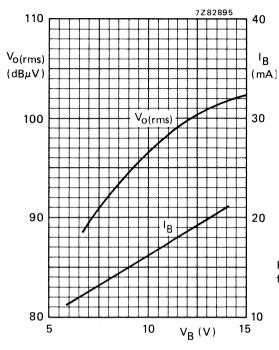


Fig. 7 Output voltage and supply current as a function of the supply voltage; typical values.

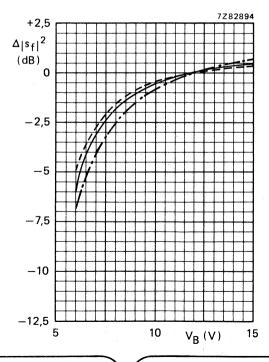


Fig. 8 Variation of transducer gain with supply voltage; reference 0 dB at 12 V:

---- f = 500 MHz;

---- f = 100 MHz;

----- f = 860 MHz;

typical values.

HYBRID INTEGRATED CIRCUIT VHF/UHF WIDE-BAND AMPLIFIER

Three-stage wide-band amplifier in hybrid integrated circuit technique on a thin-film substrate, intended for use in mast-head booster-amplifiers, as preamplifier in MATV systems, and as general-purpose amplifier for v.h.f. and u.h.f. applications.

QUICK REFERENCE DATA

	_	1.2		
Frequency range	f	40 t	o 860	V: ⊢z
Source and load (characteristic) impedance	$R_s = R_{\ell} = Z_0$	= *	75	Ω
Transducer gain	$G_{tr} = s_f ^2$	typ.	23	ďВ
Flatness of frequency response	$\pm \Delta s_{f} ^2$	typ.	1.0	dB
Output voltage at -60 dB intermodulation			105	in
distortion (DIN 45004, 3-tone)	$V_{o(rms)}$	>	105	$dB\muV$
Noise figure	F	typ.	7	dB
D.C. supply voltage	V_{B}	=	12	V ± 10%
Operating ambient temperature	T _{amb}	-20 t	o +70	oC

ENCAPSULATION 8-pin, in-line, resin-coated body, see MECHANICAL DATA (Fig. 2)

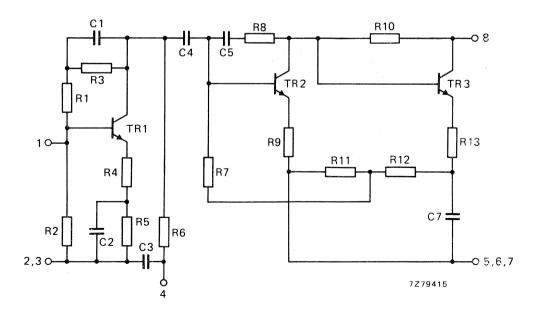


Fig. 1 Circuit diagram.

RATINGS

Limiting values in accorda	nce with the Absol	ute Maximum S	System (IEC 134)			
Operating ambient temper	rature		T _{amb}	-20	to +70	оС
Storage temperature			T_{stg}	-40 to	+125	оС
D.C. supply voltage			V_{B}	max.	15	V
Peak incident powers on p	oins 1 and 7		P _{I1M} , P _{I7M}	max.	100	mW
CHARACTERISTICS						
Measuring conditions						
Ambient temperature			T_{amb}	=	25	oC
D.C. supply voltage			VB	=	12	V
Source impedance and loa	ad impedance		R _s , Rℓ	=	75	Ω
Characteristic impedance	of h.f. connections		z_{o}	=	75	Ω
Frequency range			f	= 40	to 860	MHz
Performance						
Supply current			I _B	typ.	56	mΑ
Transducer gain			$G_{tr} = s_f ^2$	typ. 2 1	23 1 to 25	dB dB
Flatness of frequency resp	oonse		$\pm \Delta s_{f} ^2$	typ.	1.0	dB
Individual maximum v.s.w	ı.r.					
input			VSWR(i)	typ.	1,3 1,5	
output			VSWR _(o)	typ.	1,5	
Back attenuation f = 100 MHz			$ s_r ^2$	typ.	42	dB
f = 860 MHz			s _r ²	typ.	33	dB
Output voltage						
at -60 dB intermodula			V _{o(rms)}	>		dBμV dBμV
(DIN 45004, par. 6.3: 3	3-tone)		F	typ.		dBμν dB
Noise figure			Γ	typ.	,	uь
	s-parameters:	s _f = s ₂₁	s; = s ₁₁			
		Sr = \$12	s ₀ = s ₂₂			

s-parameters:	$s_f = s_{21}$	$s_i = s_{11}$
	$s_r = s_{12}$	$s_0 = s_{22}$

^{*} Highest value, for a sample, occurring in the frequency range.

Dimensions in mm

OPERATING CONDITIONS

Ambient temperature range	T _{amb}	-20 to +	70	oC
D.C. supply voltage	V_{B}	=	12	V ± 10%
Frequency range	f	40 to 8	60	MHz
Source impedance and load impedance	R_s , R_ℓ	=	75	Ω

MECHANICAL DATA

a daviag is regin agested

The device is resin coated.

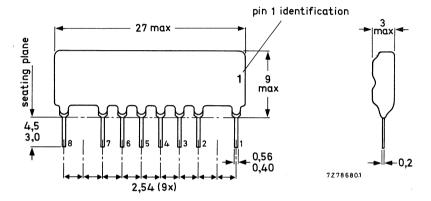


Fig. 2 Encapsulation.

Terminal connections

```
1 = input
2, 3, 5, 6, 7 = common
4 = supply (+)
8 = output/supply (+)
```

Soldering recommendations

Hand soldering

Maximum contact time for a soldering-iron temperature of 260 °C up to the seating plane is 5 s.

Dip or wave soldering

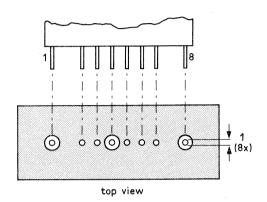
260 °C is the maximum permissible temperature of the solder; it must not be in contact with the joint for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds. The device may be mounted against the printed-circuit board, but the temperature of the device must not exceed 125 °C. If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature below the allowable limit.

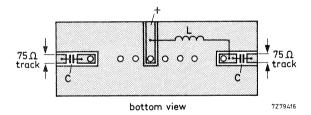
Mounting recommendations

The module should preferably be mounted on double-sided printed-circuit board, see the example shown below.

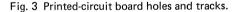
Input and output should be connected to 75 Ω tracks.

The connections to the 'common' pins should be as close to the seating plane as possible.





 $L > 5 \mu H$; e.g. catalogue no. 3122 108 20150 or 27 turns enamelled Cu wire (0,3 mm) wound on a ferrite core with a diameter of 1,6 mm. C > 220 pF ceramic capacitor.



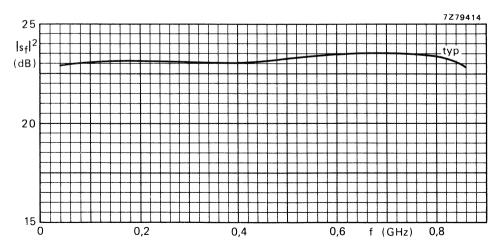


Fig. 4 Transducer gain as a function of frequency; $Z_0 = 75 \Omega$.

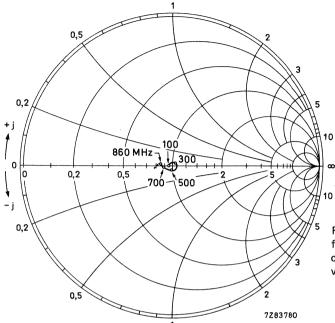


Fig. 5 Input impedance derived from input reflection coefficient s_i, co-ordinates in ohm x 75; typical values.

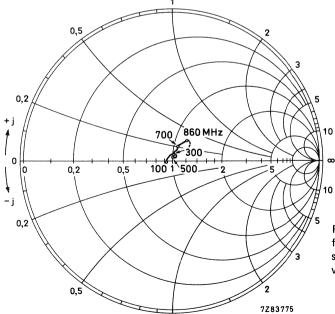


Fig. 6 Output impedance derived from output reflection coefficient s₀, co-ordinates in ohm x 75; typical values.

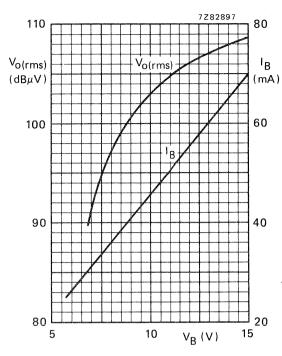
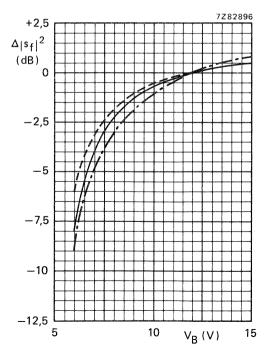


Fig. 7 Output voltage and supply current as a function of the supply voltage; typical values.



HYBRID INTEGRATED CIRCUIT VHF/UHF WIDE-BAND AMPLIFIER

Three-stage wide-band amplifier in hybrid integrated circuit technique on a thin-film substrate, intended for use in mast-head booster-amplifiers, as an amplifier in MATV systems, and as general-purpose amplifier for v.h.f. and u.h.f. applications.

QUICK REFERENCE DATA

Frequency range	f		40 to 860	MHz
Source and load (characteristic) impedance	$R_s = R_{\ell} = Z_0$	=	75	Ω
Transducer gain	$G_{tr} = s_f ^2$	typ.	28	dB
Flatness of frequency response	$\pm \Delta s_f ^2$	typ.	1	dB
Output voltage at -60 dB intermodulation distortion (DIN 45004, 3-tone)	V _{O(rms)}	>	105	dΒμV
Noise figure	F	typ.	6	dB
D.C. supply voltage	V_{B}	==	12	V ± 10%
Operating ambient temperature	T _{amb}		-20 to +70	oC

ENCAPSULATION 8-pin, in-line, resin-coated body, see MECHANICAL DATA (Fig. 2)

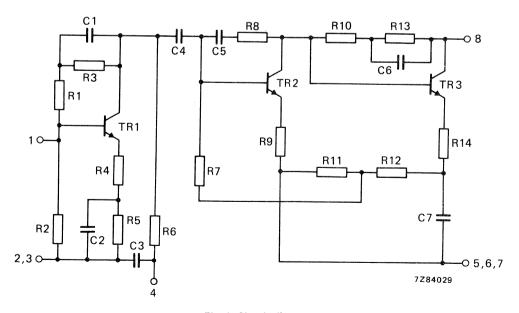


Fig. 1 Circuit diagram.

RATINGS

Limiting values in accor	dance with the Abso	ute Maximum	System (IEC 13	4)	•	
Operating ambient tem	perature		T_{amb}	-20 to +70		оС
Storage temperature			T_{stg}	-	40 to +125	оС
D.C. supply voltage			V_{B}	max.	, 15	V
Peak incident powers o	n pins 1 and 8		P _{I1M} , P _{I8M}	max.	100	mW
CHARACTERISTICS						
Measuring conditions						
Ambient temperature			T _{amb}	=		оС
D.C. supply voltage			V_{B}	=	12	
Source impedance and	load impedance		R_s , R_ℓ	=	75	Ω
Characteristic impedan	ce of h.f. connections		Z _o	=	75	Ω
Frequency range			f	=	40 to 860	MHz
Performance						
Supply current			1 _B	typ.		mΑ
Transducer gain			$G_{tr} = s_{f} ^2$	typ.	28 26 to 31	dB dB
Flatness of frequency r	esponse		$\pm \Delta \mathbf{s_f} ^2$	typ.	1	dB
Individual maximum v.	s.w.r.		VSWR(i)	typ.	1,5	*
input			VSWR _(o)	typ.	1,7	
output Back attenuation			V 3 ((()	., .	-7-	
f = 100 MHz			s _r ²	typ.	45	dB
f = 860 MHz			$ \mathbf{s_r} ^2$	typ.	35	dB
Output voltage at -60 dB intermod (DIN 45004, par. 6,3			V _{o(rms)}	> typ.		dBμV dBμV
Noise figure	2, 2 23		F	typ.	6	dB
<u> </u>						
	s-parameters:	sf = s21	$s_i = s_{11}$			
		s _r = s ₁₂	s _o = s ₂₂			

^{*} Highest value, for a sample, occurring in the frequency range.

Dimensions in mm

OPERATING CONDITIONS

Ambient temperature range	T_{amb}	٠.	−20 to +70 °C
D.C. supply voltage	V_{B}	=	12 V ± 10%
Frequency range	f		40 to 860 MHz
Source impedance and load impedance	R _s , R _ℓ	=	75 Ω

MECHANICAL DATA

The device is resin coated.

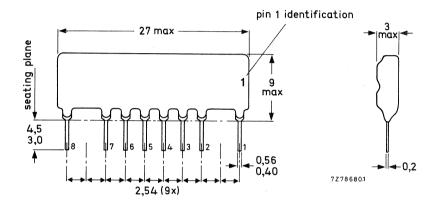


Fig. 2 Encapsulation.

Terminal connections

```
1 = input
2, 3, 5, 6, 7 = common
4 = supply (+)
8 = output/supply (+)
```

Soldering recommendations

Hand soldering

Maximum contact time for a soldering-iron temperature of 260 °C up to the seating plane is 5 s.

Dip or wave soldering

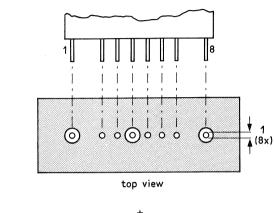
260 °C is the maximum permissible temperature of the solder; it must not be in contact with the joint for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds. The device may be mounted against the printed-circuit board, but the temperature of the device must not exceed 125 °C. If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature below the allowable limit.

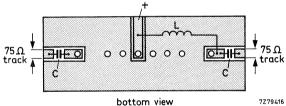
Mounting recommendations

The module should preferably be mounted on double-sided printed-circuit board, see the example shown below.

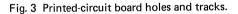
Input and output should be connected to 75 Ω tracks.

The connections to the 'common' pins should be as close to the seating plane as possible.





 $L > 5 \mu H$; e.g. catalogue no. 3122 108 20150 or 27 turns enamelled Cu wire (0,3 mm) wound on a ferrite core (material 4B1; catalogue number 3122 104 91110) with a diameter of 1,6 mm. $C > 220 \ pF$ ceramic capacitor.



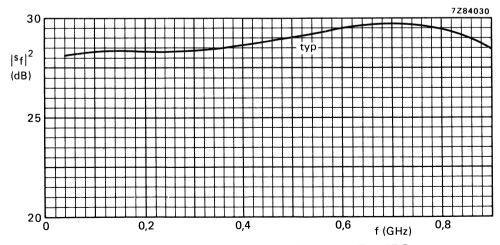


Fig. 4 Transducer gain as a function of frequency; $Z_0 = 75 \Omega$.

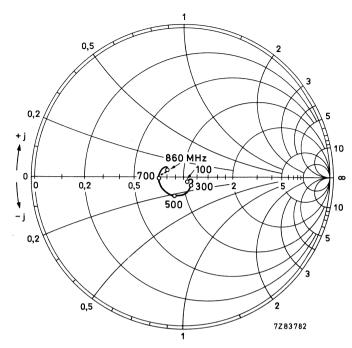


Fig. 5 Input impedance derived from input reflection coefficient s_i , co-ordinates in ohm x 75; typical values.

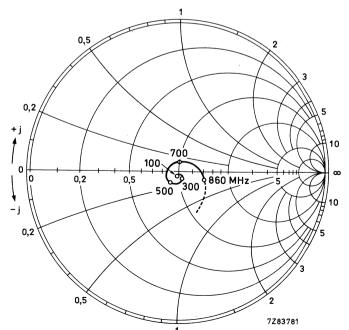


Fig. 6 Output impedance derived from output reflection coefficient s_o, co-ordinates in ohm x 75; typical values.

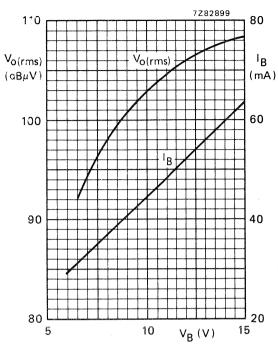


Fig. 7 Output voltage and supply current as a function of the supply voltage; typical values.

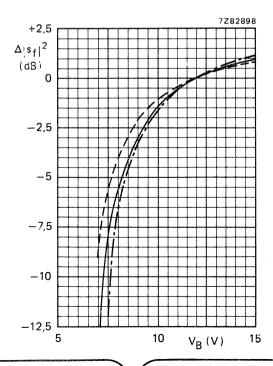


Fig. 8 Variation of transducer gain with supply voltage; reference 0 dB at 12 V;

---- f = 500 MHz;

---- f = 100 MHz;

----- f = 860 MHz;

typical values.

HYBRID INTEGRATED CIRCUIT VHF/UHF WIDE-BAND AMPLIFIER

Three-stage wide-band amplifier in hybrid integrated circuit technique on a thin-film substrate, intended for use in mast-head booster-amplifiers, as an amplifier in MATV and CATV systems, and as general-purpose amplifier for v.h.f. and u.h.f. applications.

QUICK REFERENCE DATA

Frequency range		f	40 to 860	MHz
Source and load (characteristic) impedance		$R_s = R_{\ell} = Z_0$	= 75	Ω
Transducer gain		$G_{tr} = s_f ^2$	typ. 28	dB
Flatness of frequency response		$\pm \Delta \mathbf{s}_{\mathbf{f}} ^2$	typ. 1	dB
Output voltage at -60 dB intermodulation distortion (DIN 45004, 3-tone) VHF UHF		V _O (rms) V _O (rms)	• • •	dΒμV dΒμV
Noise figure		F S(IIIIs)	typ. 7	
D.C. supply voltage		$V_{\mathbf{B}}$	= 12	V ± 10%
Operating ambient temperature	*	T _{amb}	-20 to +70	оС

ENCAPSULATION 9-pin, in-line, resin-coated body, see MECHANICAL DATA (Fig.2)

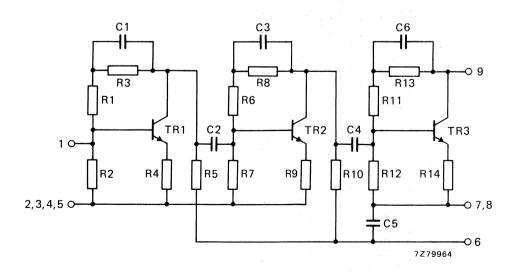


Fig. 1 Circuit diagram.

RATINGS

-20 to +70 °C T_{amb} Operating ambient temperature T_{stg} -40 to +125 °C Storage temperature 15 V V_{B} D.C. supply voltage max. P_{11M}, P_{18M} 100 mW Peak incident powers on pins 1 and 8 max. **CHARACTERISTICS** Measuring conditions 25 °C Ambient temperature Tamb 12 V D.C. supply voltage V_{R} Rs, Ro 75 Ω Source impedance and load impedance

 Z_{o}

1_

Vo(rms)

Vo(rms)

F

75 Ω

100 mA

111 $dB\mu V$

113 dBμV 110 dB_µV

112 dBμV

7 dB

40 to 860 MHz

tvn

typ.

typ.

typ.

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Performance Supply current

VHF

UHF

Noise figure

Frequency range

Characteristic impedance of h.f. connections

(DIN 45004, par. 6,3; 3-tone)

Supply current	'B	typ.	100 1117
Transducer gain	$G_{tr} = s_f ^2$	typ.	28 dB 26 to 31 dB
Flatness of frequency response	$\pm \Delta \mathbf{s_f} ^2$	typ.	1 dB
Individual maximum v.s.w.r. input	vswr _(i)	typ.	2,3 *
output	VSWR _(o)	typ.	1,9 *
Back attenuation f = 100 MHz f = 860 MHz	s _r ² s _r ²	typ.	45 dB 35 dB
Output voltage at -60 dB intermodulation distortion			

s-parameters:	s _f = s ₂₁	$s_i = s_{11}$
	$s_r = s_{12}$	$s_0 = s_{22}$

^{*} Highest value, for a sample, occurring in the frequency range.

Dimensions in mm

OPERATING CONDITIONS

Ambient temperature range	T _{amb}		–20 to +70 °C
D.C. supply voltage	v_B	=	12 V ± 10%
Frequency range	f		40 to 860 MHz
Source impedance and load impedance	R_{c} , R_{o}	=	75 Ω

MECHANICAL DATA

The device is resin coated.

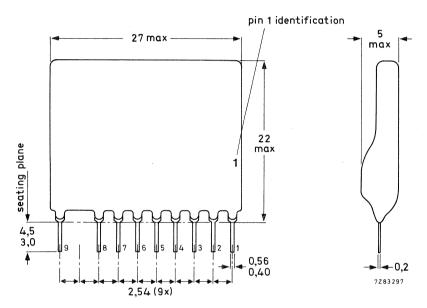


Fig. 2 Encapsulation.

Terminal connections

```
1 = input
2,3,4,5 and 7,8 = common
6 = supply (+)
9 = output/supply (+)
```

Soldering recommendations

Hand soldering

Maximum contact time for a soldering-iron temperature of 260 °C up to the seating plane is 5 s.

Dip or wave soldering

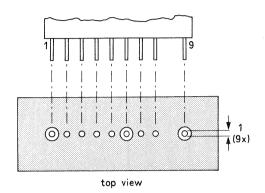
260 °C is the maximum permissible temperature of the solder; it must not be in contact with the joint for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds. The device may be mounted against the printed-circuit board, but the temperature of the device must not exceed 125 °C. If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature below the allowable limit.

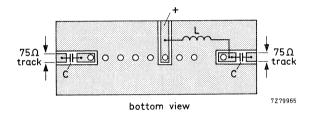
Mounting recommendations

The module should preferably be mounted on double-sided printed-circuit board, see the example shown below.

Input and output should be connected to 75 Ω tracks.

The connections to the 'common' pins should be as close to the seating plane as possible.





L > 5 μ H; e.g. catalogue no. 3122 108 20150 or 27 turns enamelled Cu wire (0,3 mm) wound on a ferrite core (material 4B1; catalogue no. 3122 104 91110) with a diameter of 1,6 mm. C > 220 pF ceramic capacitor.

Fig. 3 Printed-circuit board holes and tracks,

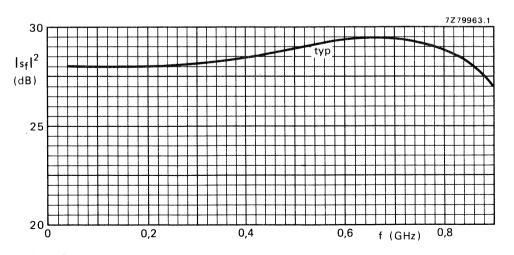


Fig. 4 Transducer gain as a function of frequency; $Z_0 = 75 \Omega$.

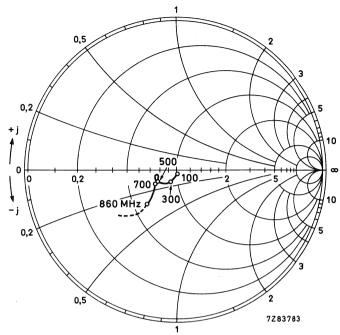


Fig. 5 Input impedance derived from input reflection coefficient s_i , co-ordinates in ohm x 75; typical values.

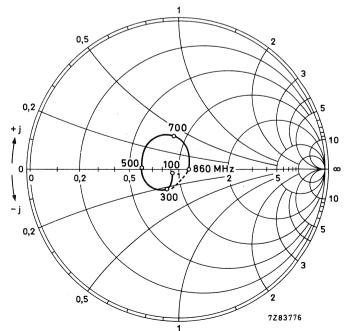


Fig. 6 Output impedance derived from output reflection coefficient s_0 , co-ordinates in ohm x 75; typical values.

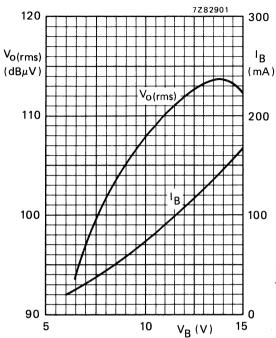


Fig. 7 Output voltage and supply current as a function of the supply voltage; typical values.

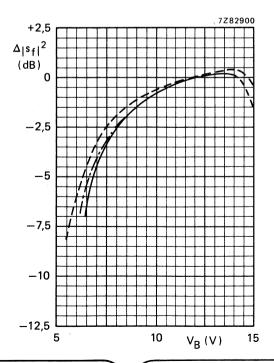


Fig. 8 Variation of transducer gain with supply voltage; reference 0 dB at 12 V;

----- f = 500 MHz;

---- f = 100 MHz;

----- f = 860 MHz;

typical values.

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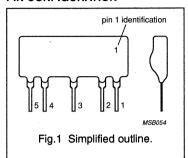
DESCRIPTION

A two-stage wideband amplifier in hybrid integrated circuit form on a thin-film substrate. The device is intended for use as an IF amplifier for satellite television and as a general purpose amplifier in the range 10 to 2000 MHz.

PINNING

PIN	DESCRIPTION
1	input
2	common
3	common
4	common
5	output/supply (+)

PIN CONFIGURATION



QUICK REFERENCE DATA

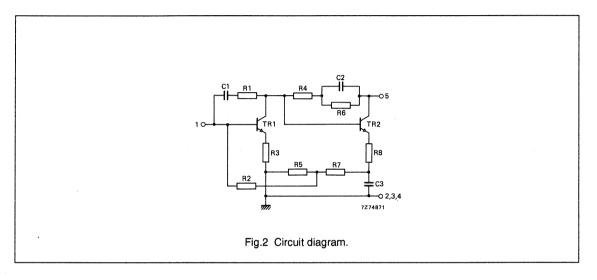
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
f	frequency range		10	_	2000	MHz
G _{tr}	transducer gain	$f = 1750 \text{ MHz};$ $G_{tr} = s_t ^2$	-	18	-	dB
V _{o(RMS)}	output voltage	d _{im} = -60 dB (DIN 45004, paragraph 6.3: 3-tone)	101	_	-	dΒμV
F	noise figure		T-	6.5	-	dB
V_B	supply voltage	DC value	I -	12	-	٧
T _{amb}	ambient operating temperature range		-20	_	70	°C

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MECHANICAL DATA

Encapsulation

The encapsulation comprises a 5-pin, in-line, resin-coated body, see Fig.8.



Soldering recommendations

HAND SOLDERING

The maximum contact time for a soldering iron temperature of 260 °C up to the seating plane is 5 s.

DIP OR WAVE SOLDERING

The maximum permissible temperature for the solder is 250 °C. It must not be in contact with the joint for more than 5 s.

The total contact time of successive solder waves must not exceed 5 s.

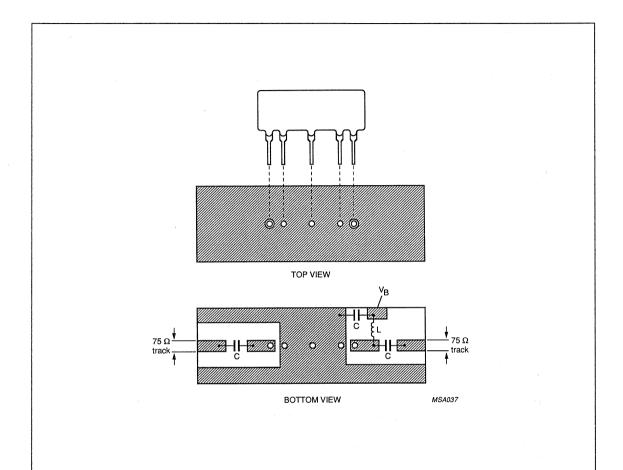
The device may be mounted against the printed-circuit board, but the temperature of the device must not exceed 125 °C.

If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature below the allowable limit.

Mounting recommendations

The module should preferably be mounted on a double-sided printed-circuit board, see Fig.3. Input and output should be connected to 75 Ω tracks. The connection to the common pins should be as close to the seating plane as possible.

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 $L > 5 \mu H$; e.g. catalogue No. 3122 108 20150, or 27 turns enamelled 0.3 mm copper wire wound on a ferrite core with a diameter of 1.6 mm.

C > 1000 pF ceramic capacitor.

Fig.3 Printed-circuit board holes and tracks.

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

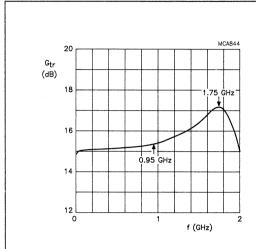
SYMBOL	PARAMETER	MIN.	MAX.	UNIT
T _{amb}	ambient operating temperature range	-20	70	°C
T _{stg}	storage temperature range	-40	125	ç
V _B	DC supply voltage	_	15	٧
P _{11M} , P _{15M}	peak incident powers on pins 1 and 5	_	100	mW

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CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Measuring	conditions					
T _{amb}	ambient operating temperature		T-	25	-	°C
V _B	supply voltage	DC value	1-	12	-	V
Z _s	source impedance		1-	75	_	Ω
Z _L	load impedance		_	75	-	Ω
Performan	ce					
I _B	supply current		-	28	_	mA
G _{tr}	transducer gain	$G_{tr} = s_t ^2$;				
		f = 10 to 1000 MHz	-	15	-	dB
		f = 1750 MHz	_	18	-	dB
		f = 2000 MHz	-	16	_	dB
S ₁₁	input return loss					
		f = 10 to 1000 MHz	-	14	_	dB
		f = 1000 to 1750 MHz	-	12		dB
S ₂₂	output return loss					
		f = 10 to 1000 MHz	_	14	-	dB
		f = 1000 to 1750 MHz	-	12	-	dB
IS _r I ²	feedback attenuation		_	25	_	dB
V _{o(RMS)}	output voltage	$d_{im} = -60 \text{ dB}$ (DIN 45004, paragraph 6.3, 3-tone)	101	103	_	dΒμV
F	noise figure		-	6.5	-	dB
Operating	conditions					
T _{amb}	ambient operating temperature range		-20	 -	70	°C
V _B	supply voltage	DC value	10.8	-	13.2	٧
f	frequency range		10	 -	2000	MHz
Z _s	source impedance		-	75	_	Ω
Z _L	load impedance		-	75	1-	Ω

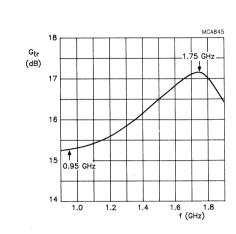
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Gain over the entire frequency range.

 $Z_o = 75 \Omega$.

Fig.4 Transducer gain as a function of frequency.



Expanded view of the satellite first IF frequency range.

 $Z_o = 75 \Omega$.

Fig.5 Transducer gain as a function of frequency.

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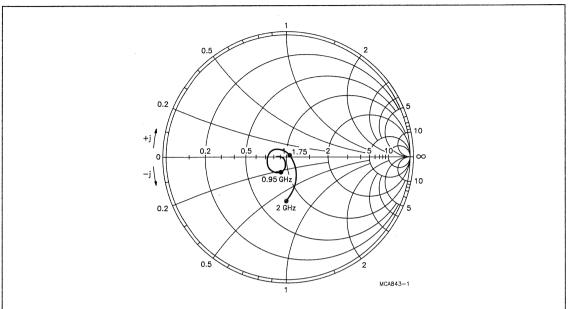
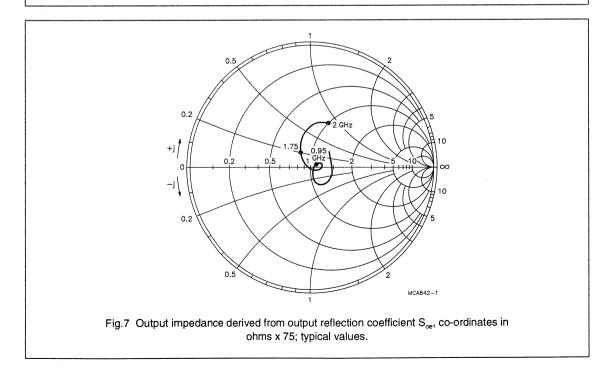
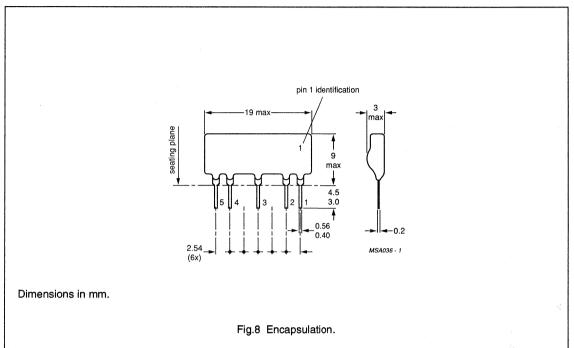


Fig.6 Input impedance derived from input reflection coefficient Sie, co-ordinates in ohms x 75; typical values.



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PACKAGE OUTLINE



HYBRID INTEGRATED CIRCUIT VHF/UHF WIDE-BAND AMPLIFIER

One-stage wide-band amplifier in hybrid integrated circuit technique on a thin-film substrate, intended for aerial amplifiers in car radios, caravans or RATV and MATV applications.

QUICK REFERENCE DATA

D.C. supply voltage	V _B	=	12 V ± 10%
Frequency range	f	4	0 to 860 MHz
Source and load (characteristic) impedance	$R_s = R_{\ell} = Z_o$	=	75 Ω
Transducer gain	$G_{tr} = s_f ^2$	typ.	12 dB
Flatness of frequency response	$\pm \Delta s_f ^2$	typ.	1 dB
Output voltage at -60 dB intermodulation distortion (DIN 45004, 3-tone)	Vo(rms)	typ.	99 dBμV
Noise figure	F	typ.	3,6 dB
Operating ambient temperature T _{amb} -20 to +) to + 70 °C	

ENCAPSULATION 5-pin, in-line, resin-coated body, see MECHANICAL DATA (Fig. 2)

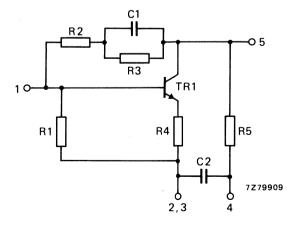


Fig. 1 Circuit diagram.

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RATINGS

NATINGS			
Limiting values in accordance with the Absolute Ma	ximum System (IEC 13	34)	
Operating ambient temperature	T _{amb}	-20	to +70 °C
Storage temperature	T _{stg}	-40 to	o +125 °C
D.C. supply voltage	VB	max.	15 V
Peak incident powers on pins 1 and 5	PI1M,PI5M	max.	100 mW
CHARACTERISTICS			
Measuring conditions			
Ambient temperature	T _{amb}	=	25 °C
D.C. supply voltage	v_B	=	12 V
Source impedance and load impedance	R _{s,} Rℓ	=	75 Ω
Characteristic impedance of h.f. connections	Z _o	=	75 Ω
Frequency range	f	= 40	to 860 MHz
Performance			
Supply current	1 _B	typ.	11,5 mA
Transducer gain	$G_{tr} = s_f ^2$	typ.	12 dB
Flatness of frequency response	$\pm \Delta s_f ^2$	typ.	1 dB
Individual maximum v.s.w.r.			
input	VSWR _(i)	typ.	2,0 *
output	VSWR(o)	typ.	1,4 *
Back attenuation			
f = 100 MHz	$ s_r ^2$	typ.	22 dB
f = 860 MHz	$ s_r ^2$	typ.	19 dB
Output voltage at -60 dB intermodulation distortion	V	turo.	99 dBμV
(DIN 45004, par. 6.3: 3-tone)	V _{o(rms)} F	typ.	3,6 dB
Noise figure	г	typ.	3,0 UD

s-parameters:
$$s_f = s_{21}$$
 $s_i = s_{11}$ $s_r = s_{12}$ $s_o = s_{22}$

^{*} Highest value, for a sample, occuring in the frequency range.

OPERATING CONDITIONS

Ambient temperature range	T _{amb}	-	-20 to + 70 °C
D.C. supply voltage	V_{B}	=	12 V ±10%
Frequency range	f		40 to 860 MHz
Source impedance and load impedance	$R_{s,R_{\ell}}$	=	75 Ω

MECHANICAL DATA

Dimensions in mm

The device is resin coated.

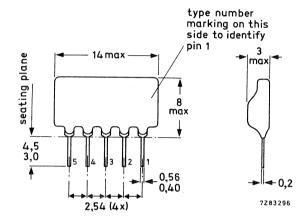


Fig. 2 Encapsulation.

Terminal connections

1 = input 2,3 = common 4 = supply (+) 5 = output

Soldering recommendations

Hand soldering

Maximum contact time for a soldering-iron temperature of 260 °C up to the seating plane is 5 s.

Dip or wave soldering

260 °C is the maximum permissible temperature of the solder; it must not be in contact with the joint for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds. The device may be mounted against the printed-circuit board, but the temperature of the device must not exceed 125 °C. If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature below the allowable limit.

Mounting recommendations

The module should preferably be mounted on double-sided printed-circuit board, see the example shown below.

Input and output should be connected to 75 Ω tracks.

The connections to the 'common' pins should be as close to the seating plane as possible.

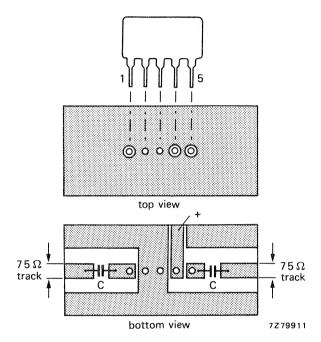


Fig. 3 Printed-circuit board holes and tracks. C > 220 pF ceramic capacitor.

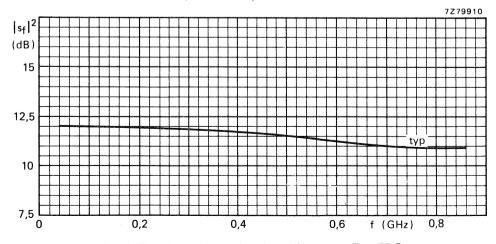


Fig. 4 Transducer gain as a function of frequency; $Z_0 = 75 \Omega$.

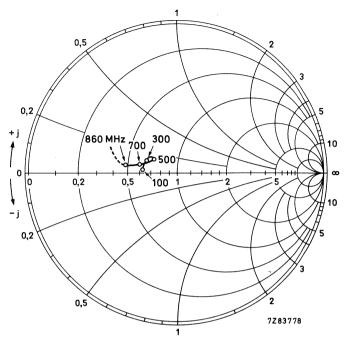


Fig. 5 Input impedance derived from input reflection coefficient s_i , co-ordinates in ohm x 75; typical values.

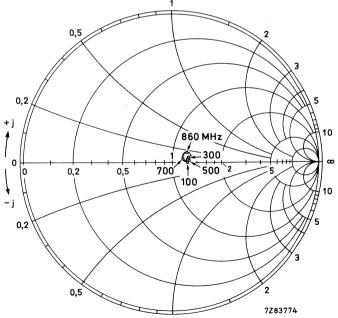


Fig. 6 Output impedance derived from output reflection coefficient s₀, co-ordinates in ohm x 75; typical values.

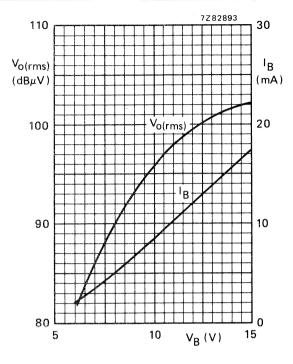


Fig. 7 Output voltage and supply current as a function of the supply voltage; typical values.

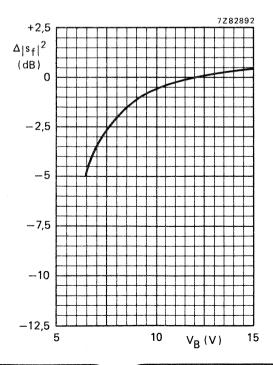


Fig. 8 Variation of transducer gain with supply voltage; reference 0 dB at 12 V; f = 100 to 860 MHz; typical values.

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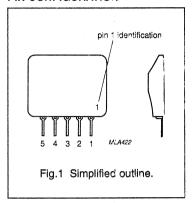
DESCRIPTION

A one-stage wideband amplifier in hybrid integrated circuit technology on a thin-film substrate, intended for use in mast-head booster-amplifiers, as an amplifier in MATV and CATV systems, and as a general purpose amplifier for VHF and UHF applications.

PINNING

PIN	DESCRIPTION
1	input
2	common (-)
3	common (-)
4	common (–)
5	output/supply (+)

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
f	frequency range		40	-	860	MHz.
R _s , R _L	source and load resistance		_	75]-	Ω
Zo	characteristic impedance of HF connections		-	75	-	Ω
$G_{tr} = s_f ^2$	transducer gain		-	10	-	dB
±Δls _f l ²	flatness of frequency response		_	1]-	dB
V _{o(RMS)}	output voltage	at -60 dB intermodulation distortion (DIN 45004, 3-tone)				
	VHF		-	116	-	dΒμV
	UHF		-	114	-	dΒμV
F	noise figure		_	10	T-	dB
V _B	DC supply voltage		10.8	12	13.2	V
T _{amb}	ambient operating temperature range		-20	_	70	°C

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MECHANICAL DATA

Encapsulation

The encapsulation comprises a 5-pin, in-line, resin-coated body, see Fig.5.

Soldering recommendations

HAND SOLDERING

The maximum contact time for a soldering iron temperature of 260 °C up to the seating plane is 5 s.

DIP OR WAVE SOLDERING

The maximum permissible temperature for the solder is 260 °C. It must not be in contact with the joint for more than 5 s.

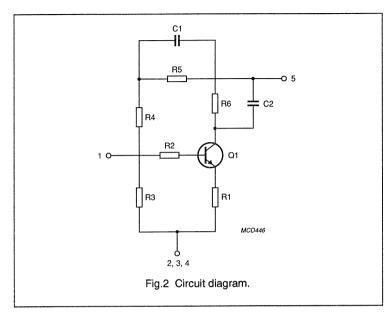
The total contact time of successive solder waves must not exceed 5 s.

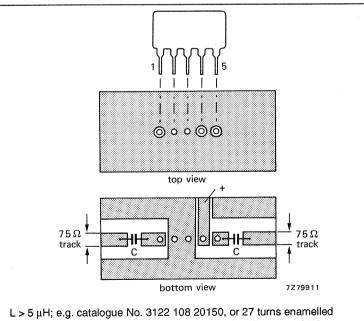
The device may be mounted against the printed-circuit board, but the temperature of the device must not exceed 125 °C.

If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature below the allowable limit.

Mounting recommendations

The module should preferably be mounted on a double-sided printed-circuit board, see Fig.3. Input and output pins should be connected to 75 Ω tracks. The connection to the common pins should be as close to the seating plane as possible.





 $L > 5 \mu H$; e.g. catalogue No. 3122 108 20150, or 27 turns enamelled 0.3 mm copper wire wound on a ferrite core with a diameter of 1.6 mm. C > 220 pF ceramic capacitor.

Fig.3 Printed-circuit board holes and tracks.

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LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
T _{amb}	ambient operating temperature range	-20	70	°C
T _{stg}	storage temperature range	-40	125	°C
V _B	DC supply voltage	_	13.5	V
P _{I1M} , P _{I8M}	peak incident powers on pins 1 and 8	_	100	mW

CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Measuring of	conditions		4	Aurorana ang panganana ang man		Accessed to the second
T _{amb}	ambient temperature		_	25	I -	°C
V _B	DC supply voltage		_	12	-	٧
R _s , R _L	source and load resistance		-	75	_	Ω
Z _o	characteristic impedance of HF connections		-	75	_	Ω
f	frequency range		40	-	860	MHz
Performanc	е					
I _B	supply current		_	82	-	mA
$G_{tr} = s_f ^2$	transducer gain		9	10	11	dB
±Δls _f l²	flatness of frequency response		_	1	_	dB
VSWR _(i)	individual maximum VSWR	input	_	1.5 (note 1)	-	
VSWR _(o)	individual maximum VSWR	output	-	1.4 (note 1)	_	
ls,l ²	back attenuation	f = 100 MHz	-	16	1-	dB
		f = 860 MHz	-	15	-	dB
V _{o(RMS)}	output voltage	at -60 dB intermodulation distortion (DIN 45004, par. 6.3, 3-tone)				
	VHF		115	116	-	dΒμV
	UHF		113	114	_	dΒμV
F	noise figure		-	10		dB

Notes

Scattering parameters: $s_f = s_{21}$; $s_r = s_{12}$.

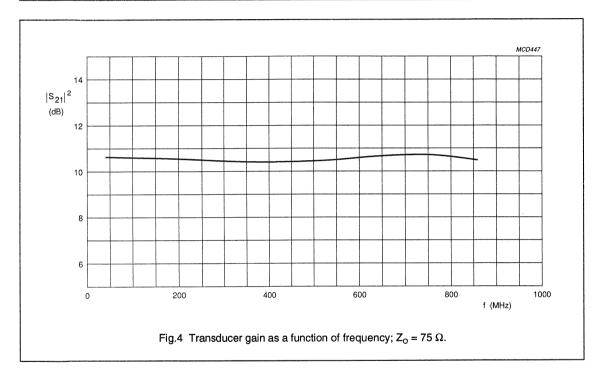
1. Highest value (for a sample) occurring in the frequency range.

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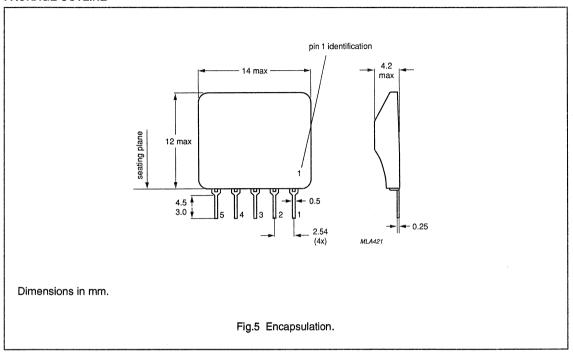
OPERATING CONDITIONS

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
T _{amb}	ambient operating temperature range	-20	_	70	°C
V _B	DC supply voltage	10.8	12	13.2	V
f	frequency range	40	_	860	MHz
R _s , R _L	source and load resistance	_	75	_	Ω



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PACKAGE OUTLINE



HYBRID INTEGRATED CIRCUIT VHF/UHF WIDE-BAND AMPLIFIER

Two-stage wide-band amplifier in hybrid integrated circuit technique on a thin-film substrate, intended for RATV and MATV applications.

QUICK REFERENCE DATA

D.C. supply voltage	v_B	=	12 V	± 10%
Frequency range	f	40 t	o 860 M	Hz
Source and load (characteristic) impedance	$R_s = R_{\ell} = Z_o$	=	75 Ω	
Transducer gain	$G_{tr} = s_f ^2$	typ.	18 dE	3
Flatness of frequency response	$\pm \Delta s_f ^2$	typ.	1 dE	3
Output voltage at -60 dB intermodulation	V	4.	100 dr	2\/
distortion (DIN 45004, 3-tone)	$V_{o(rms)}$	typ.	100 dE	3μ ν
Noise figure	F	typ.	5,2 dE	3
Operating ambient temperature	T _{amb}	-20 to	+ 70 00	2

ENCAPSULATION 5-pin, in-line, resin-coated body, see MECHANICAL DATA (Fig. 2)

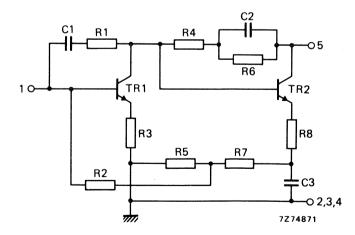


Fig. 1 Circuit diagram.

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RATINGS

Operating ambient temperature	T _{amb}	20 to	+ /0 00
Storage temperature	T _{stg}	40 to	+ 125 °C
D.C. supply voltage	V _B	max.	15 V
Peak incident powers on pins 1 and 5	P _{I1M} , P _{I5M}	max.	100 mW
CHARACTERISTICS			
Measuring conditions			

Limiting values in accordance with the Absolute Maximum System (IEC 134)

T _{amb}	=	25 °C
V _B	=	12 V
R _s , Rℓ	=	75 Ω
z_{o}	=	75 Ω
f	= 4	40 to 860 MHz
	V _B R _s , R _ℓ	$V_B = R_s, R_{\ell} = Z_o =$

Noise figure

Performance			
Supply current	IB	typ.	18 mA
Transducer gain	$G_{tr} = s_f ^2$	typ.	18 dB
Flatness of frequency response	$\pm \Delta \mid$ sf \mid 2	typ.	1 dB
Individual maximum v.s.w.r. input output	VSWR _(i) VSWR _(o)	typ. typ.	1,5 * 1,9 *
Back attenuation f = 100 MHz f = 860 MHz	s _r ² s _r ²	typ. typ.	29 dB 25 dB
Output voltage at -60 dB intermodulation distortion (DIN 45004, par. 6.3: 3-tone)	V _{o(rms)}	typ.	100 dBμV

s-parameters: s_f = s₂₁ $s_i = s_{11}$ s_r = s₁₂ $s_0 = s_{22}$

F

5,2 dB

typ.

^{*} Highest value, for a sample, occuring in the frequency range.

OPERATING CONDITIONS

Ambient temperature range

D.C. supply voltage

Frequency range

Source impedance and load impedance

 T_{amb} -20 to + 70 °C

 $V_B = 12 V \pm 10\%$

Dimensions in mm

f 40 to 860 MHz

 R_s , $R_0 = 75 \Omega$

MECHANICAL DATA

The device is resin coated.

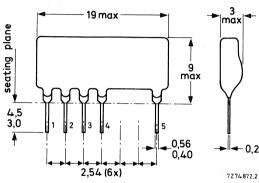


Fig. 2 Encapsulation.

Terminal connections

1 = input

2.3.4 = common

5 = output/supply(+)

Soldering recommendations

Hand soldering

Maximum contact time for a soldering-iron temperature of 260 °C up to the seating plane is 5 s.

Dip or wave soldering

260 °C is the maximum permissible temperature of the solder; it must not be in contact with the joint for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds. The device may be mounted against the printed-circuit board, but the temperature of the device must not exceed 125 °C. If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature below the allowable limit.

Mounting recommendations

The module should preferably be mounted on double-sided printed-circuit board, see the example shown below.

Input and output should be connected to 75 Ω tracks.

The connections to the 'common' pins should be as close to the seating plane as possible.

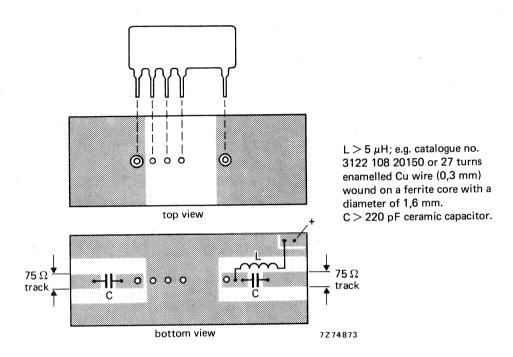


Fig. 3 Printed-circuit board holes and tracks.

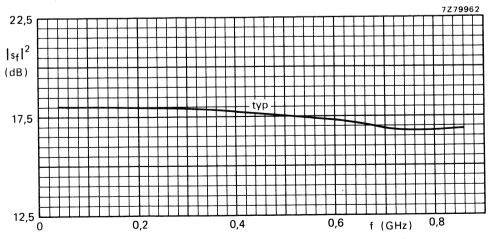


Fig. 4 Transducer gain as a function of frequency; $Z_0 = 75 \Omega$.

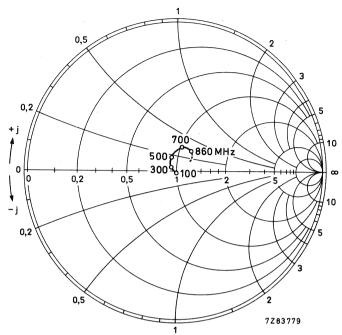


Fig. 5 Input impedance derived from input reflection coefficient s_i , co-ordinates in ohm x 75; typical values.

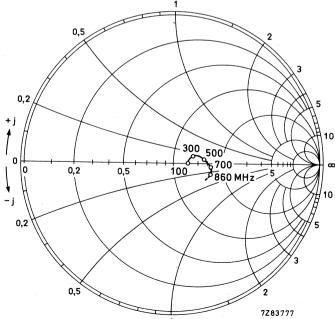


Fig. 6 Output impedance derived from output reflection coefficient s₀, co-ordinates in ohm x 75; typical values.

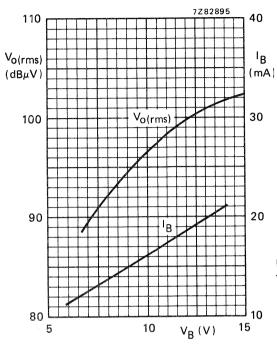


Fig. 7 Output voltage and supply current as a function of the supply voltage; typical values.

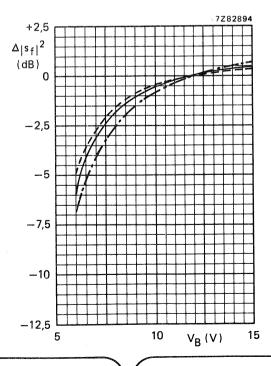


Fig. 8 Variation of transducer gain with supply voltage; reference 0 dB at 12 V: - f = 500 MHz;

---- f = 100 MHz; ----- f = 860 MHz;

typical values.

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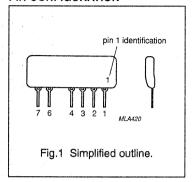
DESCRIPTION

A two-stage wideband amplifier in hybrid integrated circuit technology on a thin-film substrate, intended CATV and MATV applications.

PINNING

PIN	DESCRIPT	ION	
1	input		
2	common (-)		
3	common (-)		
4	common (-)		
5	n.c.		
6	common (-)		
7	output/supply (+)		

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
f	frequency range	1	40	-	860	MHz
R_s , R_L	source and load resistance		-	75	_	Ω
Z _o	characteristic impedance of HF connections		-	75	-	Ω
$G_{tr} = s_f ^2$	transducer gain		 -	28	_	dB
±∆ls _f l²	flatness of frequency response		1-	1	-	dB
V _{o(RMS)}	output voltage	at -60 dB intermodulation distortion (DIN 45004, 3-tone)	-	107	-	dΒμV
F	noise figure		-	4.5	-	dB
V _B	DC supply voltage		10.8	12	13.2	V
T _{amb}	ambient operating temperature range		-20	_	70	°C

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MECHANICAL DATA

Encapsulation

The encapsulation comprises an 8-pin, in-line, resin-coated body, see Fig.7.

Soldering recommendations

HAND SOLDERING

The maximum contact time for a soldering iron temperature of 260 °C up to the seating plane is 5 s.

DIP OR WAVE SOLDERING

The maximum permissible temperature for the solder is 260 °C. It must not be in contact with the joint for more than 5 s.

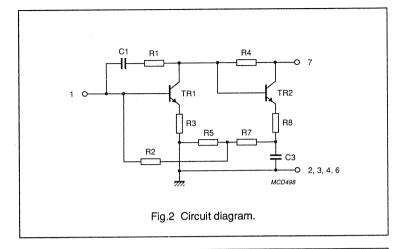
The total contact time of successive solder waves must not exceed 5 s.

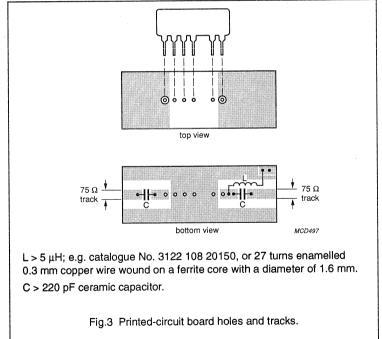
The device may be mounted against the printed-circuit board, but the temperature of the device must not exceed 125 °C.

If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature below the allowable limit.

Mounting recommendations

The module should preferably be mounted on a double-sided printed-circuit board, see Fig.3. Input and output pins should be connected to 75 Ω tracks. The connection to the common pins should be as close to the seating plane as possible.





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LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
T _{amb}	ambient operating temperature range	-20	70	°C
T _{stg}	storage temperature range	-40	125	°C
V _B	DC supply voltage	_	15	٧
P _{I1M} , P _{I8M}	peak incident powers on pins 1 and 8	_	100	mW

CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Measuring o	onditions		***************************************		·	
T _{amb}	ambient temperature		-	25	T-	°C
V _B	DC supply voltage		11.9	12	12.1	V
R _s , R _L	source and load resistance		-	75	-	Ω
Z _o	characteristic impedance of HF connections		-	75	-	Ω
f	frequency range		40	_	860	MHz
Performance	e					
l _B	supply current		38	42	44	mA
$G_{tr} = s_f ^2$	transducer gain		26	28	29	dB
±Δls _f l²	flatness of frequency response		-	1	-	dB
VSWR _(i)	individual maximum VSWR	input	-	2.2 (note 1)	-	
VSWR _(o)	individual maximum VSWR	output	_	2.1 (note 1)	-	
ls,l ²	back attenuation	f = 100 MHz	-	36	-	dB
		f = 860 MHz	-	29	-	dB
V _{o(RMS)}	output voltage	at -60 dB intermodulation distortion (DIN 45004, par. 6.3, 3-tone)	_	107	_	dBμV
F	noise figure		-	4.5	-	dB

Notes

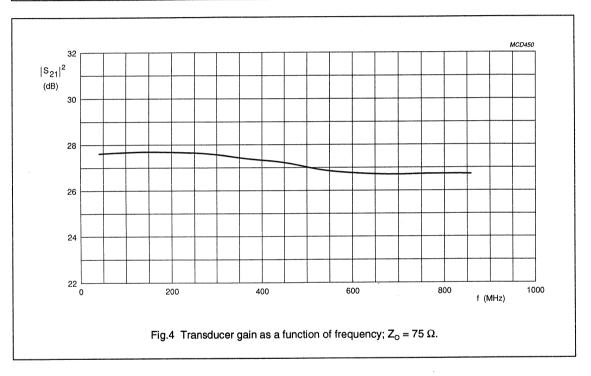
Scattering parameters: $s_f = s_{21}$; $s_r = s_{12}$; $s_i = s_{11}$; $s_o = s_{22}$.

1. Highest value (for a sample) occurring in the frequency range.

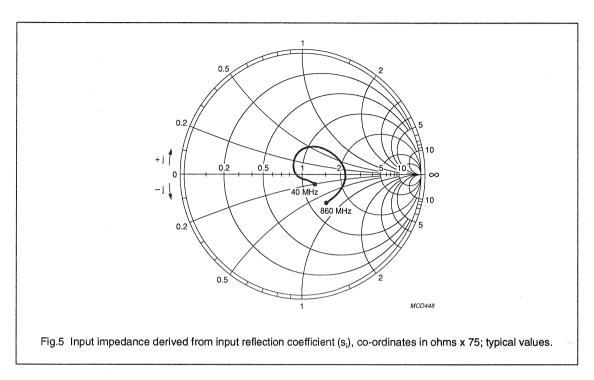
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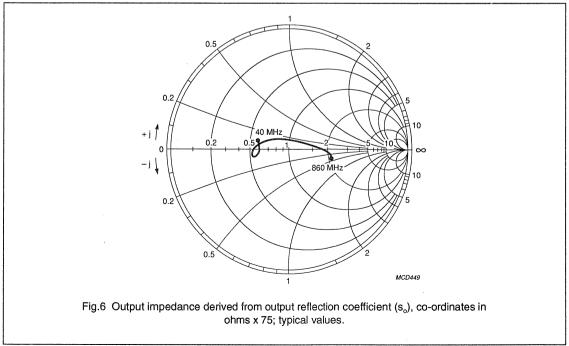
OPERATING CONDITIONS

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
T _{amb}	ambient operating temperature range	-20	_	70	°C
V _B	DC supply voltage	10.8	12	13.2	V
f	frequency range	40	_	860	MHz
R _s , R _L	source and load resistance		75	_	Ω



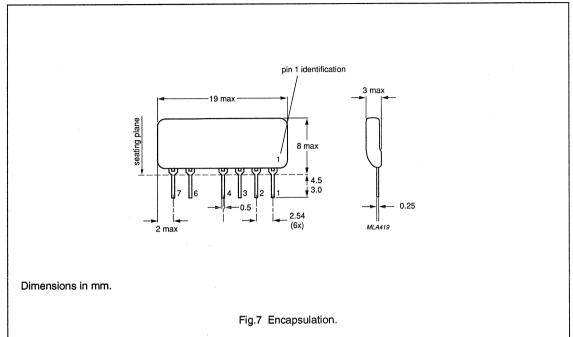
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PACKAGE OUTLINE



HYBRID INTEGRATED CIRCUIT VHF/UHF WIDE-BAND AMPLIFIER

Three-stage wide-band amplifier in hybrid integrated circuit technique on a thin-film substrate, intended for use in mast-head booster-amplifiers, as preamplifier in MATV systems, and as general-purpose amplifier for v.h.f. and u.h.f. applications.

QUICK REFERENCE DATA

Frequency range	f	40 to 860		MHz
Source and load (characteristic) impedance	$R_s = R_{\ell} = Z_o$	=	75	Ω
Transducer gain	$G_{tr} = s_f ^2$	typ.	23	dB
Flatness of frequency response	$\pm \Delta s_{f} ^2$	typ.	1.0	dB
Output voltage at -60 dB intermodulation distortion (DIN 45004, 3-tone)	V _{O(rms)}	>	105	dΒμV
Noise figure	F	typ.	5,4	dB
D.C. supply voltage	V _B	=	12	V ± 10%
Operating ambient temperature	T _{amb}	-20 to +70 °C		°C

ENCAPSULATION 8-pin, in-line, resin-coated body, see MECHANICAL DATA (Fig. 2)

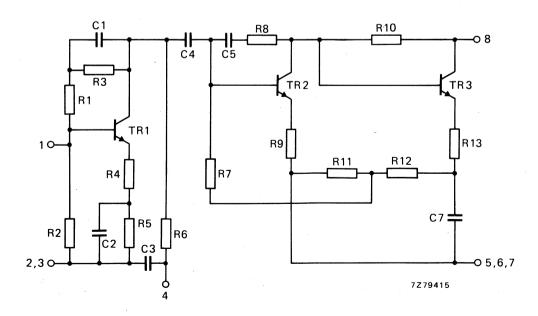


Fig. 1 Circuit diagram.

RATINGS

11/11/14/00					
Limiting values in accorda	ance with the Absolute Maxim	um System (IEC 134)			
Operating ambient tempe	rature	T_{amb}	-20	to +70	oC
Storage temperature		T_{stg}	40 1	to +125	oC
D.C. supply voltage		VB	max.	15	V
Peak incident powers on p	pins 1 and 7	P _{I1M} , P _{I7M}	max.	100	mW
CHARACTERISTICS					
Measuring conditions					
Ambient temperature		T _{amb}	=	25	oC
D.C. supply voltage		V_{B}	=	12	V
Source impedance and loa	ad impedance	R _s , Rℓ	==	75	Ω
Characteristic impedance	of h.f. connections	Z _o	=	75	Ω
Frequency range		f	= 40	to 860	MHz
Performance					
Supply current		IB	typ.	56	mΑ
Transducer gain		$G_{tr} = s_f ^2$	typ. 2	23 1 to 25	dB dB
Flatness of frequency resp	oonse	$\pm\Delta s_{f} ^2$	typ.	1.0	dB
Individual maximum v.s.v	v.r.				
input		VSWR _(i)	typ.	1.4 1.6	
output Back attenuation		VSWR _(o)	typ.	1.0	
f = 100 MHz		s _r ²	typ.	42	dB
f = 860 MHz		s _r ²	typ.	33	dB
Output voltage					
at -60 dB intermodula		Vo(rms)	>		dBμV dBμV
(DIN 45004, par. 6.3: 3	s-tone)	F.	typ.		dBμν
Noise figure		Г	typ.	5,4	ub
	s-parameters: s _f = s ₂₁	s _i = s ₁₁			
	s _r = s ₁₂	s _o = s ₂₂			

^{*} Highest value, for a sample, occurring in the frequency range.

Dimensions in mm

OPERATING CONDITIONS

Ambient temperature range	T _{amb}	-20 to +	-70	оС
D.C. supply voltage	V_{B}	=	12	V ± 10%
Frequency range	f	40 to 8	360	MHz
Source impedance and load impedance	R_s , R_{ℓ}	=	75	Ω

MECHANICAL DATA

The device is resin coated.

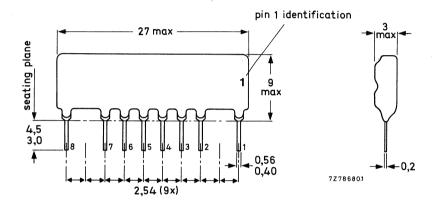


Fig. 2 Encapsulation.

Terminal connections

```
1 = input
2, 3, 5, 6, 7 = common
4 = supply (+)
8 = output/supply (+)
```

Soldering recommendations

Hand soldering

Maximum contact time for a soldering-iron temperature of 260 °C up to the seating plane is 5 s.

Dip or wave soldering

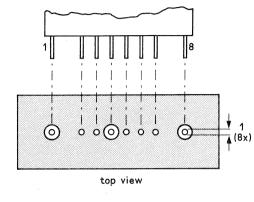
260 °C is the maximum permissible temperature of the solder; it must not be in contact with the joint for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds. The device may be mounted against the printed-circuit board, but the temperature of the device must not exceed 125 °C. If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature below the allowable limit.

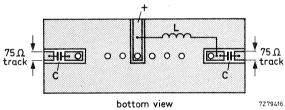
Mounting recommendations

The module should preferably be mounted on double-sided printed-circuit board, see the example shown below.

Input and output should be connected to 75 Ω tracks.

The connections to the 'common' pins should be as close to the seating plane as possible.





 $L > 5 \mu H$; e.g. catalogue no. 3122 108 20150 or 27 turns enamelled Cu wire (0,3 mm) wound on a ferrite core with a diameter of 1,6 mm. C > 220 pF ceramic capacitor.

Fig. 3 Printed-circuit board holes and tracks.

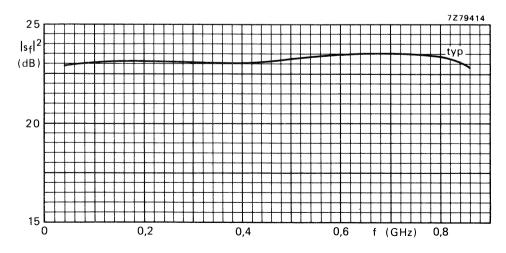


Fig. 4 Transducer gain as a function of frequency; $Z_0 = 75 \Omega$.

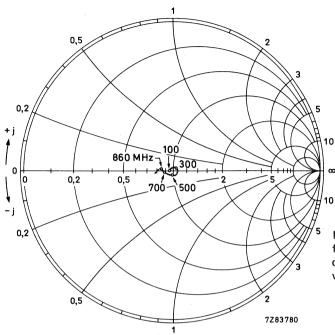


Fig. 5 Input impedance derived from input reflection coefficient s_i, co-ordinates in ohm x 75; typical values.

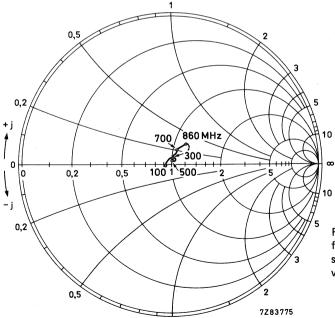


Fig. 6 Output impedance derived from output reflection coefficient s_0 , co-ordinates in ohm x 75; typical values.

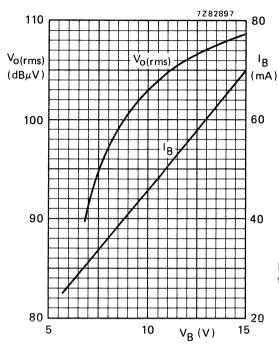


Fig. 7 Output voltage and supply current as a function of the supply voltage; typical values.

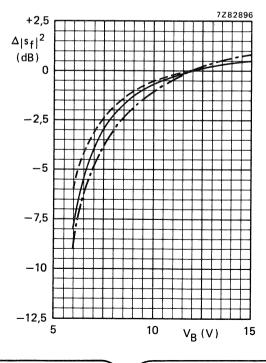


Fig. 8 Variation of transducer gain with supply voltage; reference 0 dB at 12 V;

---- f = 500 MHz;

---- f = 100 MHz;

---- f = 860 MHz;

typical values.

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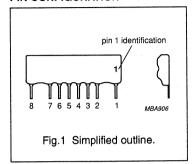
DESCRIPTION

A three-stage wideband amplifier in hybrid integrated circuit technology on a thin-film substrate, intended for use in mast-head booster-amplifiers, as an amplifier in MATV systems, and as a general purpose amplifier for VHF and UHF applications.

PINNING

PIN	DESCRIPTION
1	input
2	common
3	common
4	supply (+)
5	common
6	common
7	common
8	output/supply (+)

PIN CONFIGURATION



QUICK REFERENCE DATA

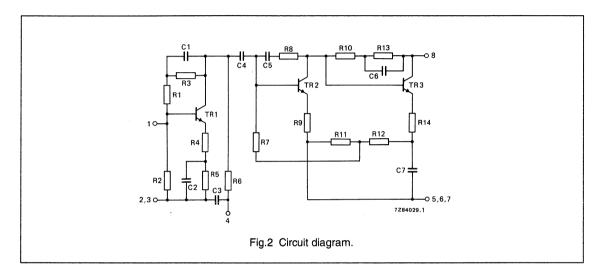
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
f	frequency range		40	_	860	MHz
$R_s = R_L = Z_o$	source and load (characteristic) impedance		_	75	- 33,000	Ω
$G_{tr} = s_t ^2$	transducer gain		-	29	-	dB
$\pm \Delta s_t ^2$	flatness of frequency response		_	1		dB
V _{o(RMS)}	output voltage	at -60 dB intermodulation distortion (DIN 45004, 3-tone)				
	VHF		-	103	-	dΒμV
·	UHF		-	105		dΒμV
F	noise figure		-	3.6	_	dB
V _B	DC supply voltage		10.8	12	13.4	V
T _{amb}	ambient operating temperature range		-20	_	70	°C

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MECHANICAL DATA

Encapsulation

The encapsulation comprises an 8-pin, in-line, resin-coated body, see Fig.8.



Soldering recommendations

HAND SOLDERING

The maximum contact time for a soldering iron temperature of 260 °C up to the seating plane is 5 s.

DIP OR WAVE SOLDERING

The maximum permissible temperature for the solder is 260 °C. It must not be in contact with the joint for more than 5 s.

The total contact time of successive solder waves must not exceed 5 s.

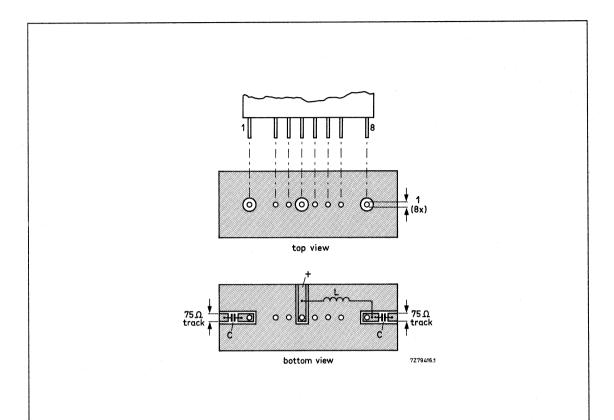
The device may be mounted against the printed-circuit board, but the temperature of the device must not exceed 125 °C.

If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature below the allowable limit.

Mounting recommendations

The module should preferably be mounted on a double-sided printed-circuit board, see Fig.3. Input and output pins should be connected to 75 Ω tracks. The connection to the common pins should be as close to the seating plane as possible.

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 $L>5~\mu H;$ e.g. catalogue No. 3122 108 20150, or 27 turns enamelled 0.3 mm copper wire wound on a ferrite core (material 4B1; catalogue No. 3122 104 91110) with a diameter of 1.6 mm.

C > 220 pF ceramic capacitor.

Fig.3 Printed-circuit board holes and tracks.

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
T _{amb}	ambient operating temperature range	-20	70	°C
T _{stg}	storage temperature range	-40	125	°C
V _B	DC supply voltage	_	15	٧
P _{I1M} , P _{I8M}	peak incident powers on pins 1 and 8	-	100	mW

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CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Measuring c	onditions		· Laurence and construction			
T _{amb}	ambient temperature		T-	25	T-	°C
V _B	DC supply voltage		-	12	-	V
R _s , R _L	source impedance and load impedance		-	75	_	Ω
Z _o	characteristic impedance of HF connections		-	75	_	Ω
f .	frequency range		40	-	860	MHz
Performance	•					
I _B	supply current		1-	52	-	mA
$G_{tr} = s_f ^2$	transducer gain		-	29	-	dB
±Δ S _f ²	flatness of frequency response		-	1	1.5	dB
VSWR _(i)	individual maximum VSWR	input	-	2.3 (note 1)	-	
VSWR _(o)	individual maximum VSWR	output	-	1.4 (note 1)	-	
ls _r l ²	back attenuation	f = 100 MHz	_	46	_	dB
		f = 860 MHz	_	41	-	dB
$V_{o(RMS)}$	output voltage	at -60 dB intermodulation distortion (DIN 45004, par. 6.3, 3-tone)				
	VHF		-	103	_	dΒμV
	UHF		_	105	_	dΒμV
F	noise figure		-	3.6	-	dB

Notes

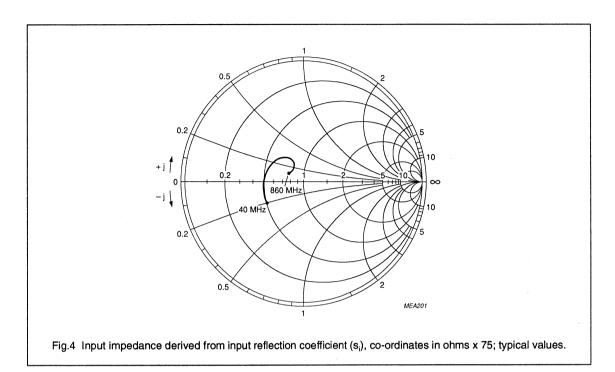
Scattering parameters: $s_f = s_{21}$; $s_r = s_{12}$.

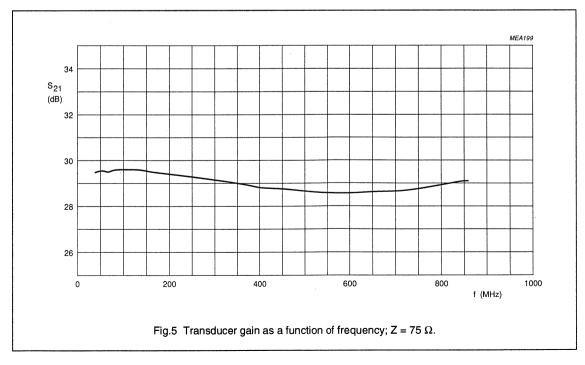
1. Highest value (for a sample) occurring in the frequency range.

OPERATING CONDITIONS

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
T _{amb}	ambient operating temperature range	-20	_	70	°C
V _B	DC supply voltage	10.8	12	13.4	٧
f	frequency range	40	-	860	MHz
R _s , R _L	source impedance and load impedance	-	75	_	Ω

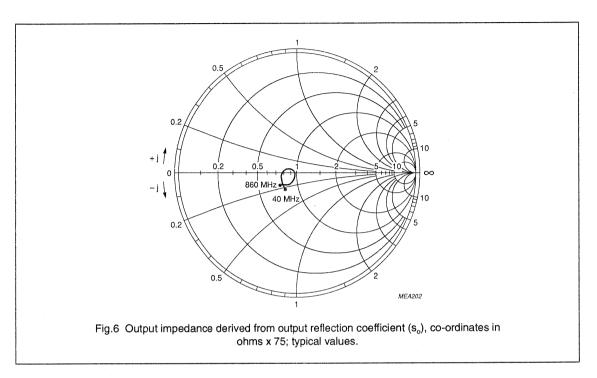
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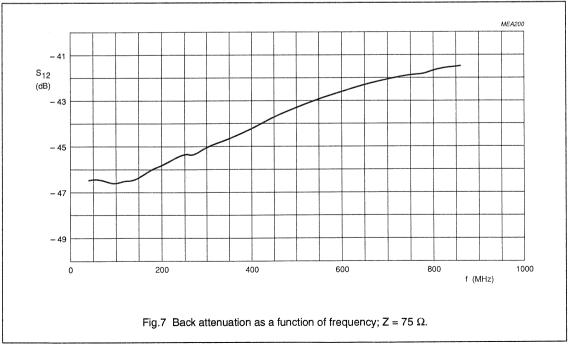




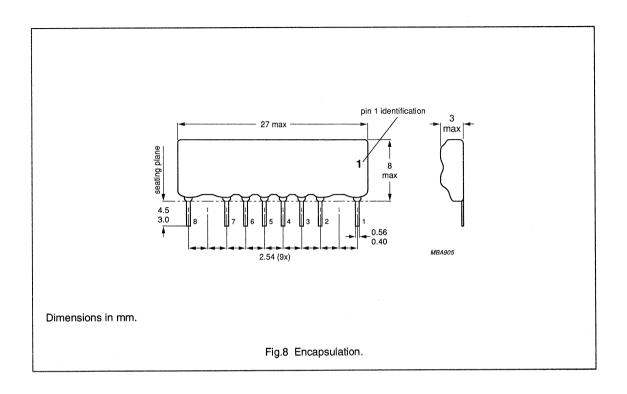
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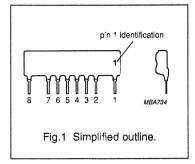
DESCRIPTION

A three-stage wideband amplifier in hybrid integrated circuit technology on a thin-film substrate, intended for use in mast-head booster-amplifiers, as an amplifier in MATV systems, and as a general purpose amplifier for VHF and UHF applications.

PINNING

PIN	DESCRIPTION
1	input
2	common
3	common
4	supply (+)
5	common
6	common
7	common
8	output/supply (+)

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
f	frequency range		40	-	860	MHz
$R_S = R_L = Z_O$	source and load (characteristic) impedance		-	75	_	Ω
$G_{tr} = s_f ^2$	transducer gain		-	28	-	dB
±ΔlS _f l ²	flatness of frequency response		 -	1	-	dB
V _{o(RMS)}	output voltage	at -60 dB intermodulation distortion (DIN 45004, 3-tone)	105	107	_	dΒμV
F	noise figure		-	4.4	_	dB
V _B	DC supply voltage		10.8	12	13.4	٧
T _{amb}	ambient operating temperature range		-20	_	70	°C

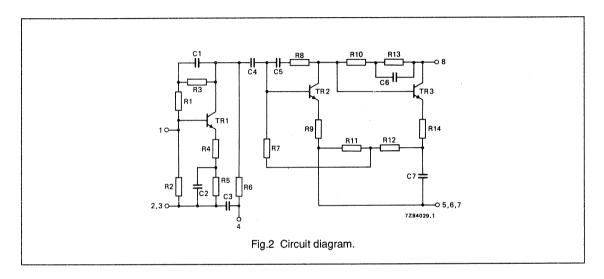
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MECHANICAL DATA

Encapsulation

The encapsulation comprises an 8-pin, in-line, resin-coated body, see Fig.7.



Soldering recommendations

HAND SOLDERING

The maximum contact time for a soldering iron temperature of 260 °C up to the seating plane is 5 s.

DIP OR WAVE SOLDERING

The maximum permissible temperature for the solder is 260 °C. It must not be in contact with the joint for more than 5 s.

The total contact time of successive solder waves must not exceed 5 s.

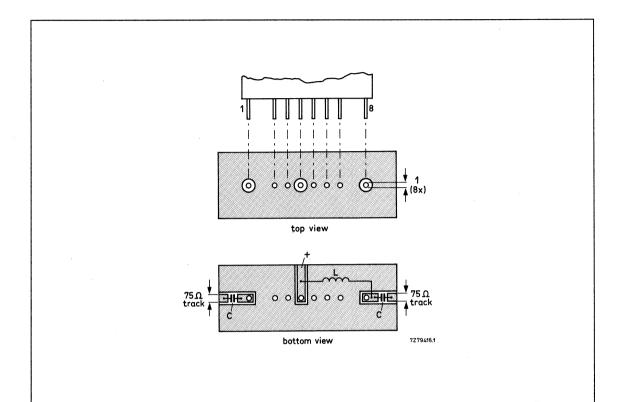
The device may be mounted against the printed-circuit board, but the temperature of the device must not exceed 125 °C.

If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature below the allowable limit.

Mounting recommendations

The module should preferably be mounted on a double-sided printed-circuit board, see Fig.3. Input and output should be connected to 75 Ω tracks. The connection to the common pins should be as close to the seating plane as possible.

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 $L > 5 \mu H$; e.g. catalogue No. 3122 108 20150, or 27 turns enamelled 0.3 mm copper wire wound on a ferrite core (material 4B1; catalogue No. 3122 104 91110) with a diameter of 1.6 mm.

C > 220 pF ceramic capacitor.

Fig.3 Printed-circuit board holes and tracks.

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
T _{amb}	ambient operating temperature range	-20	70	°C
T _{stg}	storage temperature range	-40	125	°C
V _B	DC supply voltage	-	15	٧
P _{I1M} , P _{I8M}	peak incident powers on pins 1 and 8	_	100	mW

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CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Measuring	conditions					-
T _{amb}	ambient temperature		_	25	-	°C
V _B	DC supply voltage		_	12	-	V
R _s , R _L	source impedance and load impedance		_	75	_	Ω
Zo	characteristic impedance of HF connections		-	75	_	Ω
f	frequency range		40	-	860	MHz
Performan	ice					
l _B	supply current		48	51	54	mA
$G_{tr} = s_f ^2$	transducer gain		26	28	31	dB
±Δls _f l ²	flatness of frequency response		-	1	1.5	dB
VSWR _(i)	individual maximum VSWR	input	_	1.3 (note 1)	1.5	
VSWR _(o)	individual maximum VSWR	output	_	1.5 (note 1)	1.6	
ls _r l ²	back attenuation	f = 100 MHz	42	44	Ī-	dB
		f = 860 MHz	37	39	-	dB
V _{o(RMS)}	output voltage	at -60 dB intermodulation distortion (DIN 45004, par. 6.3, 3-tone)	105	107	_	dΒμV
F	noise figure		_	4.4	-	dB

Notes

Scattering parameters: $s_f = s_{21}$; $s_r = s_{12}$.

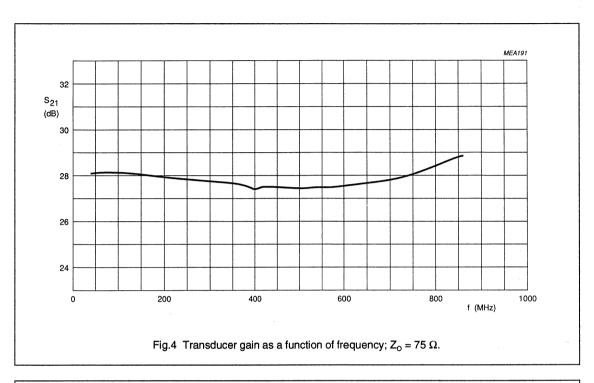
1. Highest value (for a sample) occurring in the frequency range.

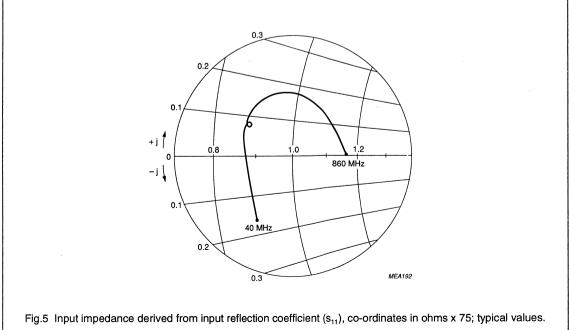
OPERATING CONDITIONS

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
T _{amb}	ambient temperature range	-20	_	70	°C
V _B	DC supply voltage	10.8	12	13.4	٧
f	frequency range	40	_	860	MHz
R _s , R _L	source impedance and load impedance	<u> </u>	75	_	Ω

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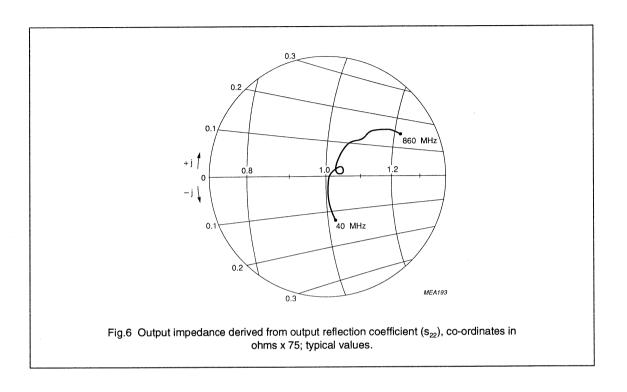
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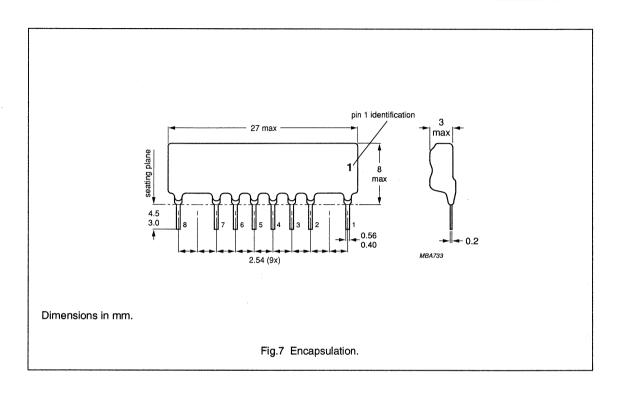


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HYBRID INTEGRATED CIRCUIT VHF/UHF WIDE-BAND AMPLIFIER

Three-stage wide-band amplifier in hybrid integrated circuit technique on a thin-film substrate, intended for use in mast-head booster-amplifiers, as an amplifier in MATV and CATV systems, and as general-purpose amplifier for v.h.f. and u.h.f. applications.

QUICK REFERENCE DATA

Frequency range	f		40 to 860	MHz
Source and load (characteristic) impedance	$R_s = R_{\ell} = Z_{\ell}$) =	75	Ω
Transducer gain	$G_{tr} = s_f ^2$	typ.	28	dB
Flatness of frequency response	$\pm \Delta \mathbf{s_f} ^2$	typ.	1	dB
Output voltage at -60 dB intermodulation distortion (DIN 45004, 3-tone) VHF UHF	Vo(rms) Vo(rms)	typ. typ.		dΒμV dΒμV
Noise figure	F	typ.	4,8	dB
D.C. supply voltage	v _B	=	12	V ± 10%
Operating ambient temperature	T _{amb}		-20 to +70	оС

ENCAPSULATION 9-pin, in-line, resin-coated body, see MECHANICAL DATA (Fig.2)

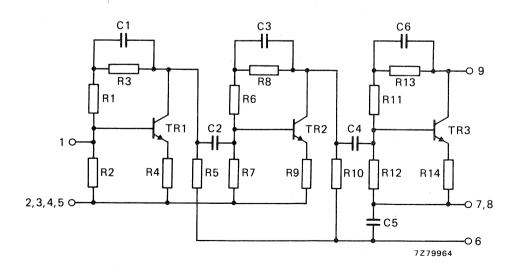


Fig. 1 Circuit diagram.

RATINGS

Limiting values in accordance with the Absolute Maximur	m System (IEC 13			
Operating ambient temperature	T _{amb}	-20 to +70		
Storage temperature			40 to +125	οС
D.C. supply voltage	v _B	max.	15	-
Peak incident powers on pins 1 and 8	P _{I1M} , P _{I8M}	max.	100	mW
CHARACTERISTICS				
Measuring conditions			٠	_
Ambient temperature	T_{amb}	=		°С
D.C. supply voltage	v_B	=	12	٧
Source impedance and load impedance	R _s , R _ℓ	=	75	
Characteristic impedance of h.f. connections	z _o	=	75	W.,
Frequency range	f	=	40 to 860	MHz
Performance		•		
Supply current	I _B	typ.	100	mΑ
Transducer gain	$G_{tr} = s_f ^2$	typ.	28 26 to 31	dB dB
Flatness of frequency response	$\pm \Delta s_f ^2$	typ.	1	dB
Individual maximum v.s.w.r.				
input	vswr _(i)	typ.	2,3	
output	VSWR _(o)	typ.	1,9	*
Back attenuation	2	4	45	םג
f = 100 MHz f = 860 MHz	s _r ² s _r ²	typ. typ.		dB dB
Output voltage	1 °ri	٠, ٢,	00	
at –60 dB intermodulation distortion (DIN 45004, par. 6,3; 3-tone)				
VHF	V _{o(rms)}	> typ.		dBμV dBμV
UHF	V _{o(rms)}	> typ.		dΒμV dΒμV
Noise figure	F	typ.	4,8	dB
s-parameters: $s_f = s_{21}$ $s_r = s_{12}$	s _i = s ₁₁ s _o = s ₂₂			

^{*} Highest value, for a sample, occurring in the frequency range.

OPERATING CONDITIONS

Ambient	temperature	range
---------	-------------	-------

D.C. supply voltage

Frequency range

Source impedance and load impedance

Dimensions in mm

MECHANICAL DATA

The device is resin coated.

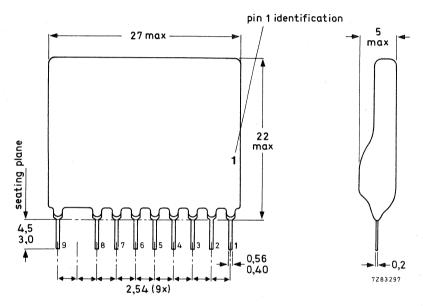


Fig. 2 Encapsulation.

Terminal connections

1 = input 2,3,4,5 and 7,8 = common 6 = supply (+) 9 = output/supply (+)

Soldering recommendations

Hand soldering

Maximum contact time for a soldering-iron temperature of 260 °C up to the seating plane is 5 s.

Dip or wave soldering

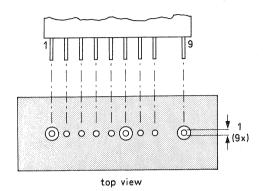
260 °C is the maximum permissible temperature of the solder; it must not be in contact with the joint for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds. The device may be mounted against the printed-circuit board, but the temperature of the device must not exceed 125 °C. If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature below the allowable limit.

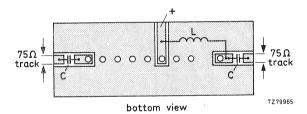
Mounting recommendations

The module should preferably be mounted on double-sided printed-circuit board, see the example shown below.

Input and output should be connected to 75 Ω tracks.

The connections to the 'common' pins should be as close to the seating plane as possible.





L > 5 μ H; e.g. catalogue no. 3122 108 20150 or 27 turns enamelled Cu wire (0,3 mm) wound on a ferrite core (material 4B1; catalogue no. 3122 104 91110) with a diameter of 1,6 mm. C > 220 pF ceramic capacitor.

Fig. 3 Printed-circuit board holes and tracks.

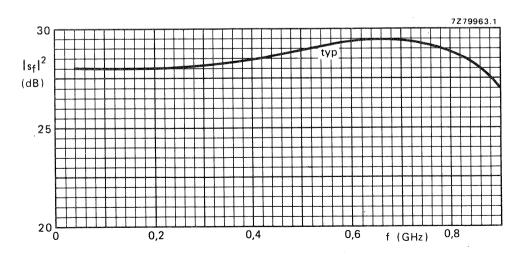


Fig. 4 Transducer gain as a function of frequency; $Z_0 = 75 \Omega$.

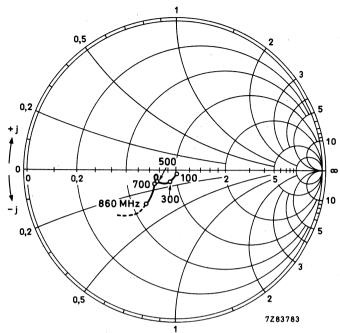


Fig. 5 Input impedance derived from input reflection coefficient s_i , co-ordinates in ohm x 75; typical values.

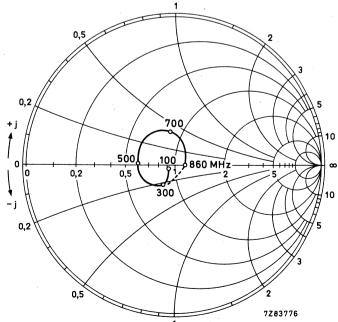


Fig. 6 Output impedance derived from output reflection coefficient s_0 , co-ordinates in ohm x 75; typical values.

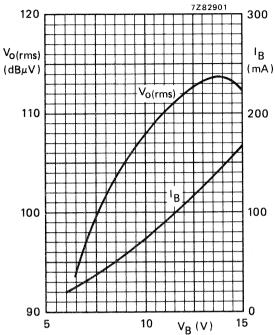


Fig. 7 Output voltage and supply current as a function of the supply voltage; typical values.

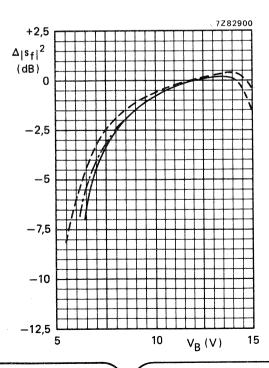


Fig. 8 Variation of transducer gain with supply voltage; reference 0 dB at 12 V;

---- f = 500 MHz;

---- f = 100 MHz;

----- f = 860 MHz;

typical values.

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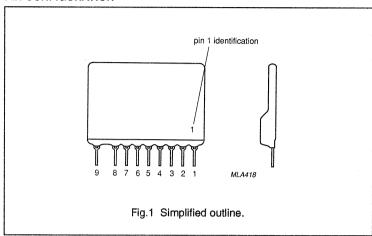
DESCRIPTION

A three-stage wideband amplifier in hybrid integrated circuit technology on a thin-film substrate, intended for use in mast-head booster-amplifiers, as an amplifier in CATV and MATV systems, and as a general purpose amplifier for VHF and UHF applications.

PINNING

PIN	DESCRIPTION
1	input
2	common (-)
3	common ()
4	common (-)
5	common (–)
6	supply (+)
7	common (-)
8	common (–)
9	output/supply (+)

PIN CONFIGURATION



QUICK REFERENCE DATA

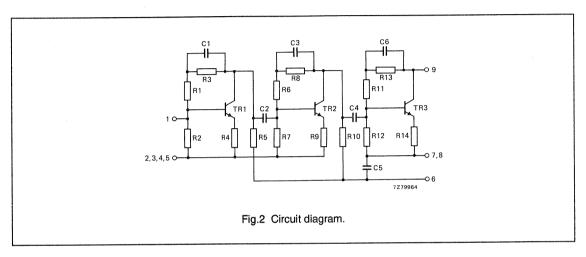
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
f	frequency range		40	-	860	MHz
R_s , R_L	source and load resistance		_	75	-	Ω
Zo	characteristic impedance of HF connections		-	75	-	Ω
$G_{tr} = s_t ^2$	transducer gain		Ī-	30	-	dB
±Δls _f l ²	flatness of frequency response		 -	1	-	dB
V _{o(RMS)}	output voltage VHF UHF	at -60 dB intermodulation distortion (DIN 45004, 3-tone)	_	113 112	_	dΒμV dΒμV
F	noise figure		-	4.8	-	dB
V _B	DC supply voltage		10.8	12	13.2	٧
T _{amb}	ambient operating temperature range		-20	-	70	°C

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MECHANICAL DATA

Encapsulation

The encapsulation comprises a 9-pin, in-line, resin-coated body, see Fig.6.



Soldering recommendations

HAND SOLDERING

The maximum contact time for a soldering iron temperature of 260 °C up to the seating plane is 5 s.

DIP OR WAVE SOLDERING

The maximum permissible temperature for the solder is 260 °C. It must not be in contact with the joint for more than 5 s.

The total contact time of successive solder waves must not exceed 5 s.

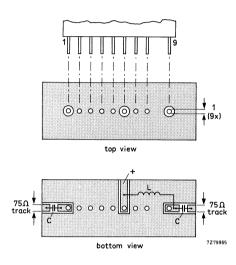
The device may be mounted against the printed-circuit board, but the temperature of the device must not exceed 125 °C.

If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature below the allowable limit.

Mounting recommendations

The module should preferably be mounted on a double-sided printed-circuit board, see Fig.3. Input and output pins should be connected to 75 Ω tracks. The connection to the common pins should be as close to the seating plane as possible.

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 $L > 5~\mu H$; e.g. catalogue No. 3122 108 20150, or 27 turns enamelled 0.3 mm copper wire wound on a ferrite core with a diameter of 1.6 mm.

C > 220 pF ceramic capacitor.

Fig.3 Printed-circuit board holes and tracks.

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
T _{amb}	ambient operating temperature range	-20	70	°C
T _{stg}	storage temperature range	-40	125	°C
V_{B}	DC supply voltage	_	15	V
P _{11M} , P _{18M}	peak incident powers on pins 1 and 8	_	100	mW

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CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Measuring c	onditions					
T _{amb}	ambient temperature			25		°C
V _B	DC supply voltage		l –	12		٧
R _s , R _L	source and load resistance			75		Ω
Zo	characteristic impedance of HF connections		_	75	_	Ω
f	frequency range		40		860	MHz
Performance	ė					
I _B	supply current			100		mA
$G_{tr} = s_t ^2$	transducer gain		28	30	33	dB
±Δls _t l ²	flatness of frequency response		_	1		dB
VSWR _(i)	individual maximum VSWR	input		2.7 (note 1)	-	
VSWR _(o)	individual maximum VSWR	output	_	1.9 (note 1)	•••	
ls,l ²	back attenuation	f = 100 MHz	_	45	I-	dB
'		f = 860 MHz	-	35	-	dB
V _{o(RMS)}	output voltage VHF UHF	at -60 dB intermodulation distortion (DIN 45004, par. 6.3, 3-tone)	111 110	113 112	-	dΒμV dΒμV
F	noise figure		-	4.8	_	dB

Notes

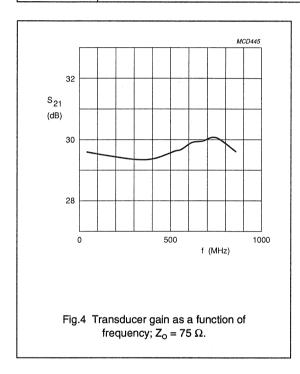
Scattering parameters: $s_f = s_{21}$; $s_r = s_{12}$; $s_i = s_{11}$; $s_o = s_{22}$.

1. Highest value (for a sample) occurring in the frequency range.

OM2070B

OPERATING CONDITIONS

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
T _{amb}	ambient operating temperature range	-20		70	°C
V_B	DC supply voltage	10.8	12	13.2	٧
f	frequency range	40	-	860	MHz
R _s , R _L	source and load resistance	_	75	_	Ω



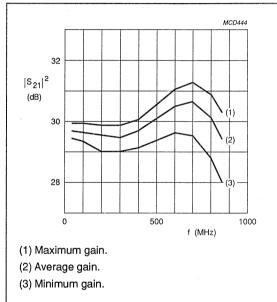
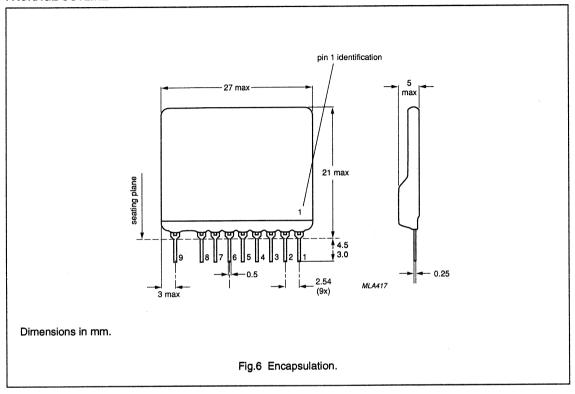


Fig.5 Power gain.

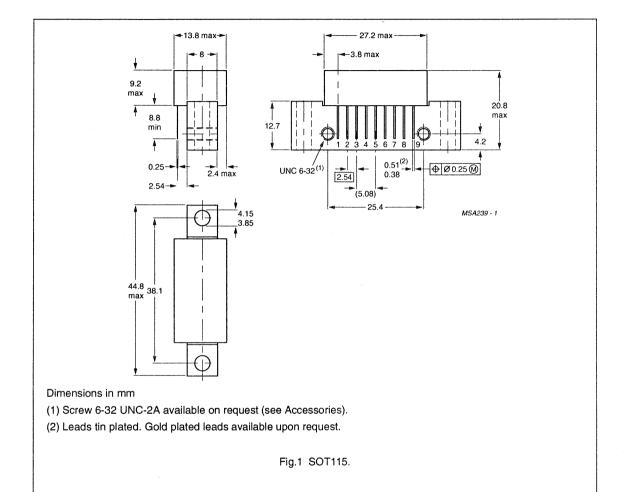
OM2070B

PACKAGE OUTLINE



ENVELOPES





ENVELOPES - SOT115

VARIANT	NUMBER OF PINS	USED PINS
С	7	1, 2, 3, 5, 7, 8, 9
D	9	ALL
Н	6	1, 2, 5, 6, 8, 9



ACCESSORIES



CATV test jig Accessories

Devices

Ordering

information

suitable only for BGX885 and

CATV test fixture 860 MHz,

12NC: 7322 142 89060.

BGD885

SPECIFICATION FOR CATVITEST JIG

(range 40 - 860 MHz)

Impedance

75 Ω

Return loss

< -40 dB at 40 MHz. Decreases 1.5 dB/octave up to 860 MHz. < -32 dB at 860 MHz. (Measured with thru-line system and other port terminated with a very good 75 Ω

load)

Cross talk

< -80 dB

Insertion loss

< 0.1 dB (Measured with thru-line

system)

Note

The above parameters are in the frequency range from 40-860 MHz.

DC current

max. 1 A.

Voltage

max. 50 V. (The DC is automatically switched to the device, by means of a micro-switch, after closing the

pressing system.)

Temperature

-25 to +75 °C.

range

RF connectors : N-type female (75 Ω)

DC connectors :

Banana plug

Dimensions

110 x 60 x 55 mm (I x b x h, dimensions without pressing system, RF connectors and cooling

connections).

Distance between the centre contact of the RF connectors is

35.2 mm.

Cooling

October 1990

possibility for water cooling available

on the fixture.

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CATV test jig Accessories

SPECIFICATION FOR CATV TEST JIG

(range 5 - 600 MHz)

Impedance

 75Ω

Return loss

<-40 dB (Measured with thru-line

system and other port terminated

with a very good 75 Ω load)

Cross talk

<-80 dB

Insertion loss

< 0.1 dB (Measured with thru-line

system)

Note

The above parameters are in the frequency range from 5 - 600 MHz.

DC current

max. 1 A.

Voltage

max. 50 V. (The DC is automatically

switched to the device, by means of a micro-switch, after closing the

pressing system.)

Temperature

range

-25 to +75 °C.

RF connectors

N-type female (75 Ω)

DC connectors :

Banana plug

Dimensions

110 x 60 x 55 mm (l x b x h,

dimensions without pressing system, RF connectors and cooling

connections).

Distance between the centre contact of the RF connectors is

35.2 mm.

Cooling

possibility for water cooling available

on the fixture.

Devices

suitable only for devices with positive and negative power

requirement, (by means of switch).

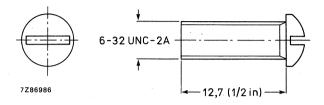
Ordering information

CATV test fixture 600 MHz, 12NC: 7322 142 54250.

October 1990

ROUND HEAD SCREW 6-32 UNC-2A

Available, upon request, under type number 56396 or 12 NC code number 9390 298 10xx0.





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Data handbook system

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PROFESSIONAL COMPONENTS;

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